

# Detectors for Reactions

Exotic Beam Summer School 2016

*Steven D. Pain*  
*Physics Division*



OAK RIDGE NATIONAL LABORATORY

Managed by UT-Battelle for the Department of Energy

# Measurement in Nuclear Experiments

## ***What I'll try to cover:***

*Interaction of energetic particles with materials*

*Gas detectors*

*Semiconductor detectors*

*Signal processing*

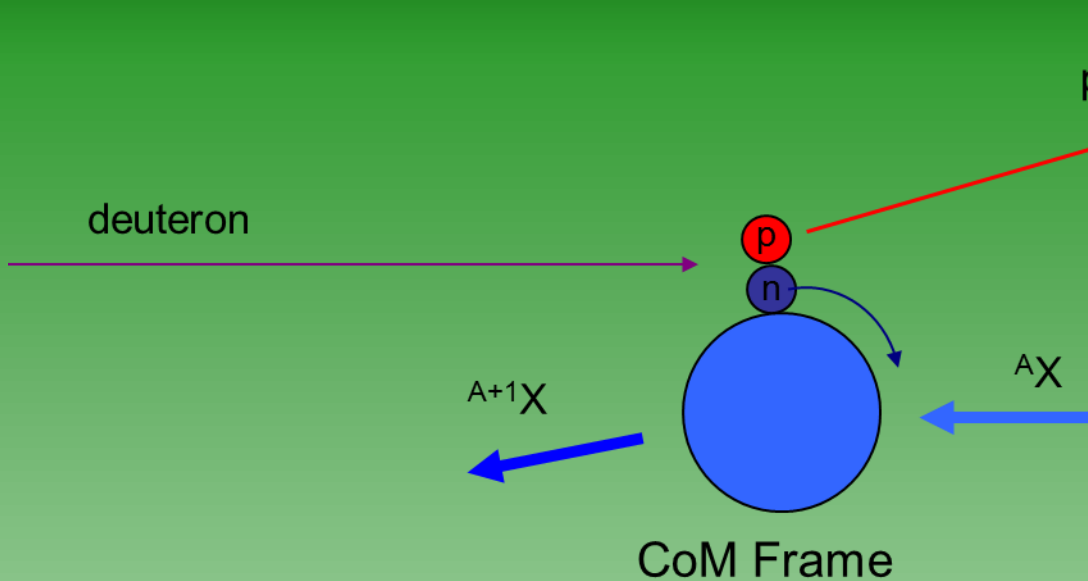
## ***What I will barely touch upon:***

*Scintillator detectors*

*Neutron detectors*

*Transfer reactions*

# Transfer reactions in inverse kinematics

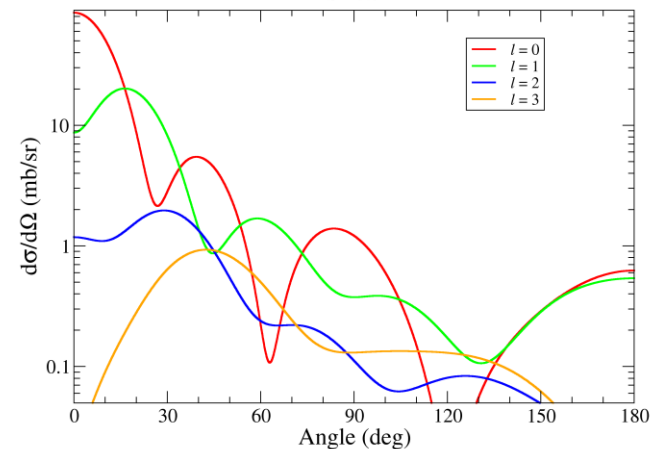
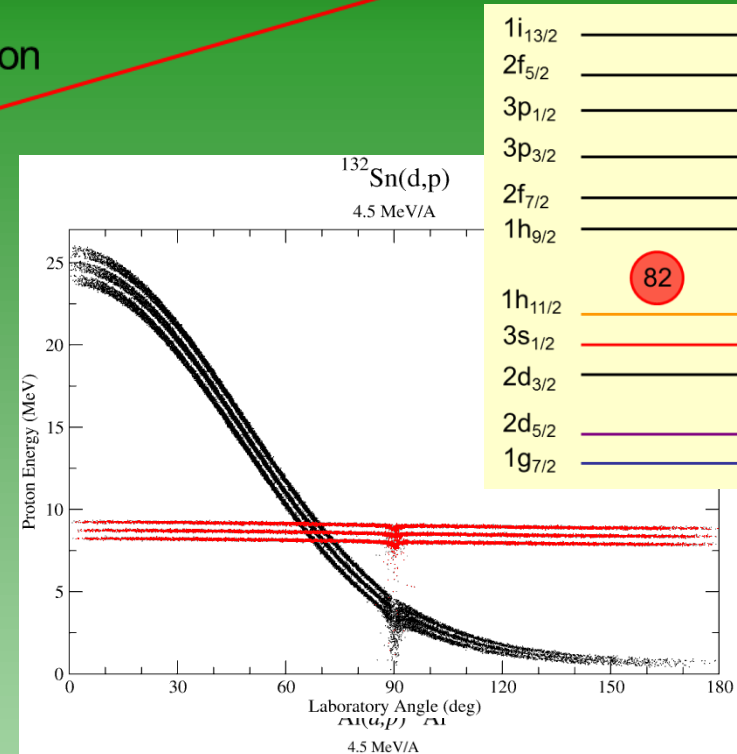


Typically performed and 5-20 MeV/A  
 Selectively probes single-particle (SM) states

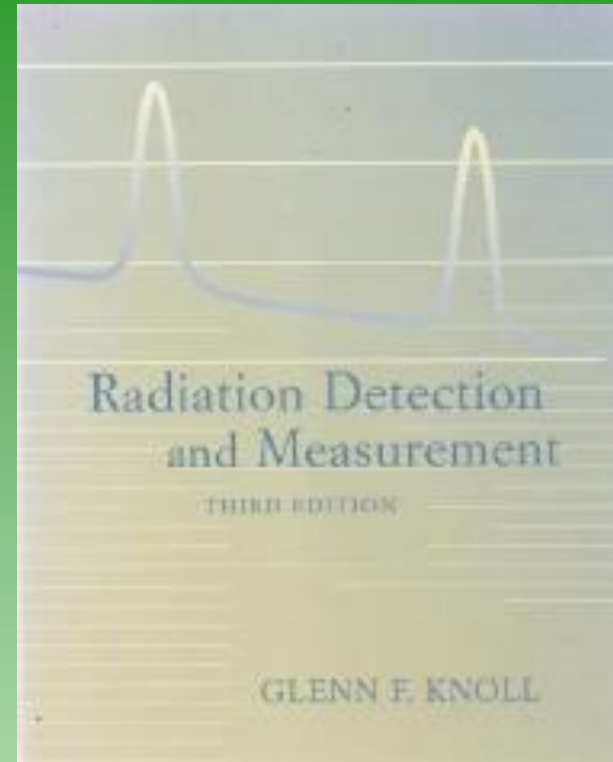
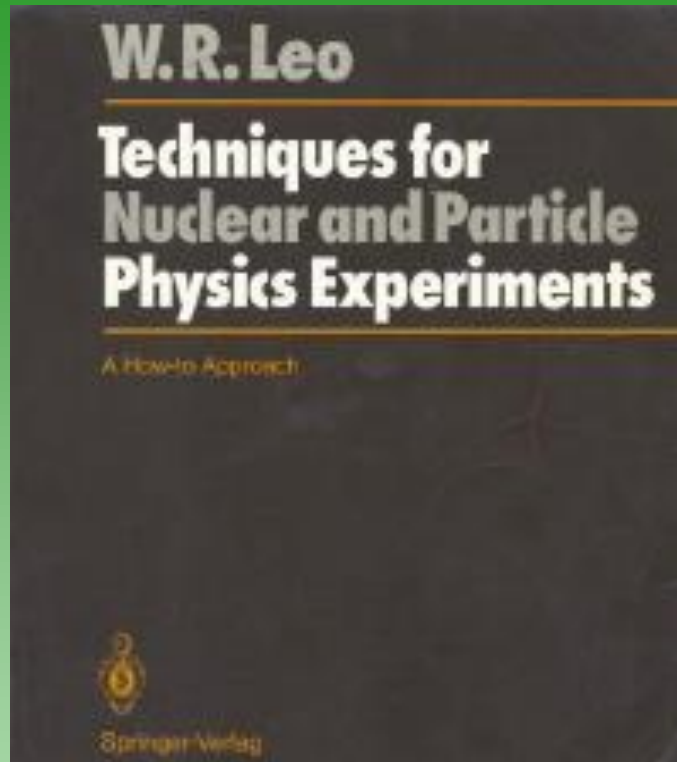
$$\left. \frac{d\sigma}{d\Omega} \right|_{\text{Measured}} = g S_{lj} \left. \frac{d\sigma}{d\Omega} \right|_{\text{DWBA}}$$

Statistical factor

Spectroscopic factor  
 (cf reduced width)



# References



**J.B. Marion and F.C. Young**

***Nuclear Reaction Analysis Graphs & Tables***

**North Holland Publishing Company (1968)**

# Measurement in Nuclear Experiments

*“All measurements are essentially of position, right?”*

(photographic plates)

# Measurement in Nuclear Experiments

*“All measurements are essentially of position, right?”*

(photographic plates)

## Things you can measure:

- Charge (voltage, current)
- Time (frequency)
- Position
- Number

## Things to optimize:

- Resolution
- Efficiency (statistics!)
- Selectivity
- Rates

## Things you can calculate:

- Energy
- Velocity
- Mass
- Momentum
- Charge (nuclear or atomic)
- Probabilities (eg cross sections)

*Many times, improving one of these comes at the expense of another*

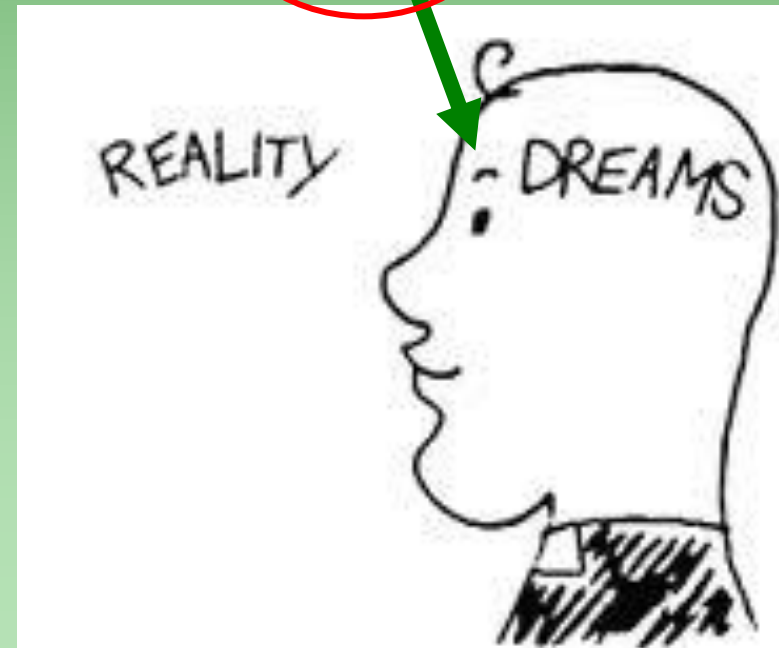
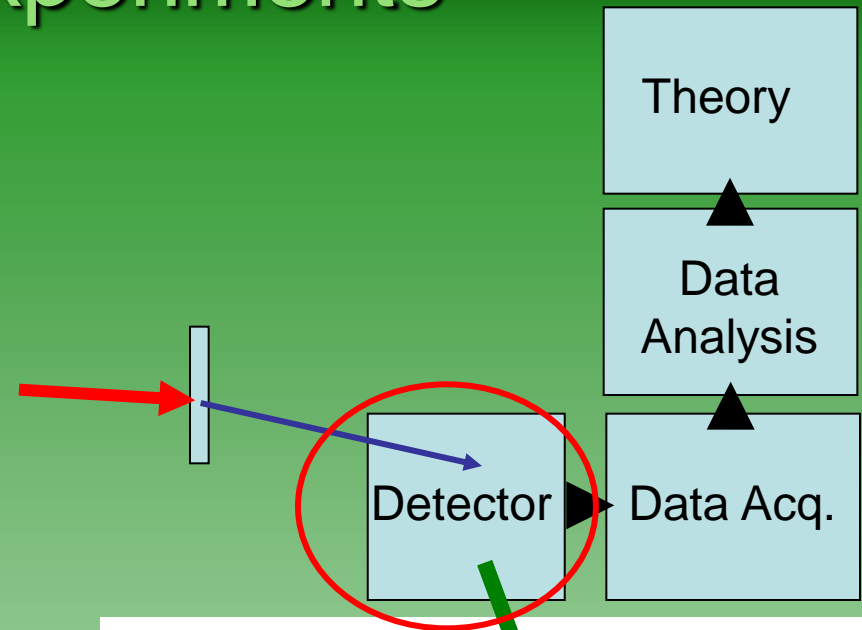
## Things you can infer:

- Quantum numbers ( $\ell, J, \pi, S\dots$ )  
(discrete assignments from continuous data)

*Theory*

# Nuclear Experiments

- Usually involve a beam and a target (sometimes just a source)
- Detectors are our eyes (all observable information comes from them)
- All detectors involve the interaction of radiation with matter
  - Different modes of interaction
  - Different detector types



# Energetic particles in materials



# Energetic charged particles in matter

- Charged particles of energy  $E$  lose energy in passing through material via a number of processes

- Charged (large field), so many small interactions with electrons (large-statistics behaviour)



- The dominant losses are through

- Collisions with atomic electrons (excitation/ionization)

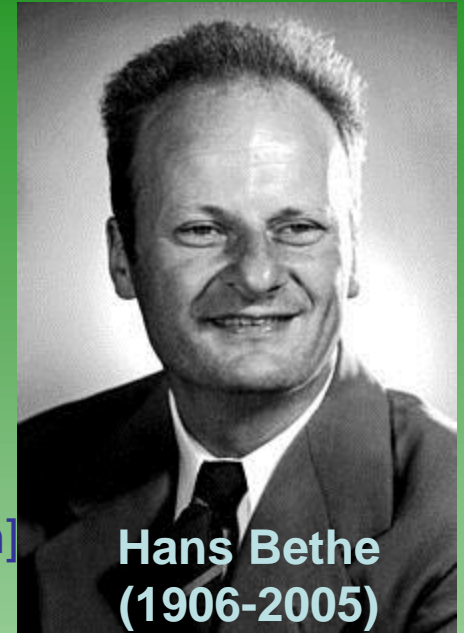
- Nuclear elastic scattering

(consider nucleus of  $10^{-15}$  m, and atom of  $10^{-10}$  m)

- Other interaction forms (nuclear inelastic, nuclear reactions, etc)

# Energetic charged particles in matter

$$E = \frac{1}{2}mv^2 \quad -\frac{dE}{dx} \propto \frac{mz^2}{E}$$



**Hans Bethe**  
(1906-2005)

dominant in the classical limit [40 MeV/A (0.3 c) – <1% deviation]

$$-\frac{dE}{dx} = \frac{4\pi e^4 z^2}{m_0 v^2} nZ \left[ \ln \frac{2m_0 v^2}{I} - \ln \left( 1 - \frac{v^2}{c^2} \right) - \frac{v^2}{c^2} \right]$$

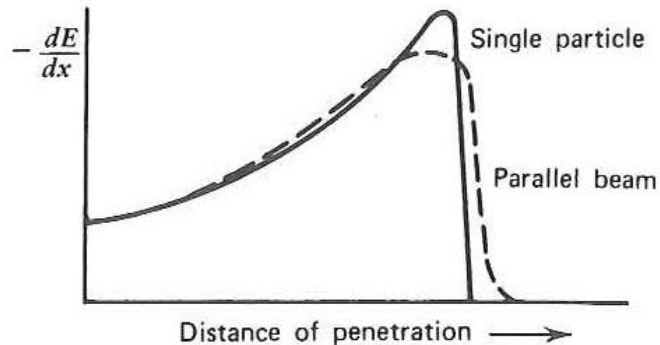
Bethe-Block formula

z – projectile atomic number  
v – projectile velocity  
 $m_0$  – electron mass  
e – electron charge

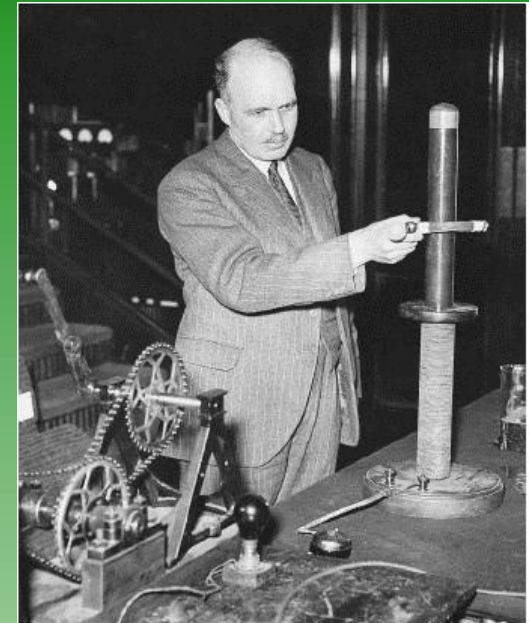
n – target number density  
Z – target atomic number  
nZ – target electron density  
I – average excitation and ionization potential

# Energetic charged particles in matter

Bragg curve



$$-\frac{dE}{dx} \propto \frac{mz^2}{E}$$



**William Henry  
Bragg (1890-1971)**

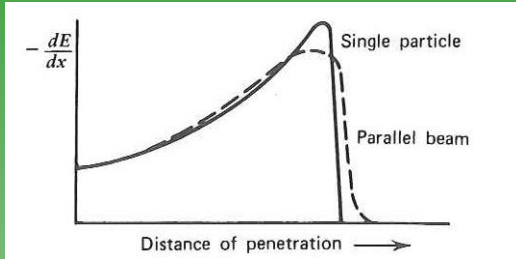
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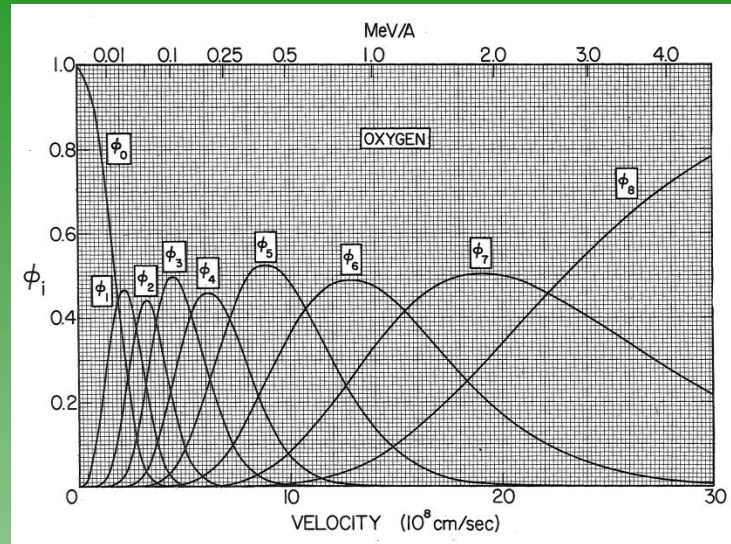
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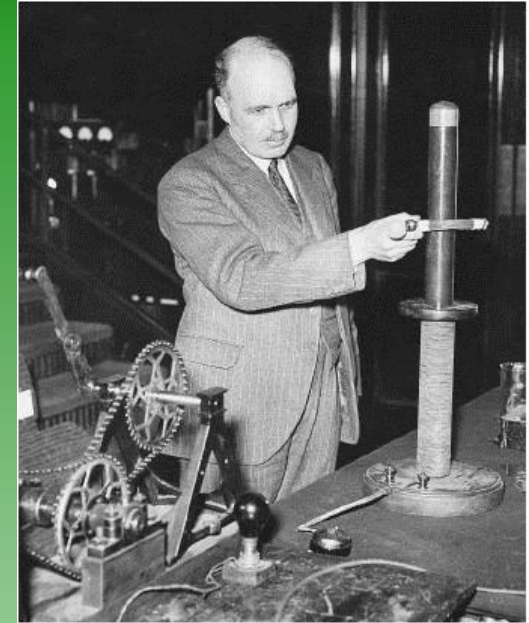
# Energetic charged particles in matter



*Bragg curve*



*Charge state fraction*



**William Henry Bragg (1890-1971)**

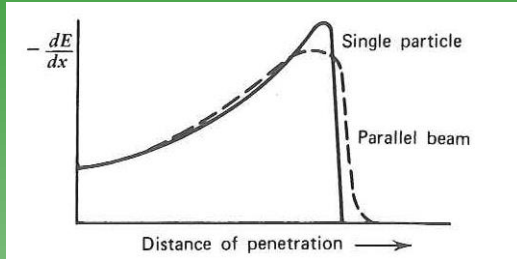
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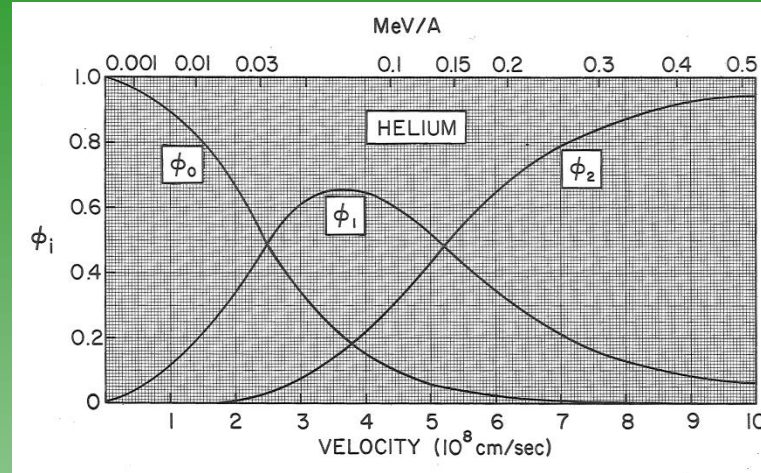
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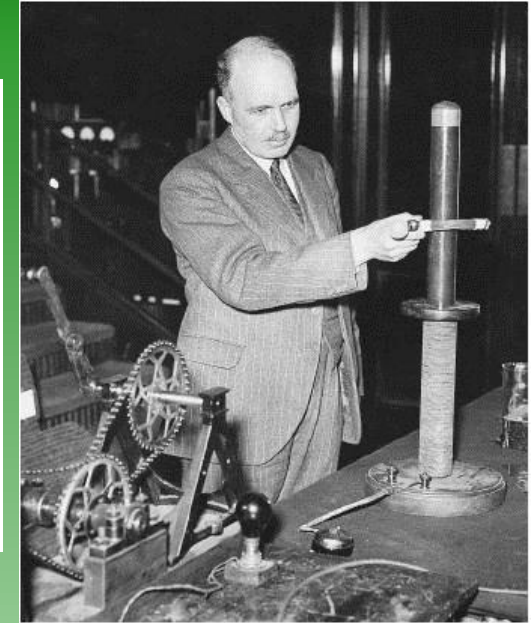
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Charge state fraction



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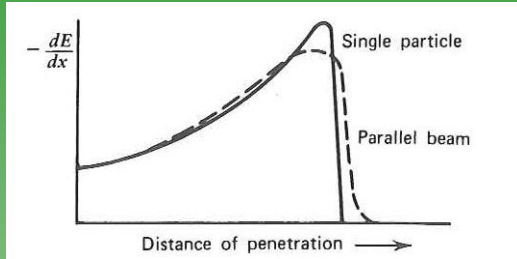
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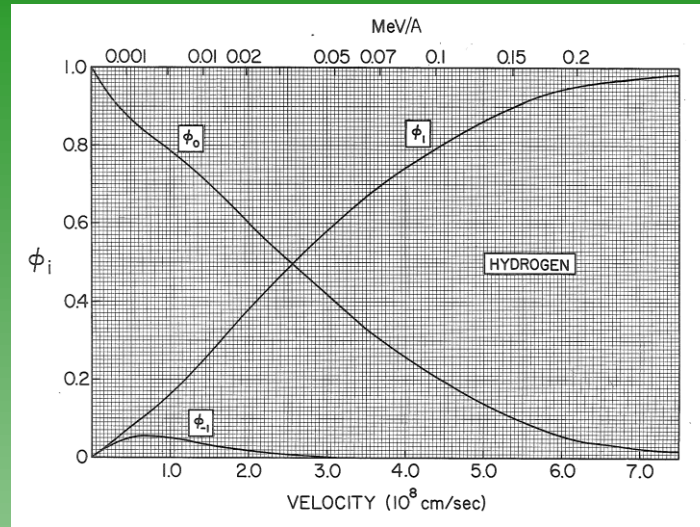
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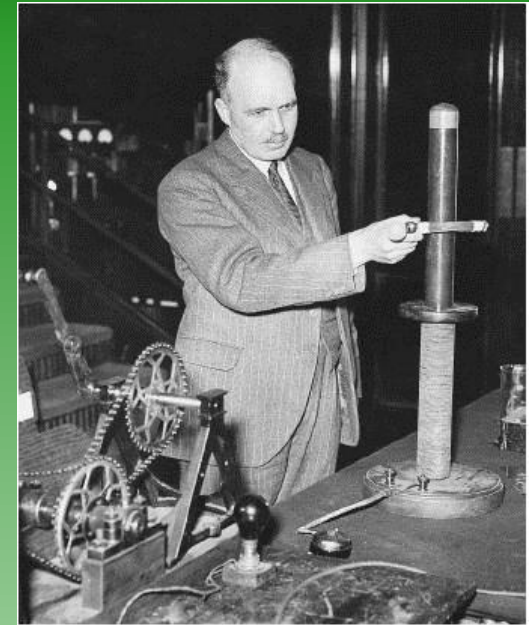
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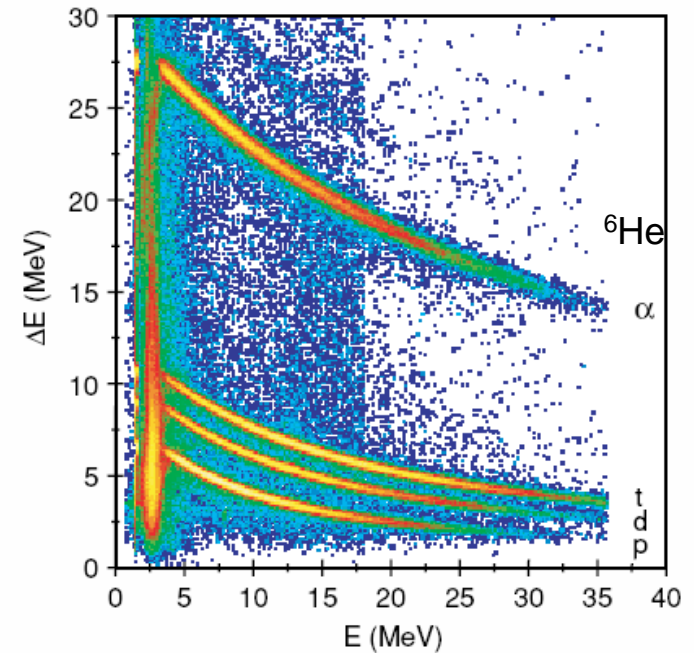
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# Energetic charged particles in matter

$$-\frac{dE}{dx} \propto \frac{mz^2}{E}$$

Charged particle identification with segmented or stacked detectors



$$-\frac{dE}{dx} = \frac{4\pi e^4 z^2}{m_0 v^2} nZ \left[ \ln \frac{2m_0 v^2}{I} - \ln \left( 1 - \frac{v^2}{c^2} \right) - \frac{v^2}{c^2} \right] \quad \text{Bethe-Block formula}$$

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# Photons in matter

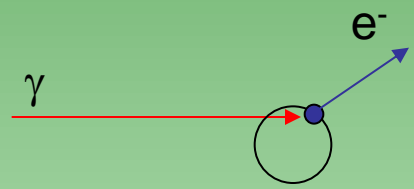


Probabilistic  
(few large interactions)  
Material causes attenuation



## Photoelectric absorption

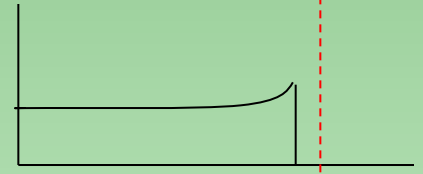
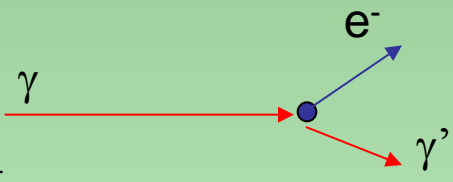
$$E_{e^-} = E_{\gamma} - E_b$$



## Compton scattering

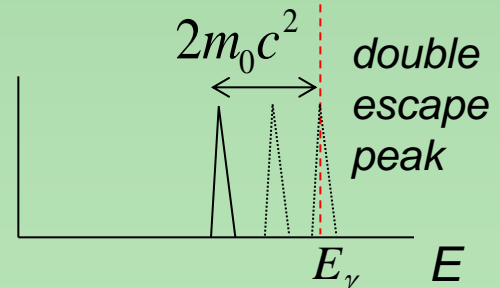
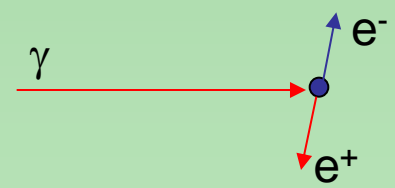
$$E_{e^-} = E_{\gamma} - E_{\gamma'}$$

$$E_{\gamma'} = \frac{E_{\gamma}}{1 + (hv/mc^2)(1 - \cos \theta)}$$



## Pair production

$$E_{e^-} + E_{e^+} = hv - 2m_0c^2$$





# Photons in matter



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## Photoelectric absorption

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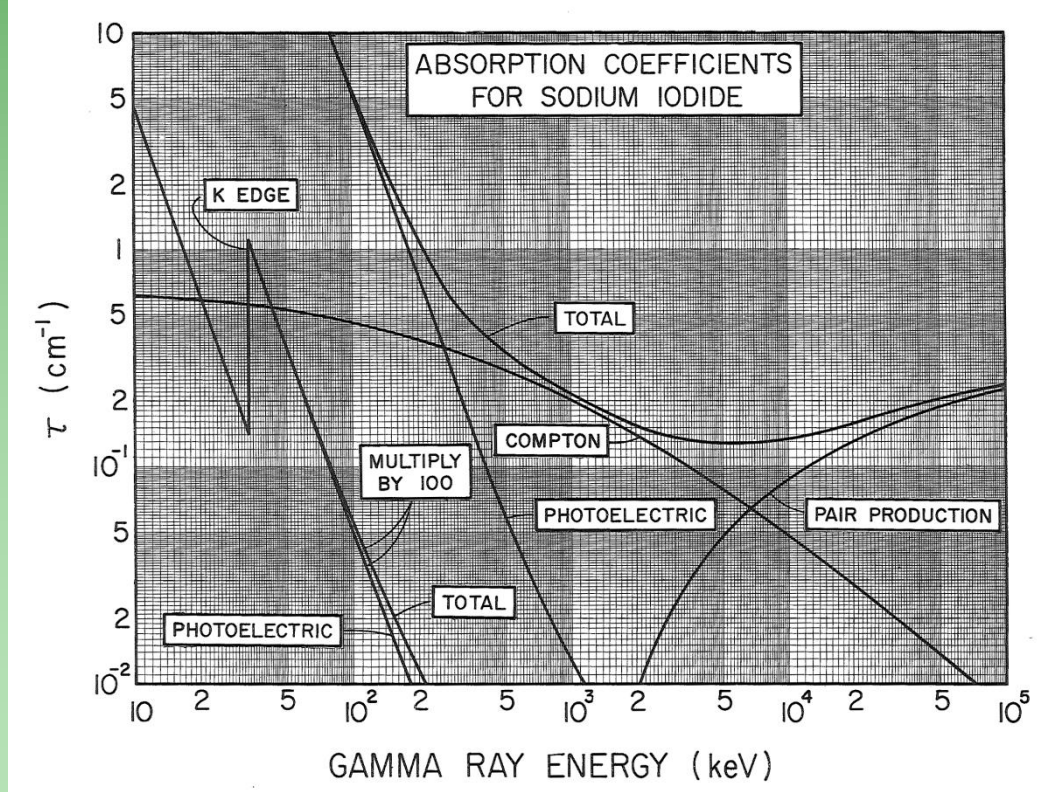
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## Pair production

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# Neutrons in matter

- Most energy lost through nuclear scattering (low cross sections, signal from movement of scattered nucleus)
- Largest energy transfer for proton scattering (hydrogen content important)
- Multiple scattering to thermalize, then other reaction cross sections become significant
  - (n, $\gamma$ ) (n, $\alpha$ ) (n,p) (n,f)
- To detect, can use large signals/cross section reactions (eg  $^3\text{He}$ )
- Difficult to collect all the energy (signal not necessarily proportional to n energy)
- To get energy, use timing for ToF measurement (scintillators)



# Neutrons in matter

- Most energy lost through nuclear scattering (low cross sections, signal from movement of scatterer)
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  - $(n,\gamma)$   $(n,\alpha)$   $(n,p)$
- To detect, can use cross section reactions
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# Neutrons in matter

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# Neutrons in matter

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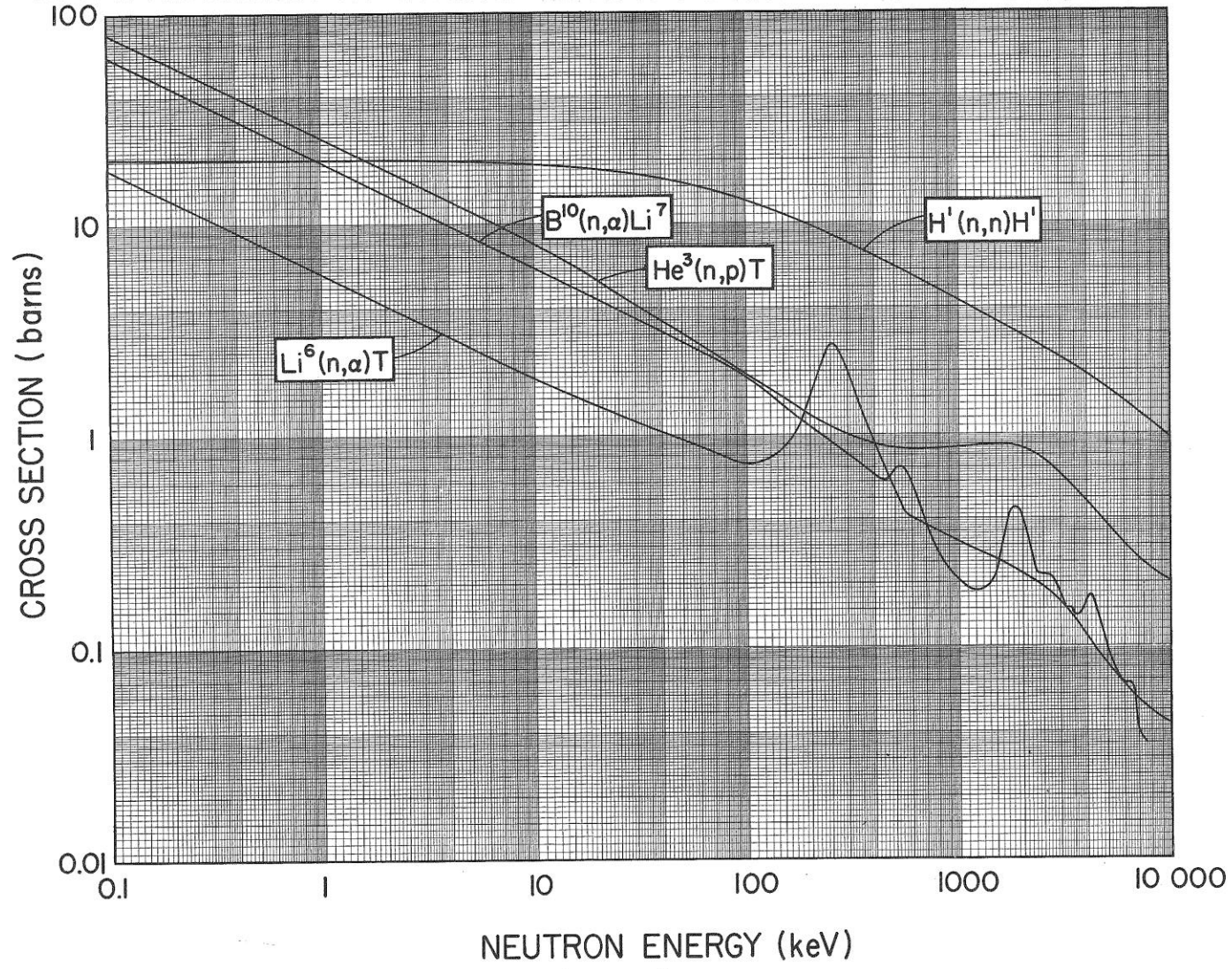
- Large cross section

- Much then become

- To cross

- Different

- To (scintillators)



# Detectors

# Gas detectors

Charged particle measurements (typical)

Energy loss through ionization of the gas molecules

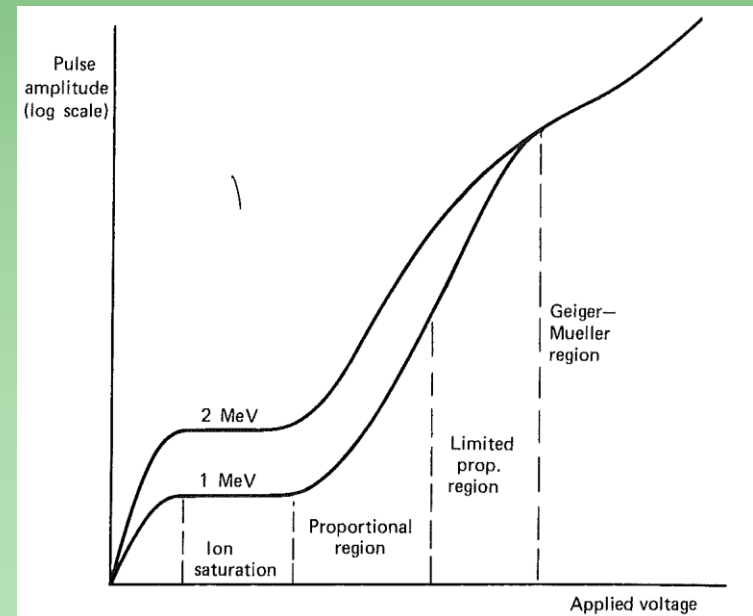
Voltage to separate and collect charge

Electric field (strength, shape) applied determines mode of operation (ionization chamber, proportional counter, GM)

**Pulse** and DC modes

## *Advantages*

- Variable thickness (pressure, can be made thin wrt solids)
- Inexpensive and simple
- Radiation-hard



# Gas detectors

## Signal generation

First ionization potential  
(energy to remove valence  
electron)

$w$ -value = average energy  
per  $e^-$  – ion pair (non-  
ionizing excitations,  
removal of more deeply  
bound electrons, etc)

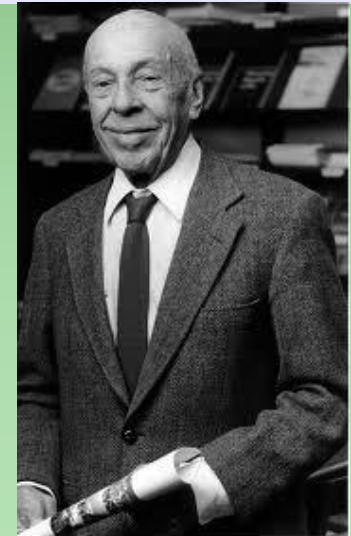
Typically  $\sim 30$  eV per  $e^-$  ion pair

Expect  $\sigma = \sqrt{N} = \sqrt{\frac{E}{w}}$  Find empirically  $\sigma = \sqrt{\frac{FE}{w}}$

*Fano factor*  $F$  accounts empirically for deviation from  
Poisson statistics (limited ways ions can be formed)

$F \sim 0.2$  for gasses,  $\sim 0.1$  for semiconductors

Gas	First ionization potential (eV)	W-value	
		Fast electrons (eV/ion pair)	Alphas (eV/ion pair)
Ar	15.7	26.4	26.3
He	24.5	41.3	42.7
H <sub>2</sub>	15.6	36.5	36.4
N <sub>2</sub>	15.5	34.8	36.4
Air		33.8	35.1
O <sub>2</sub>	12.5	30.8	32.2
CH <sub>4</sub>	14.5	27.3	29.1



Ugo Fano (1912-2001)



# Gas Detectors

## *Signal collection*

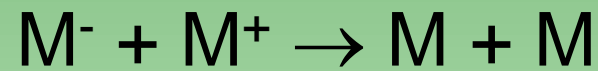
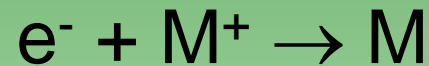
### *Diffusion*

(spreading of the spatial charge distribution)

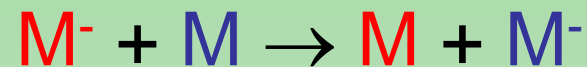
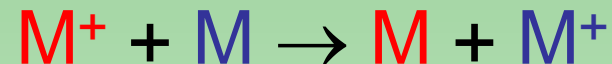
### *Electron attachment*



### *Recombination*



### *Charge transfer*



Matters if gas mixture is used

# Ionization Chambers

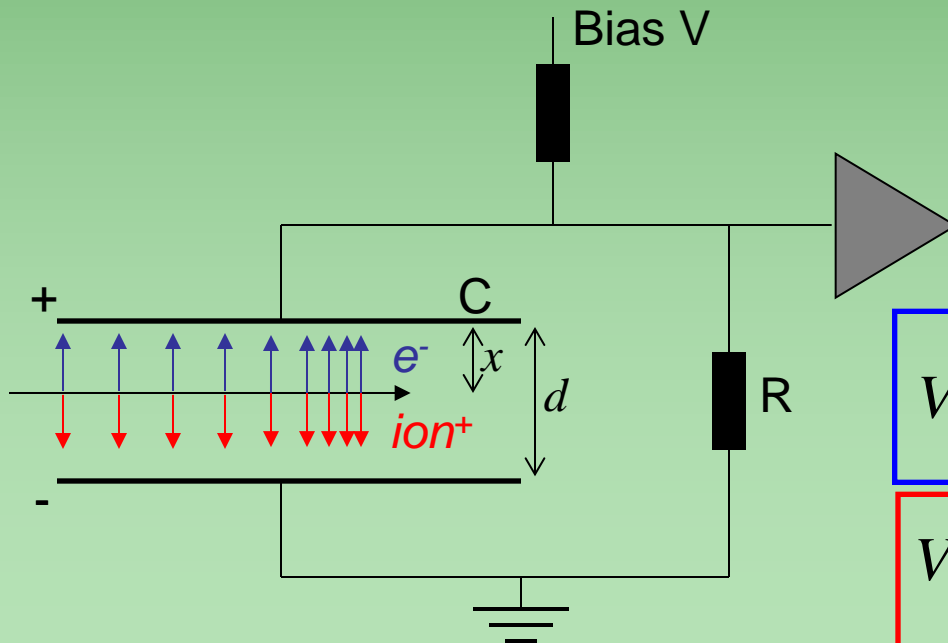
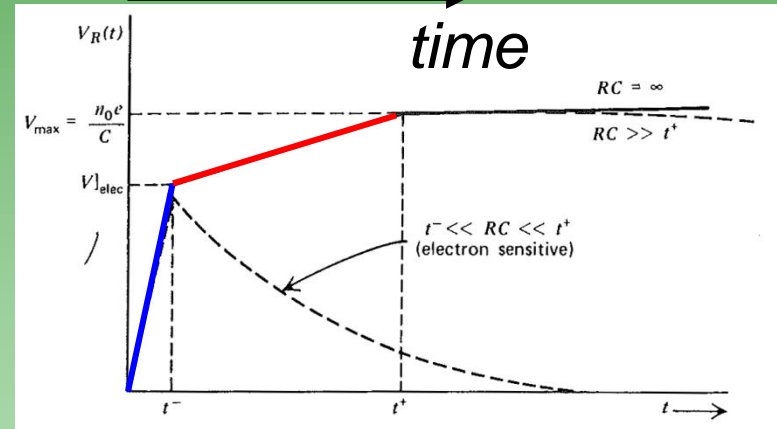
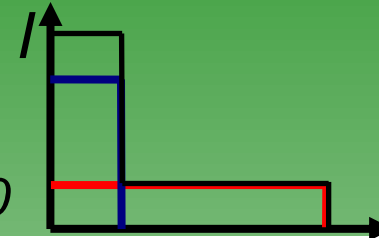
Drift velocity for ions  $v = \frac{\mu \mathcal{E}}{p}$

$\mu$  = mobility (gas dependent quantity)  
 $\mathcal{E}$  = electric field strength ( $\sim 10^4$  V/m)  
 $p$  = gas pressure

$\mu \sim 1 \times 10^{-4}$  m<sup>2</sup> atm/V.s for ions of most gasses

*Electrons are typically faster by a factor of  $\sim 1000$*

Signal induced by movement of charge in  $E$



$$V_R = \frac{n_0 e}{dC} (v^- + v^+) t$$

$$V_{elec} = \frac{n_0 e}{dC} x$$

$$V_R = \frac{n_0 e}{dC} (v^+ + x) t$$

$$V_{max} = \frac{n_0 e}{C}$$

# Ionization Chambers

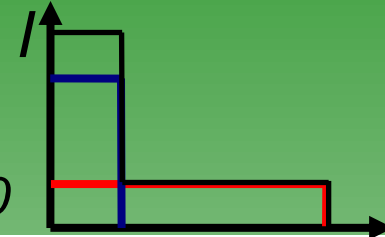
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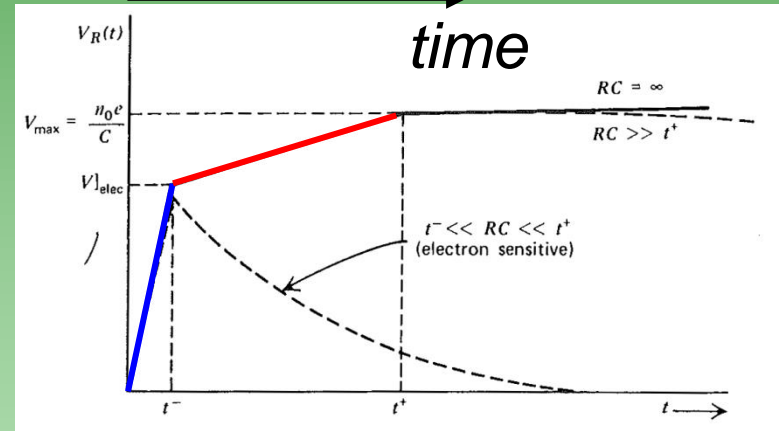
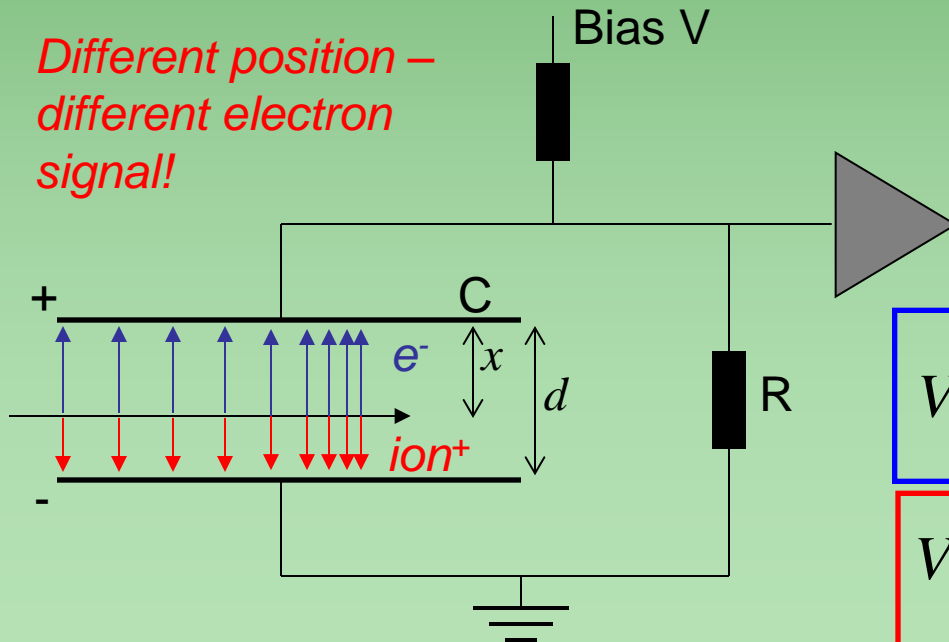
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*Different position – different electron signal!*



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# Gridded Ionization Chambers



Scanned at the American Institute of Physics

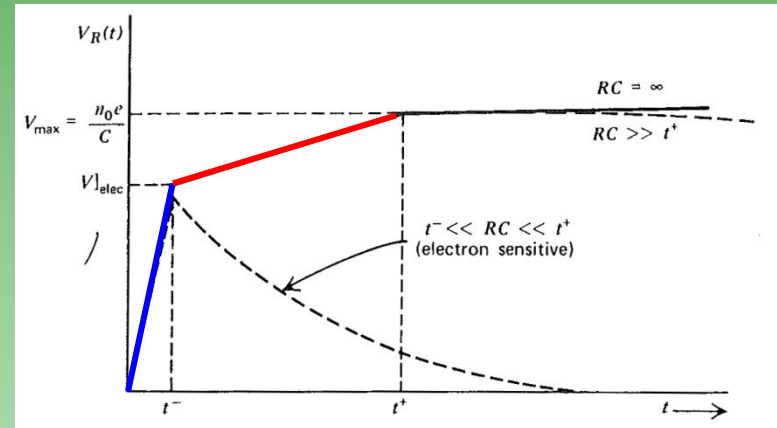
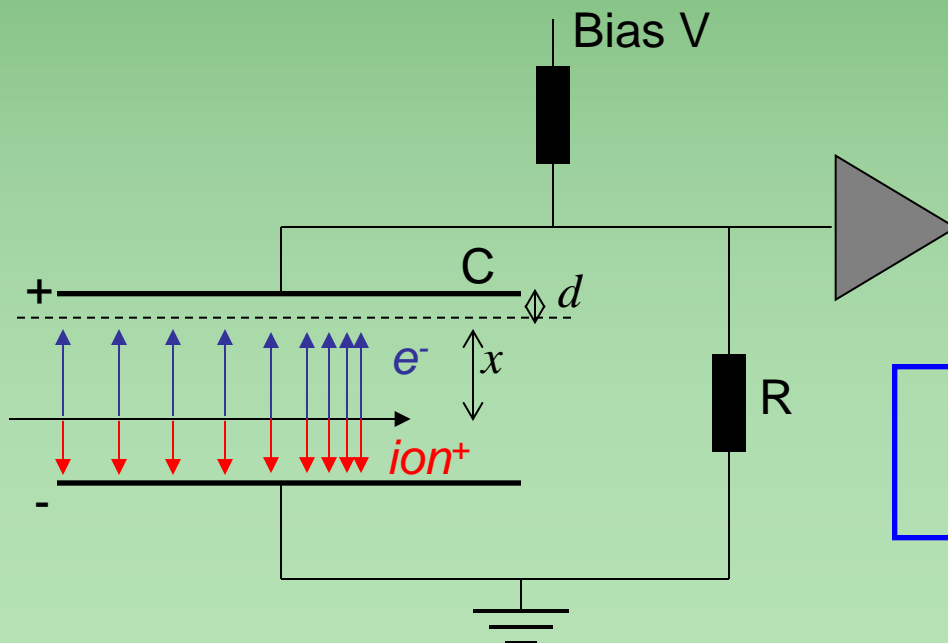
Otto Robert Frisch  
(1904-1979)

Frisch grid incorporated to shield anode from the moving electrons until they get close

Anode is sensitive to movement of charge over a fixed distance

Removes position dependence of electron signal

Short  $\tau$  – high rate



$$V_R = \frac{n_0 e}{dC} v^- t$$

$$V_{\max} = \frac{n_0 e}{C}$$

# Ionization Chambers

## Segmented IC

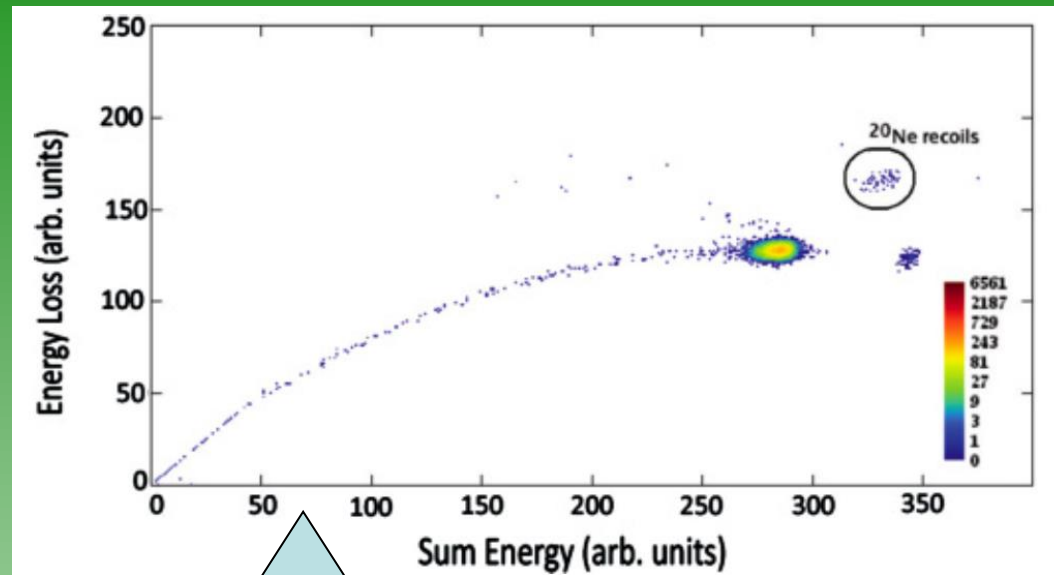
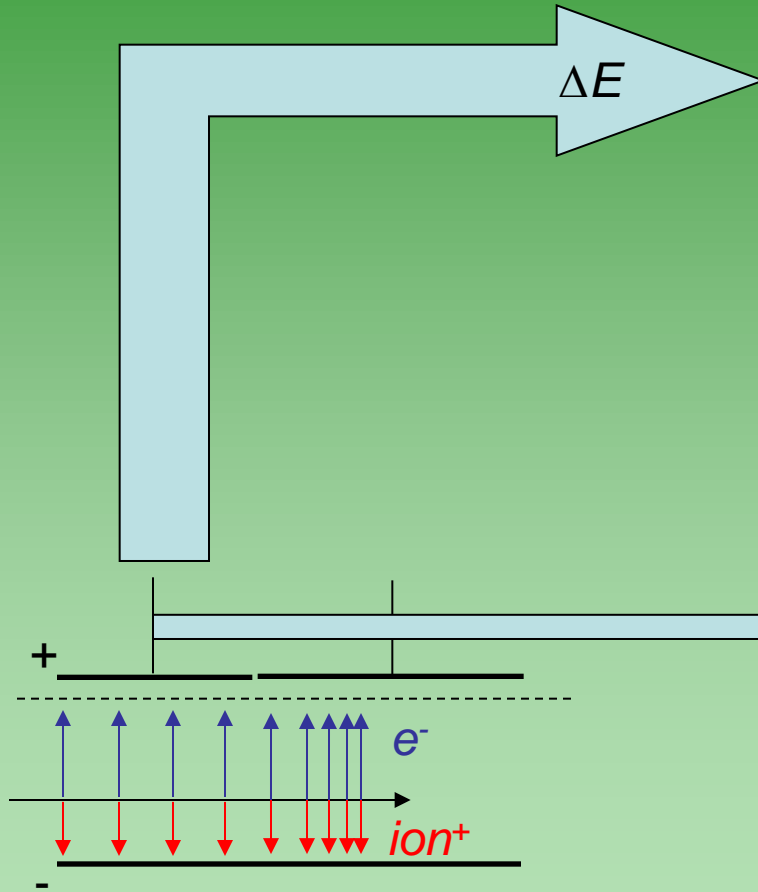


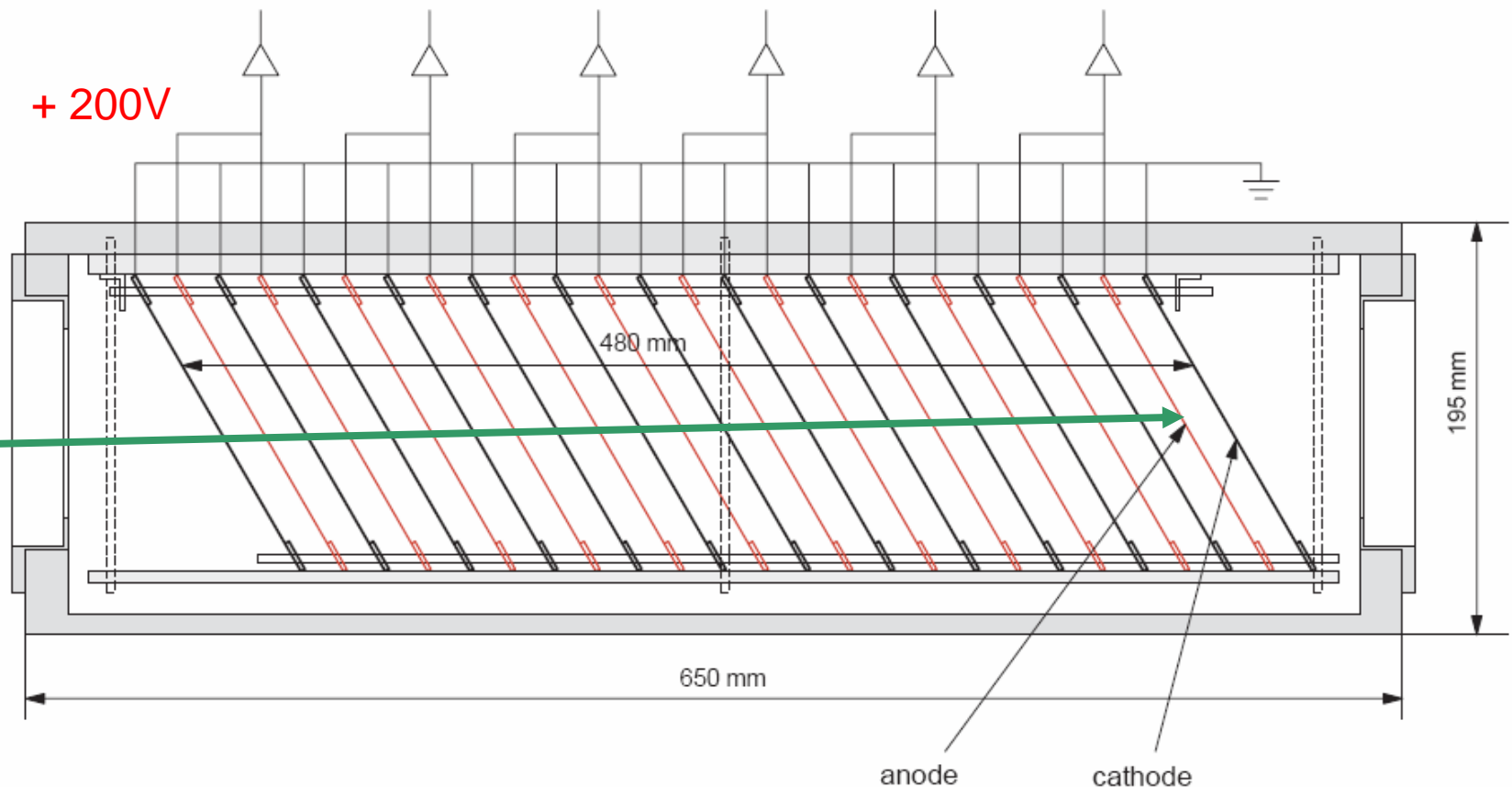
FIG. 5. (Continued) Ionization chamber spectrum for the  $^{17}\text{O} + ^{20}\text{Ne}$  scattering measurement with Ne recoils indicated; performed to verify the location of  $^{18}\text{Ne}$  recoils during the  $^{17}\text{F}(p,\gamma)^{18}\text{Ne}$  experiment.

Particle ID from  $\Delta E + E$

Counting rate limited by response time of IC (high  $10^4$  pps)

# Ionization Chambers

## Tilted Electrode Gas Ionization Chamber

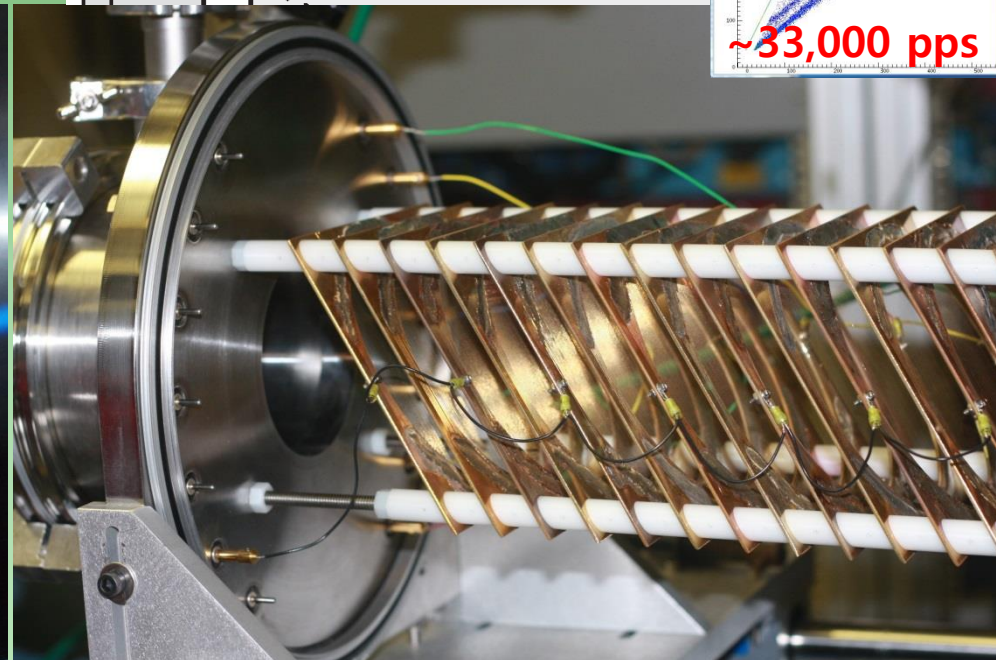
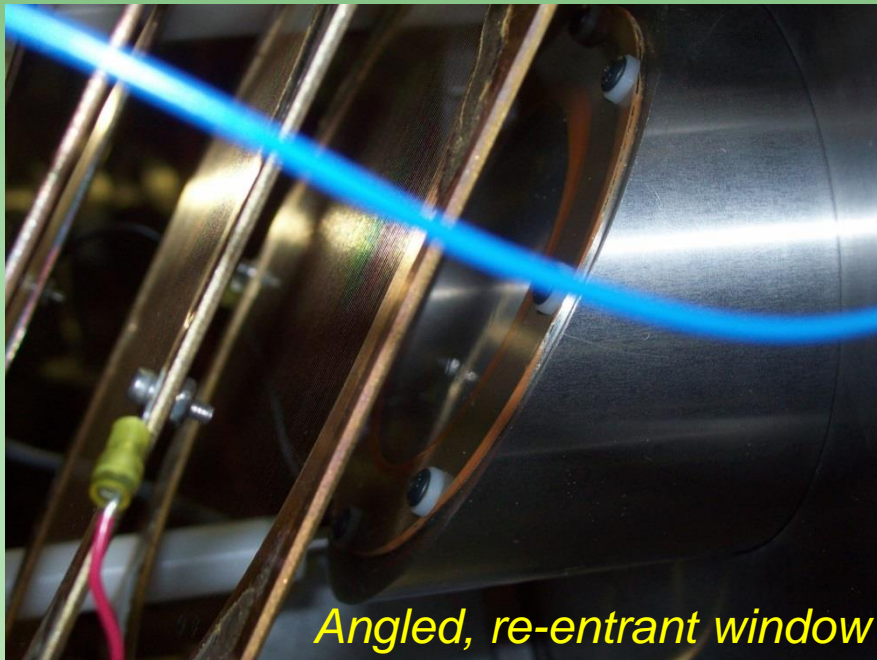
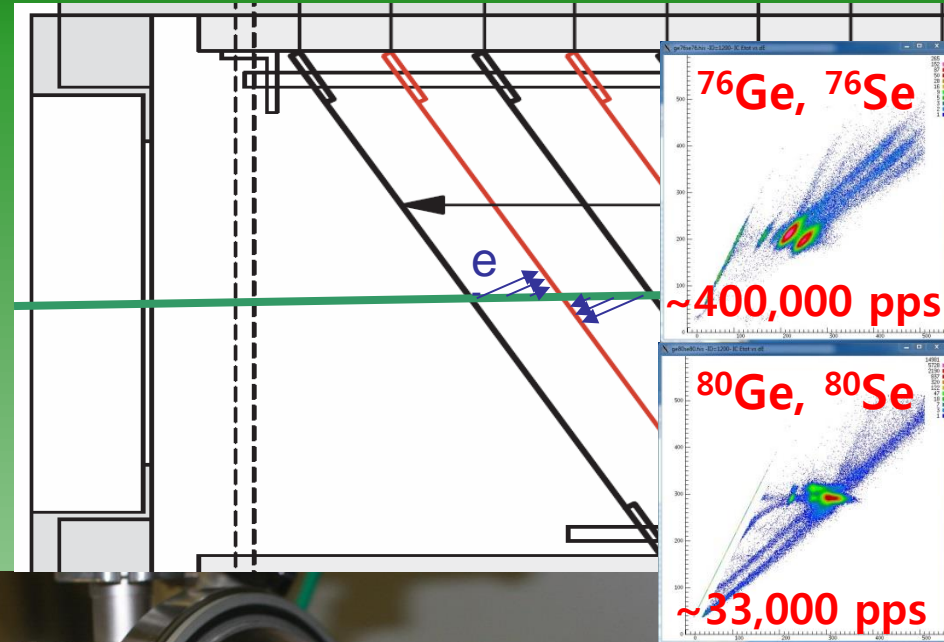


# Ionization Chambers

*Design used for beam-like detection for:*

- ORRUBA
- ANASEN
- HELIOS
- GODDESS
- (TIGRESS)

- Position dependence minimized
- Small distance – fast collection times
- Easy to adjust anode combinations to optimize  $\Delta E - E$



# Proportional Counters

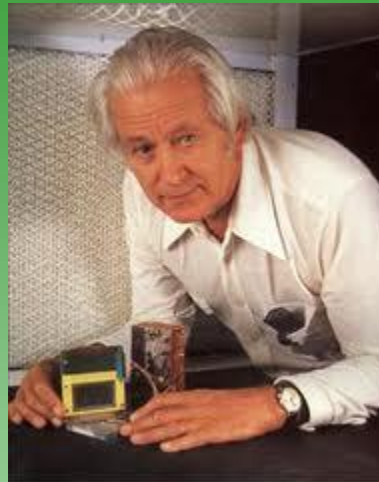
Sufficient voltage to cause secondary ionization ( $10^6$  V/m)

Amplification of signal

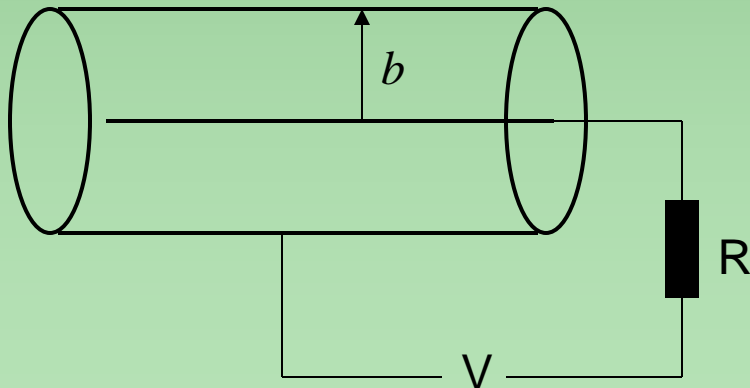
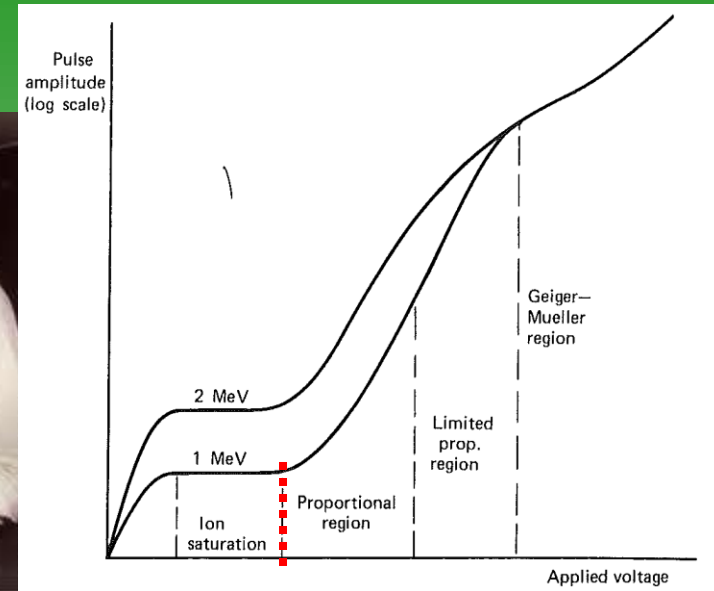
Wires used to limit the proportional region to a small volume (reduces position-dependence of gain)

Basic cylindrical configuration

Multi-wire proportional counters can be made in various geometries to cover large areas (tracking detectors)

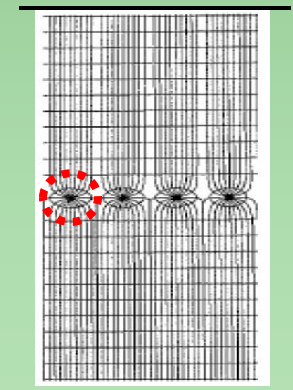


**Georges Charpak**  
(1924-2010)



$$\mathcal{E}(r) = \frac{V}{r \ln(b/a)}$$

$a =$  wire radius



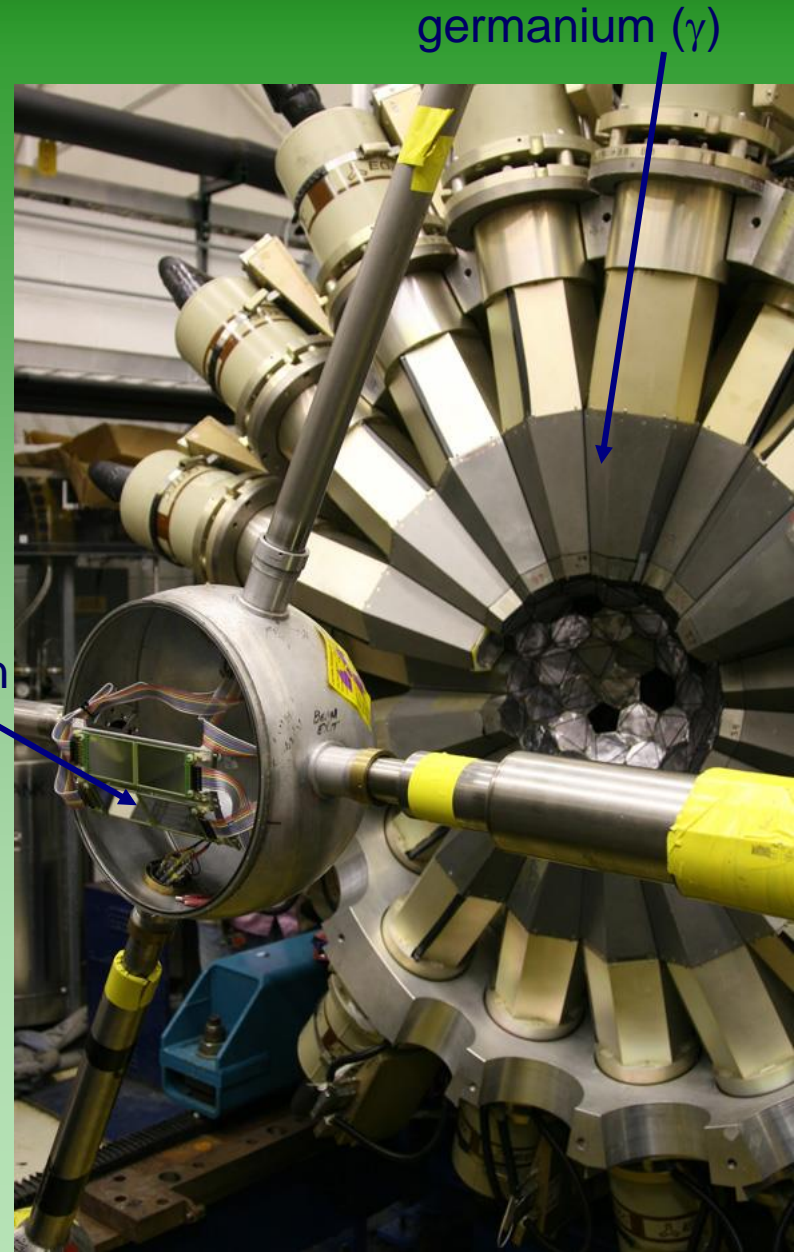


# Semiconductor detectors

- Charged particle and photons
- Large arrays, in various geometries
- High resolution
- Compact (Si)
- Delicate (esp radiation damage for stopping detectors)



silicon  
(charged particle detectors)



germanium ( $\gamma$ )

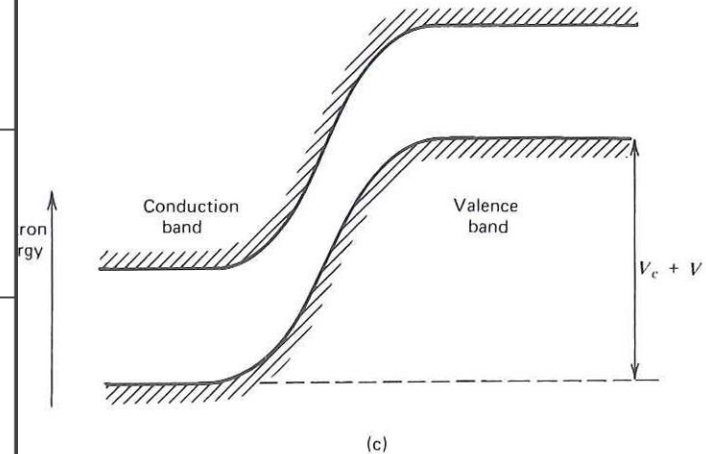
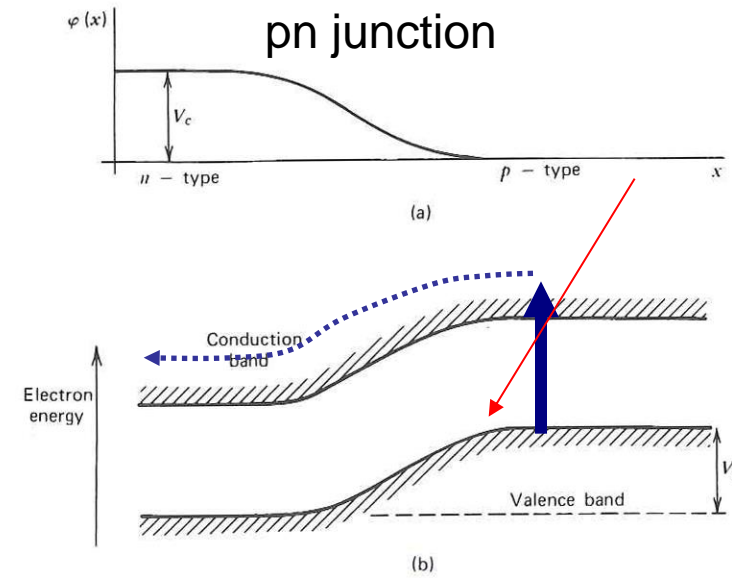
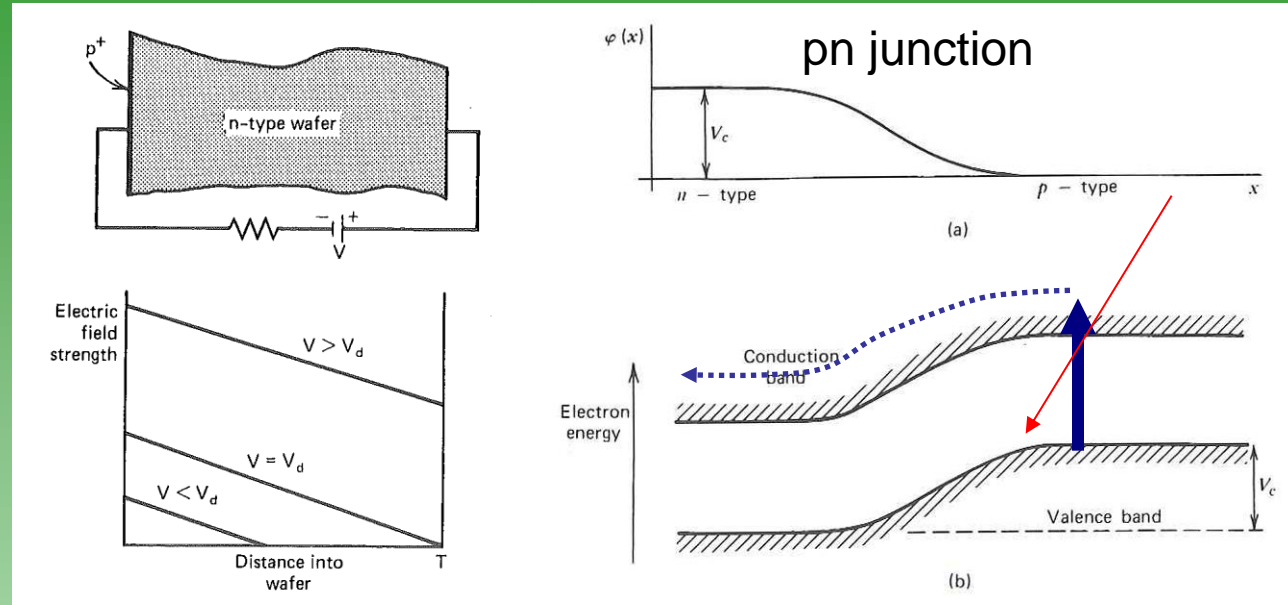
# Semiconductor detectors

Active in depletion region around a pn junction

Energy loss through electron excitation from valance to conduction bands

For gammas,  $Z$  is important

[Recall  $\sim 30$  eV per e<sup>-</sup> ion pair for gasses]



material	Atomic number	density	gap	Energy per e-h pair	Temp	Comments
Si	14	2.33 g/cm <sup>3</sup>	1.1 eV	3.62 eV	300 K room	thin
Ge	32	5.32 g/cm <sup>3</sup>	0.7 eV	2.96 eV	77 K LN2	Excellent E large Expensive

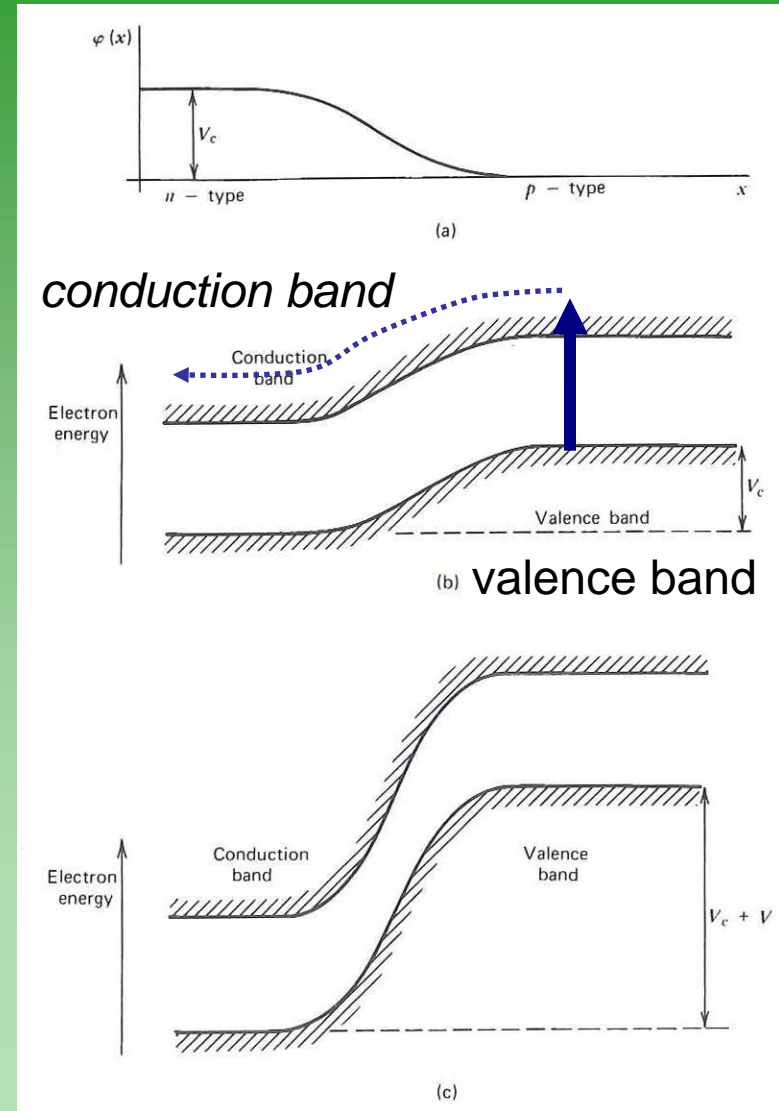
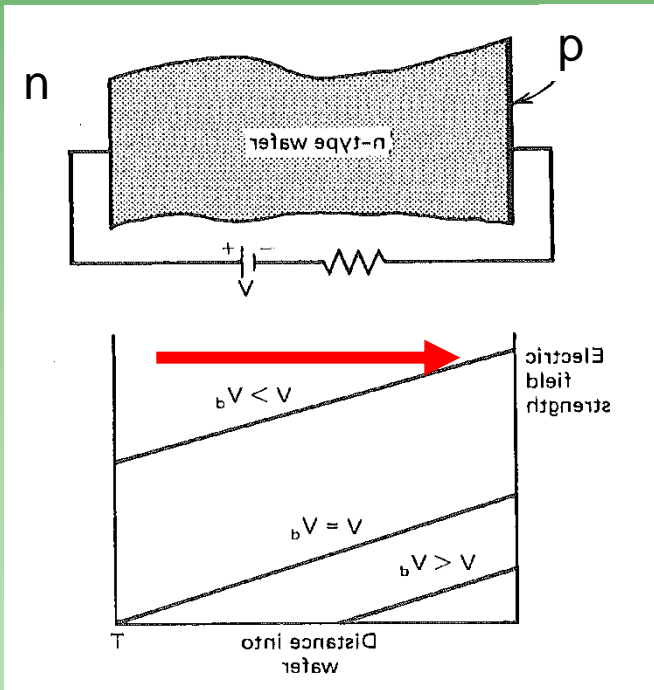
# Semiconductor detectors

Leakage currents (thermal effects):

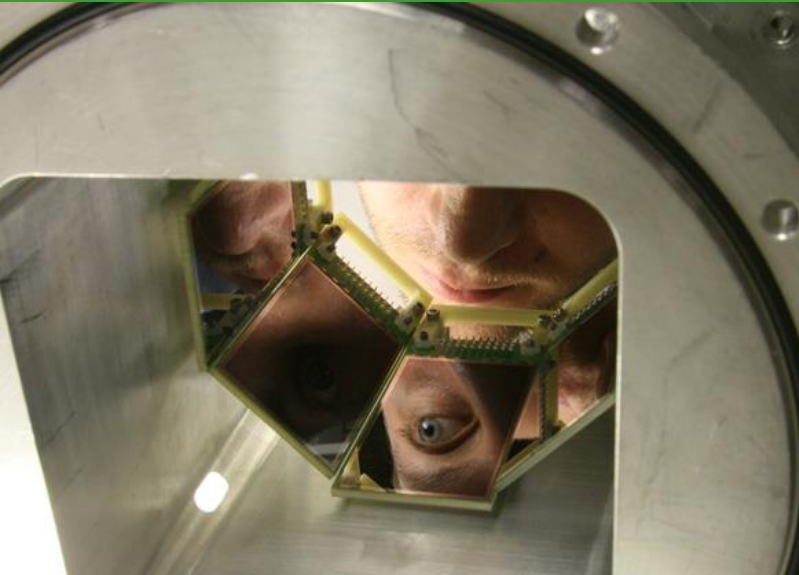
Diffusion current 

Drift current 

Surface leakage



# Silicon detectors



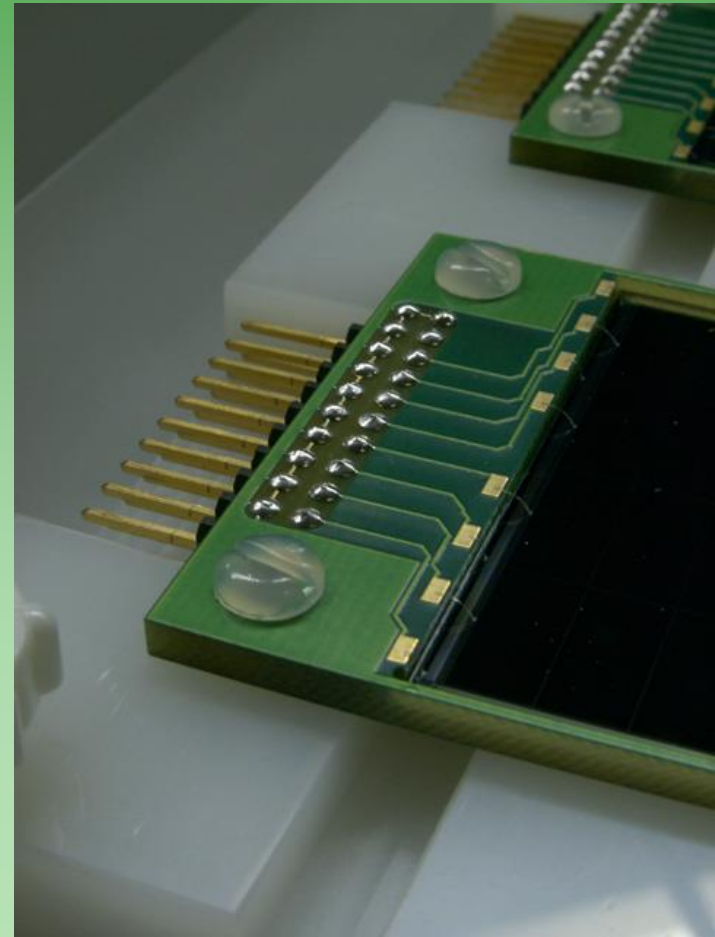
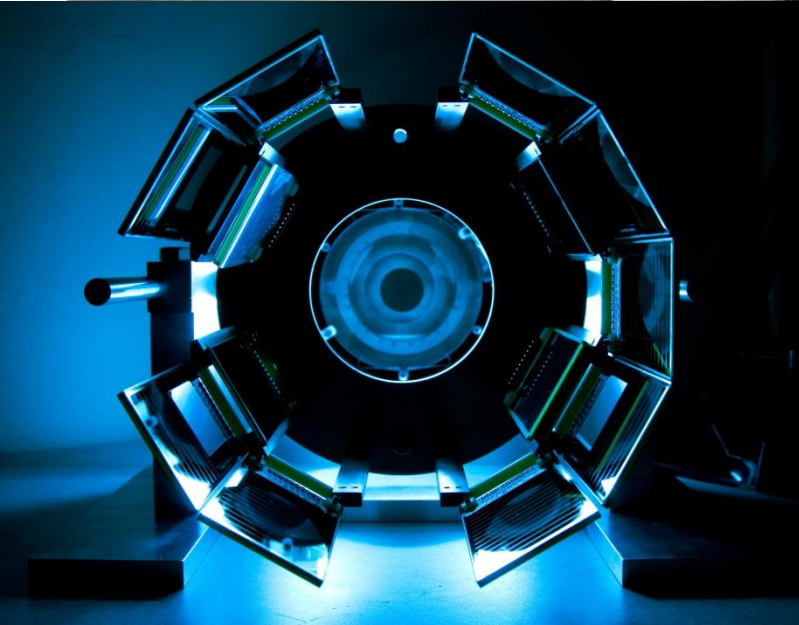
Thin particle detectors

Highly segmented

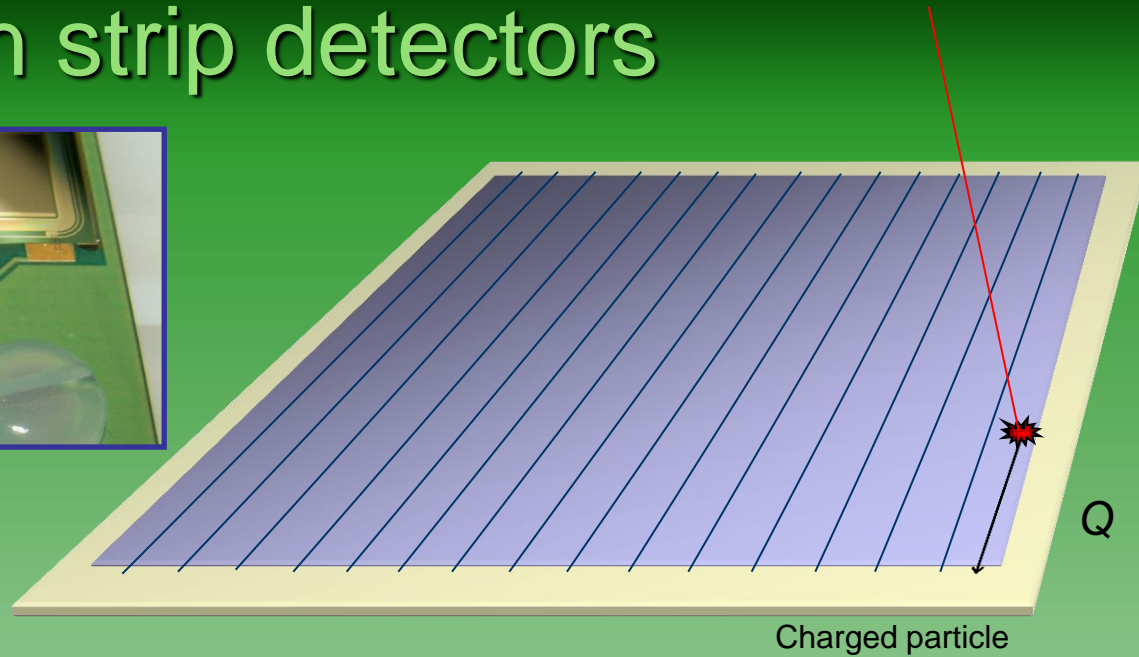
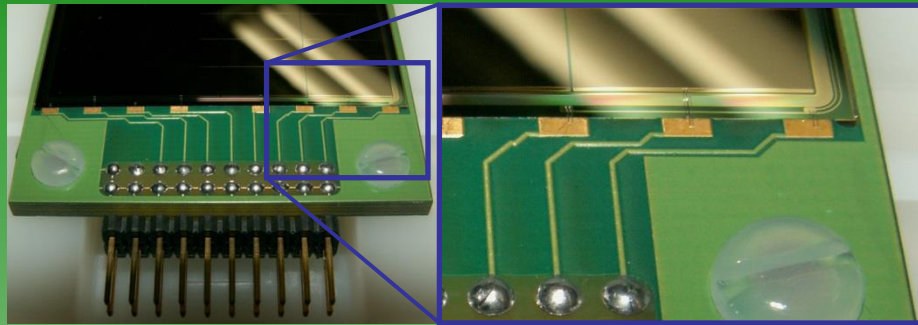
Range of thicknesses ( $\sim 20 \mu\text{m}$  –  $\sim 2 \text{mm}$ )

Large area

Room temp  
(performance  
gains with  
cooling)

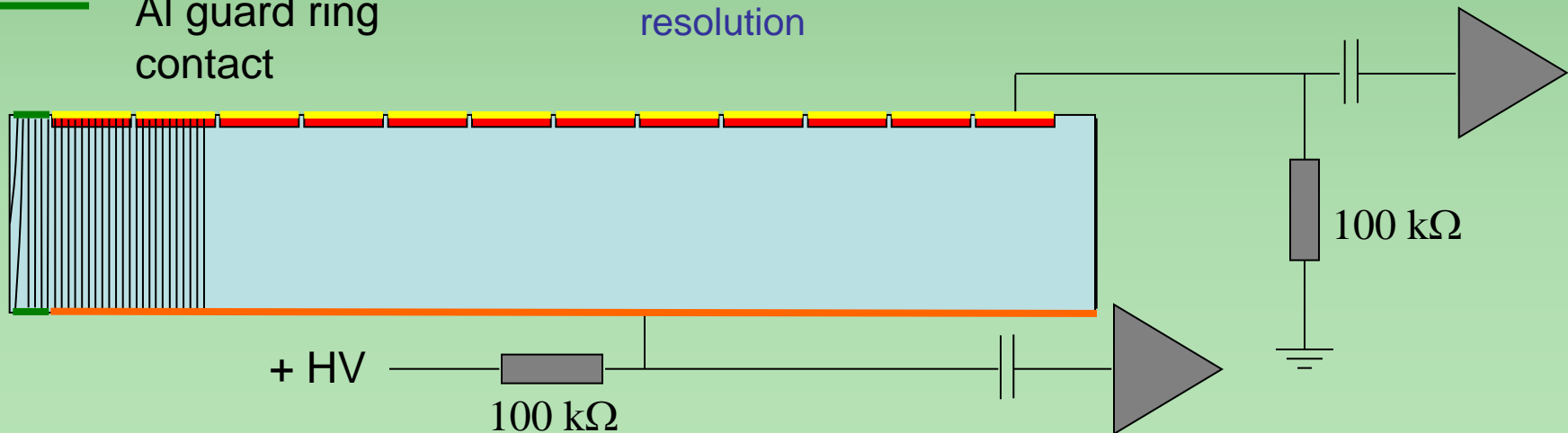


# Silicon strip detectors

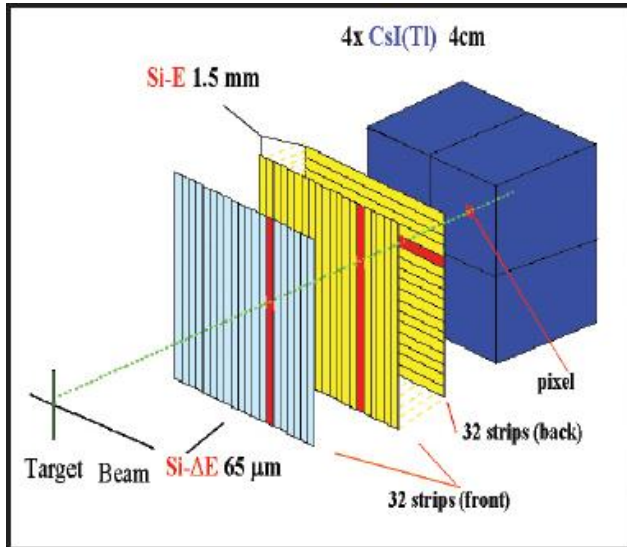


- Energy =  $Q$
- Position = strip location
- Many channels required to achieve high spatial resolution

-  Al contact
-  p-type Si
-  residual n-type Si
-  Al contact
-  Al guard ring contact



# Example silicon strip detector arrays

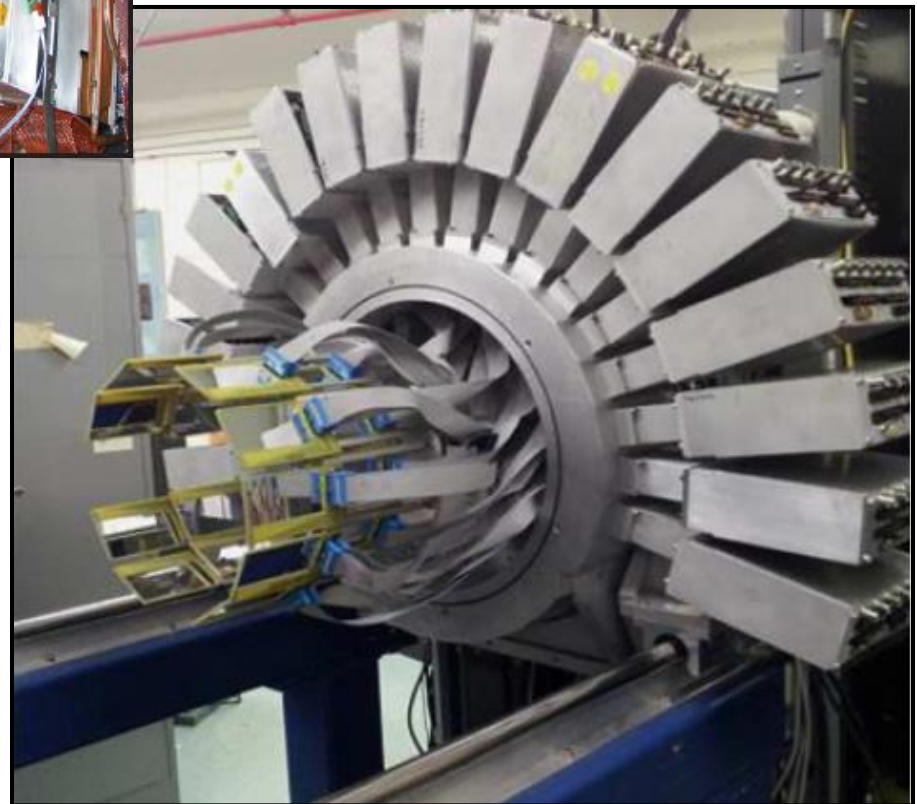


## HiRA

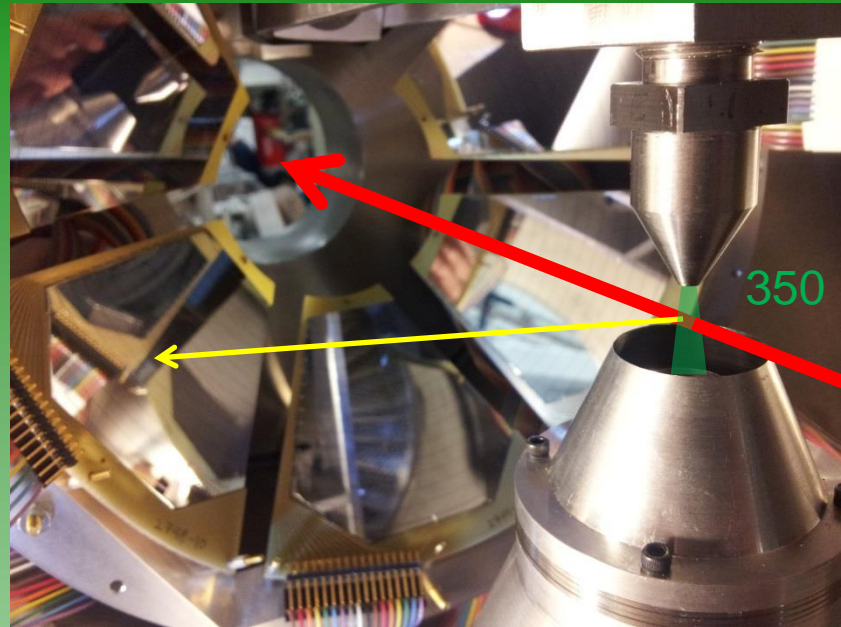
Wall array of Si-Si-CsI telescopes  
DSSD (32x32 2mm strips)  
Instrumented with ASICs  
(~100 ch per telescope)  
NSCL, WashU, Indiana U, INFN

## SuperORRUBA

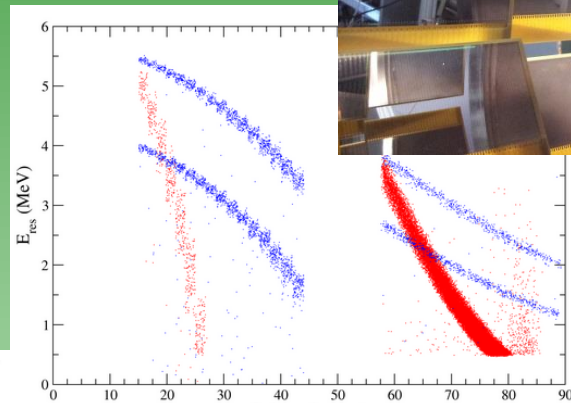
Barrel array of Si detectors  
DSSD 75mm x 40 mm  
64 x 1.3mm strips, 4 x 10mm strips  
Instrumented with ASICs  
(68ch per detector)  
ORNL, Rutgers, WashU, UTK, TTU, LSU



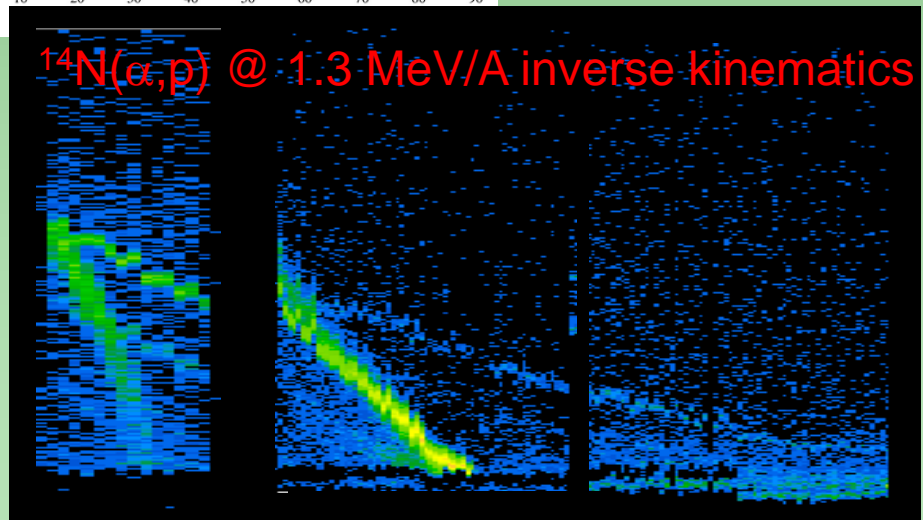
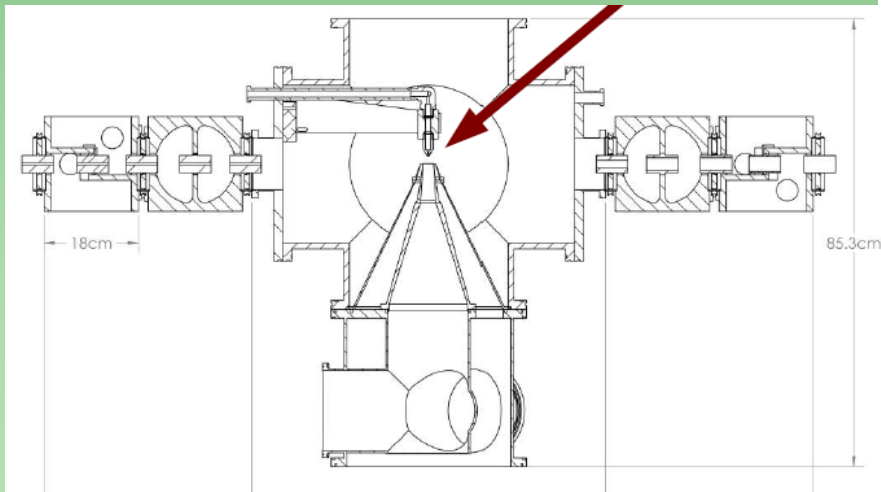
# JENSA + superORRUBA – commissioning at ReA3



Proof of principle for  $(\alpha, p)$  X-ray burst experiments



No 90° shadowing

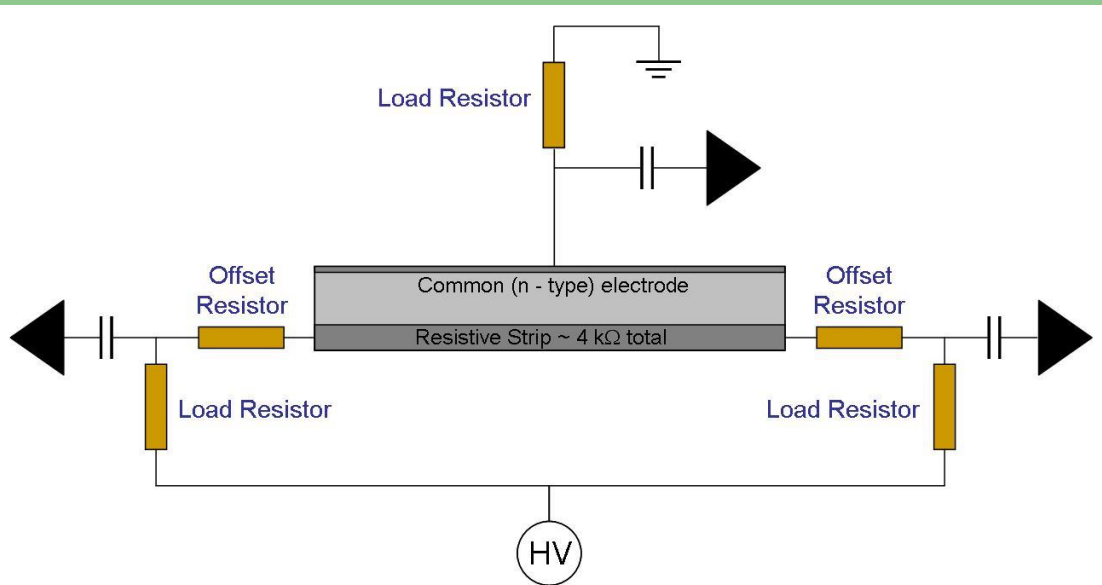
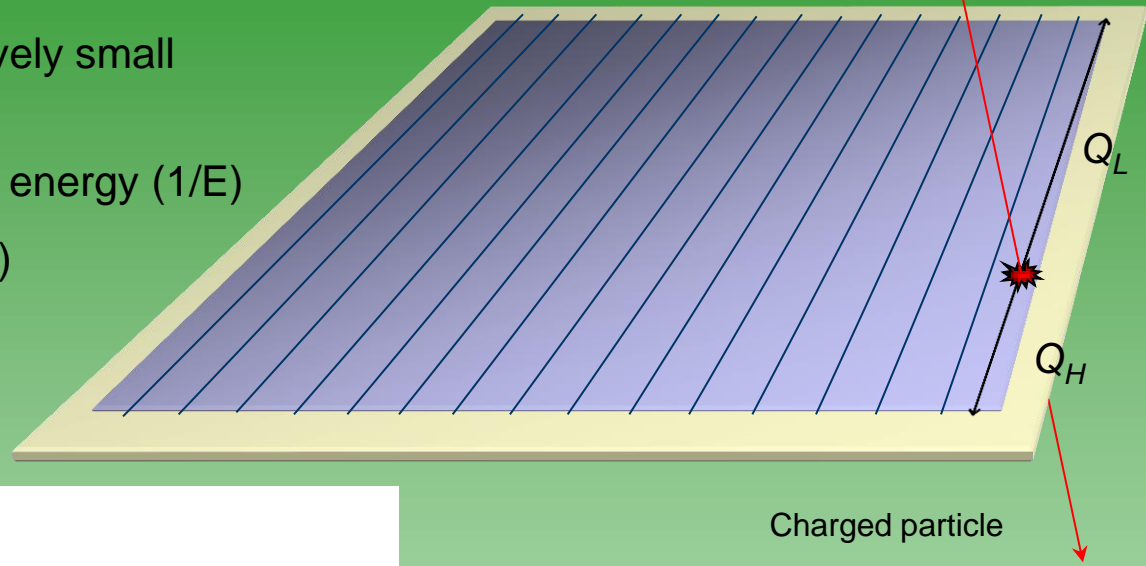


Feb 2016, May 2016  $^{34}\text{Ar}(\alpha, p)$

# Resistive silicon strip detectors

## Resistive strip Si detectors

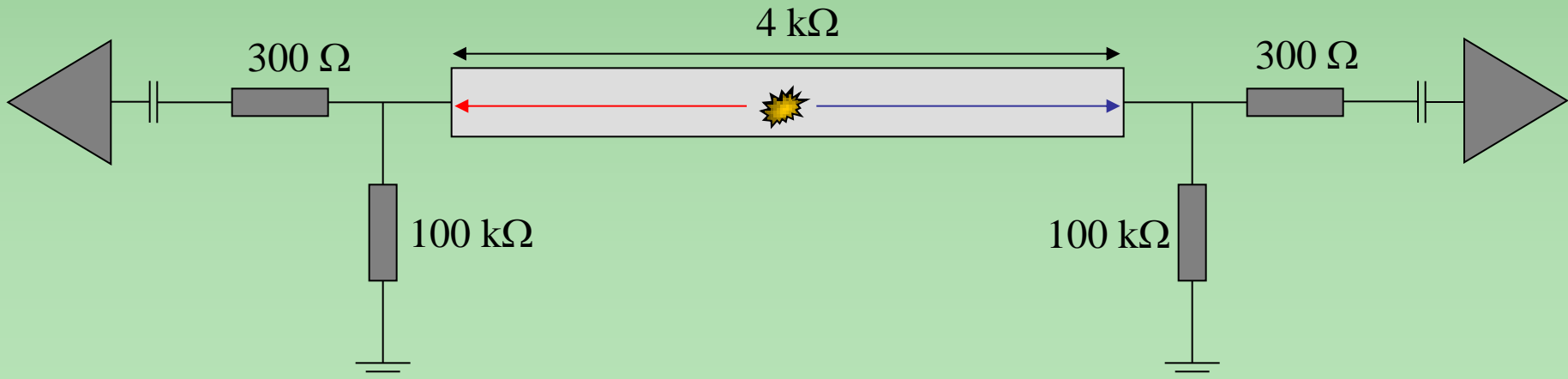
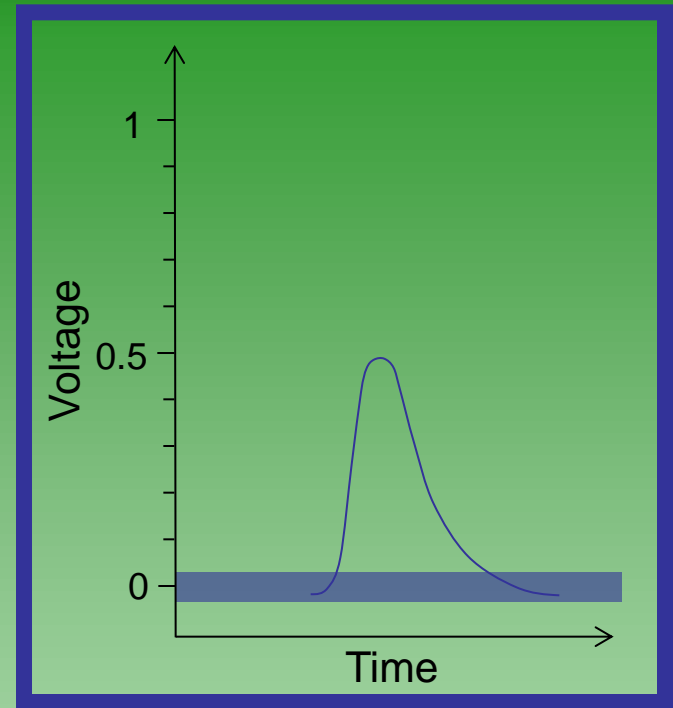
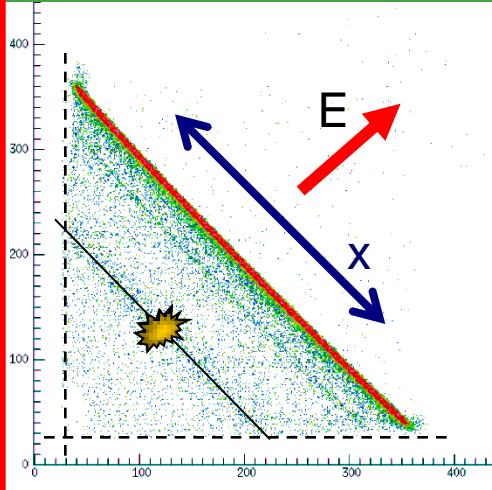
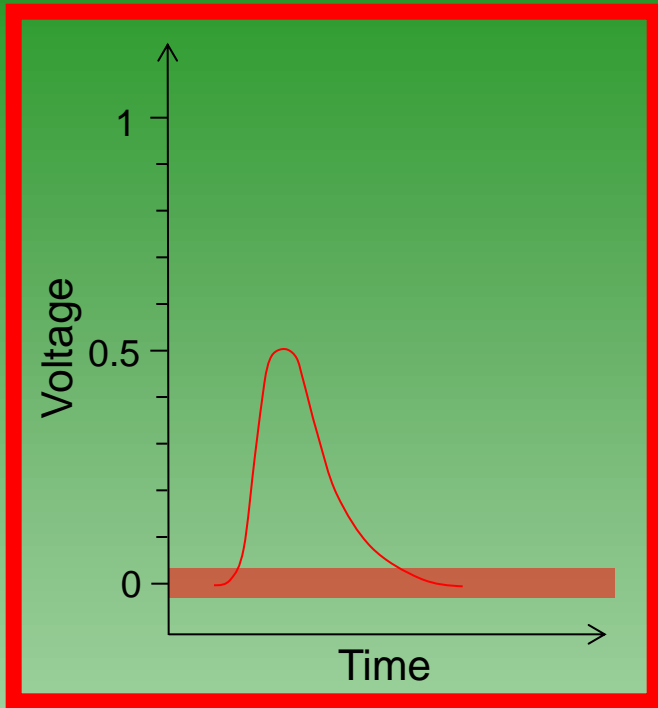
- Good position resolution with relatively small channel count
- Position resolution degrades at low energy ( $1/E$ )
- Threshold issues (esp at strip ends)



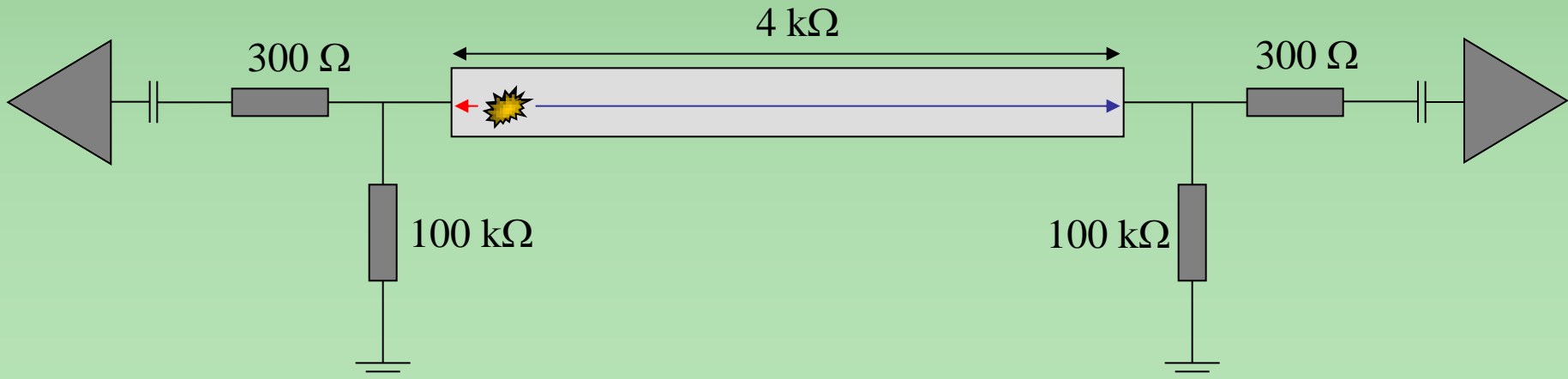
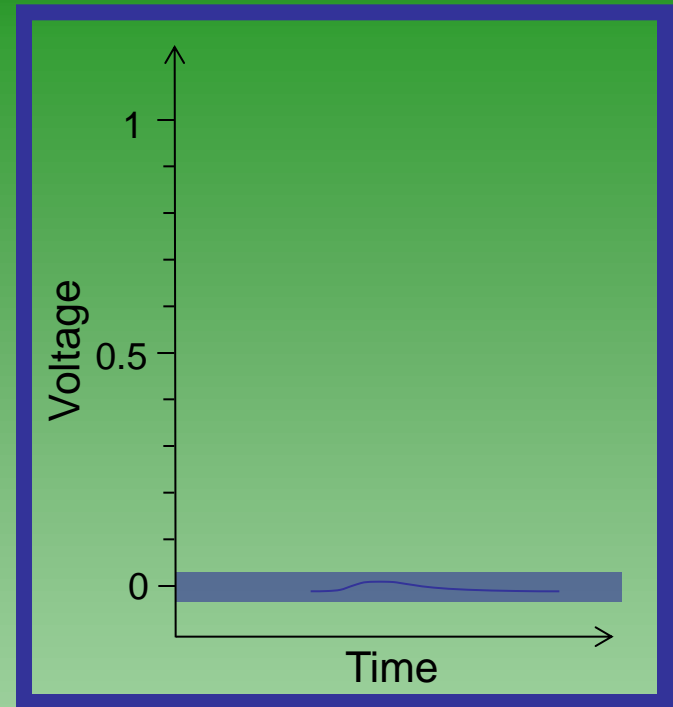
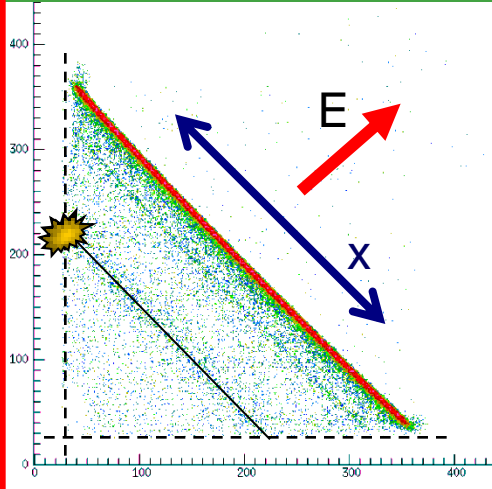
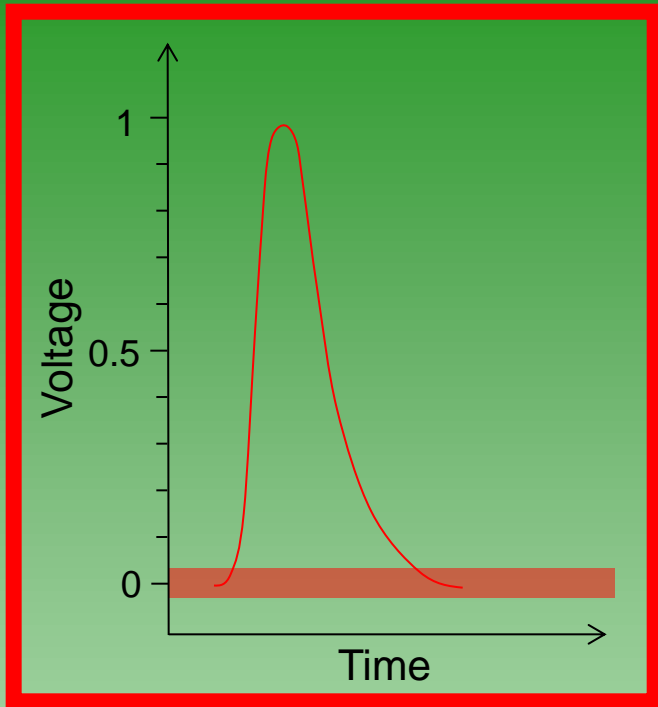
- Energy =  $Q_H + Q_L$
- Position =  $\frac{Q_H - Q_L}{Q_H + Q_L}$



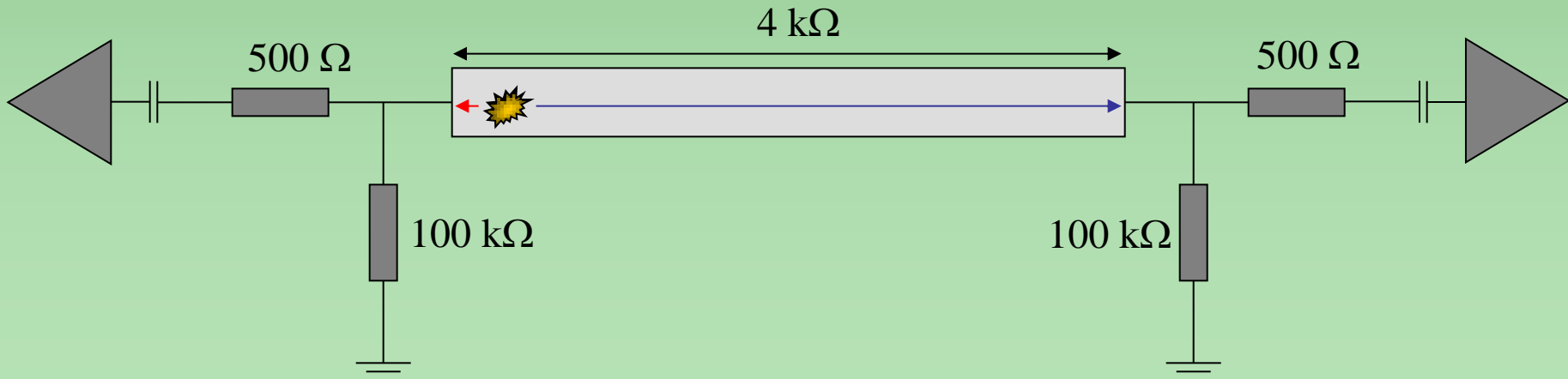
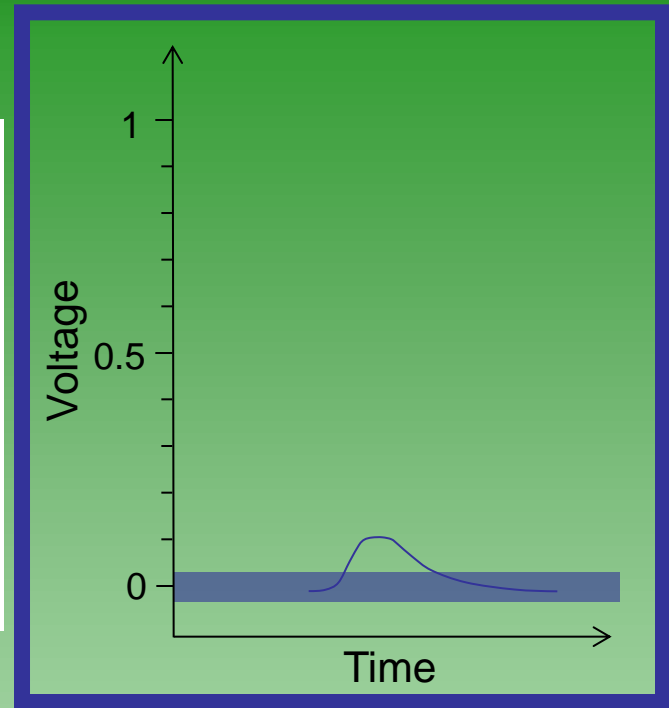
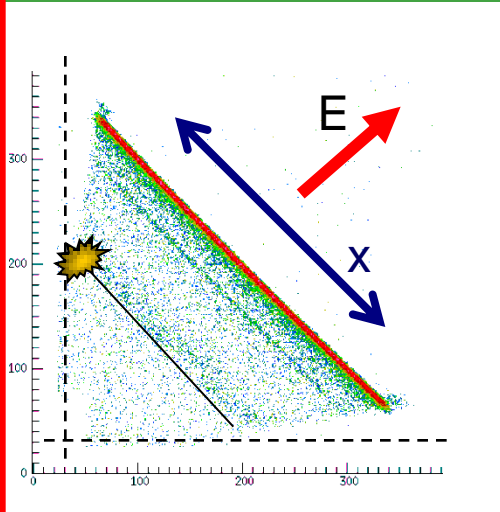
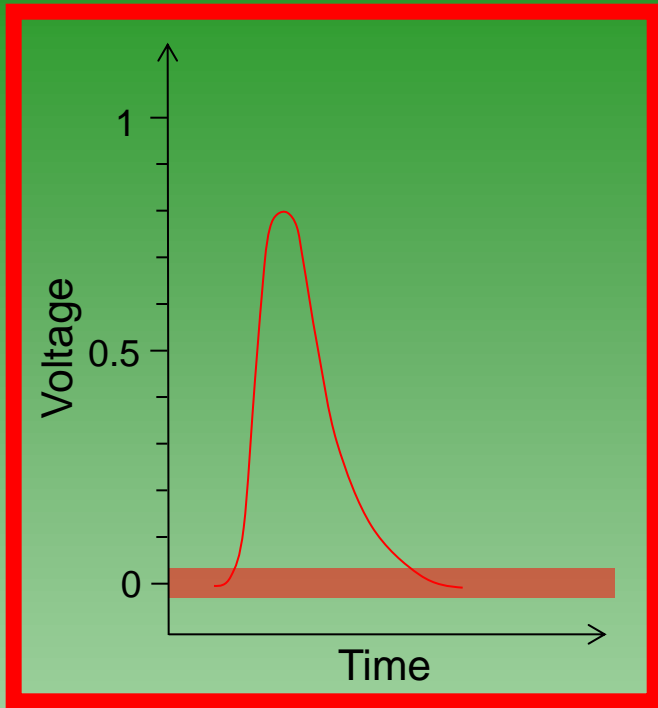
# Resistive silicon strip detectors



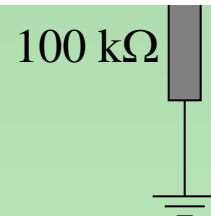
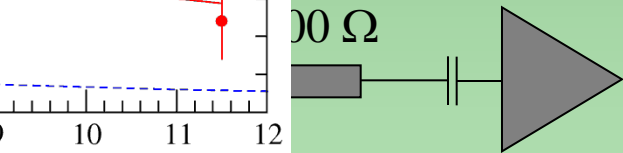
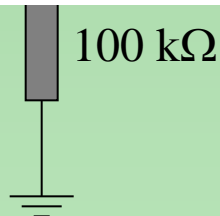
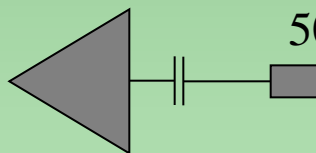
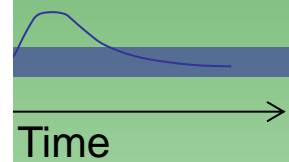
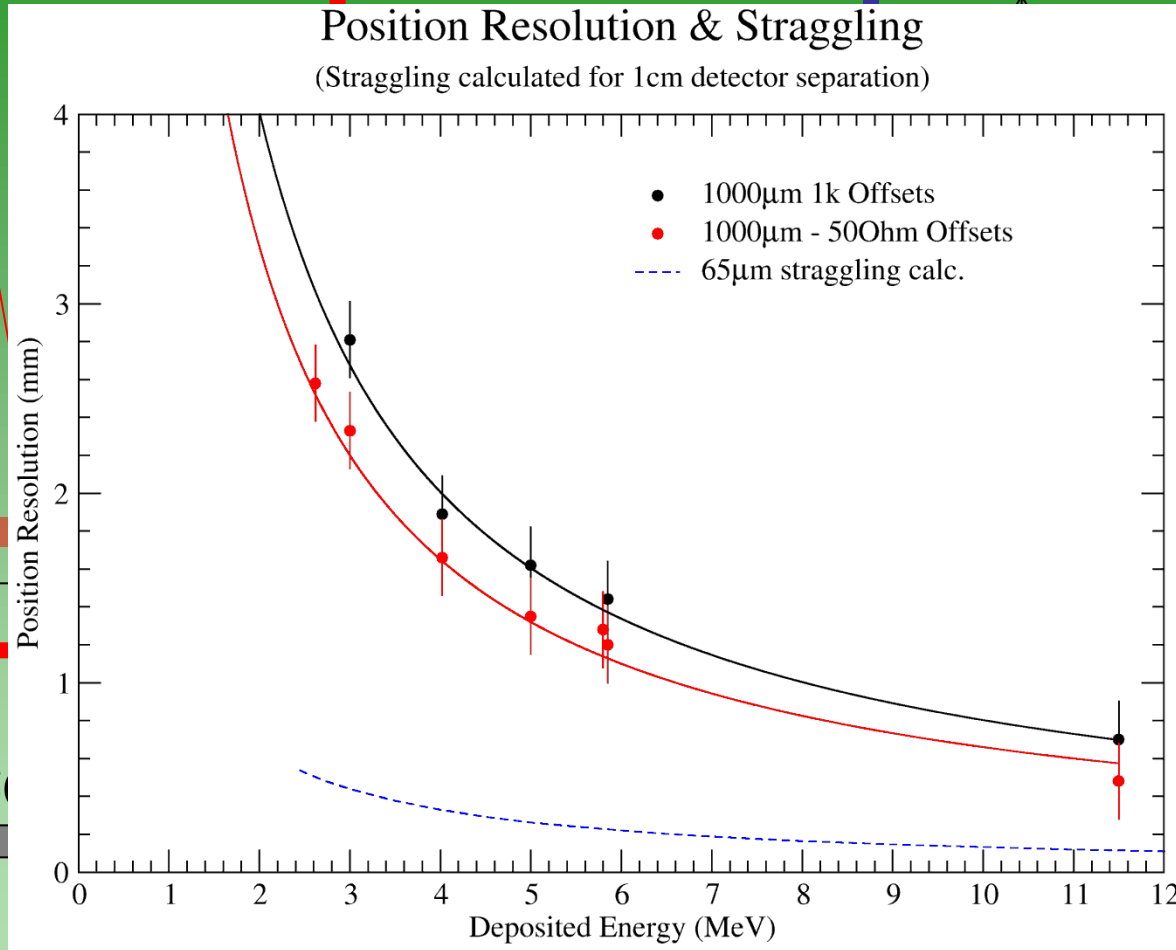
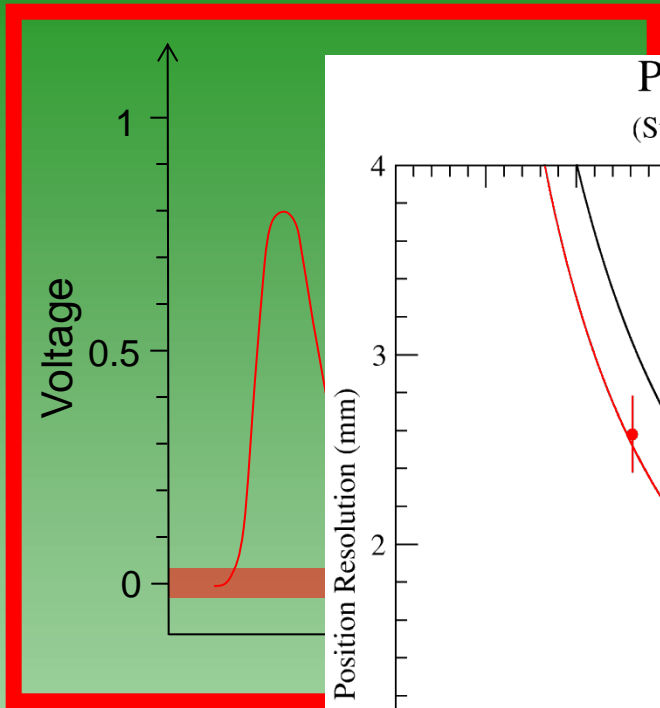
# Resistive silicon strip detectors



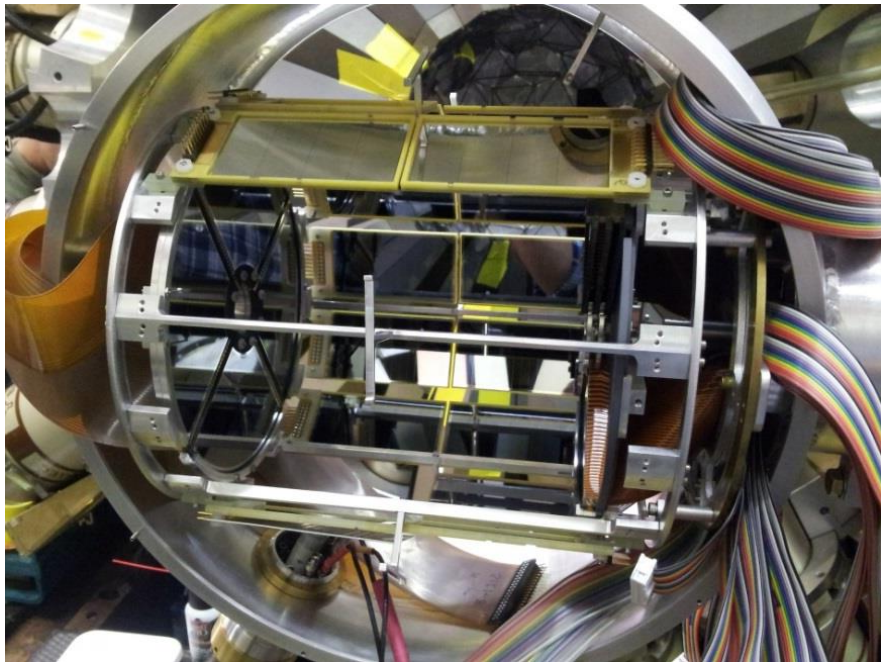
# Resistive silicon strip detectors



# Resistive silicon strip detectors



# Example silicon strip detector arrays

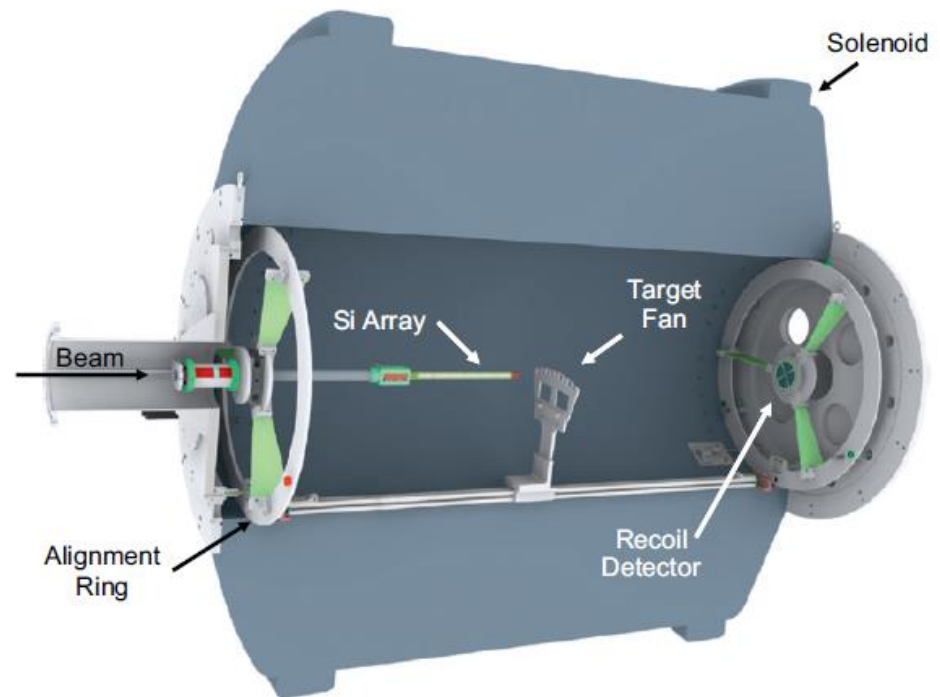


## ORRUBA/GODDESS

Barrel array of Si telescopes  
Resistive DSSD 75mm x 40mm  
(4x resistive strips, 4x non-resistive pads)  
Instrumented with conventional/digital  
(12ch per detector)  
ORNL, Rutgers, UTK, TTU, LSU

## HELIOS

Solenoidal spectrometer  
Array of axial Si detectors  
Resistive detectors (~10mm x  
~60 mm)  
Instrumented conventional/digital  
ANL, WMU, U. of Manchester

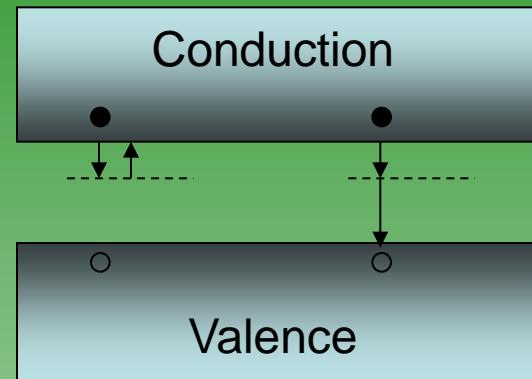


# Charge collection in silicon detectors

## Trapping and Recombination

Impurities in the crystal, and defects in the lattice structure, can cause energy levels within the energy gap (at certain spatial points)

This leads to worse charge collection



### ***Trapping***

At such sites, electrons can be trapped from the conduction band for a time. If their release time is significant compared to the charge collection time, can cause signal degradation

### ***Recombination***

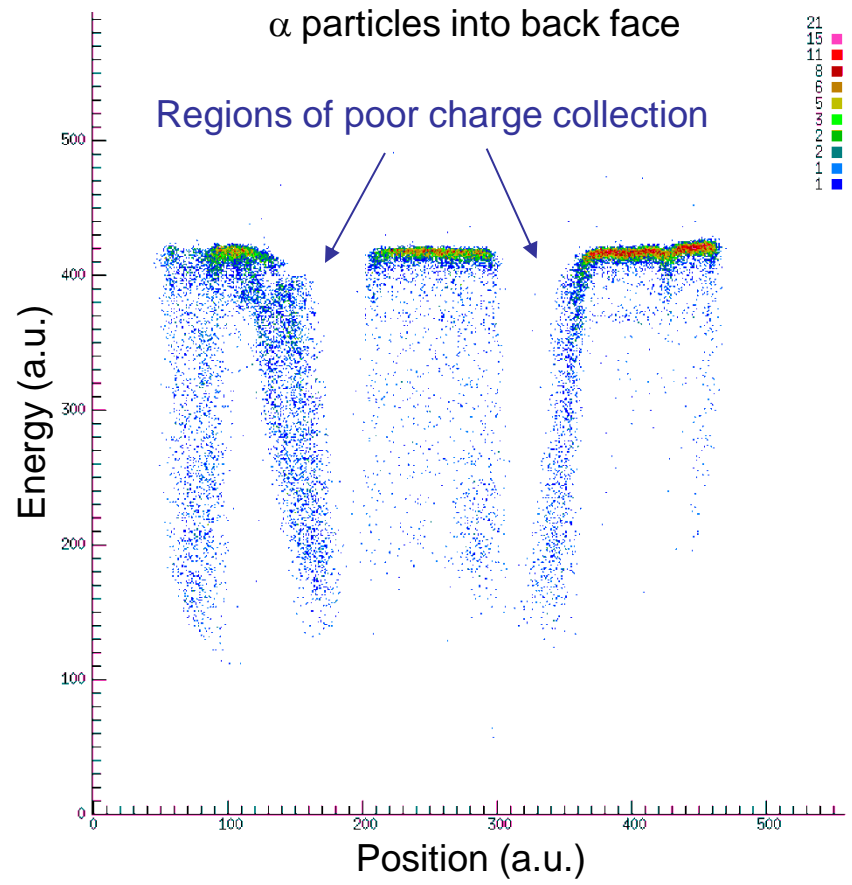
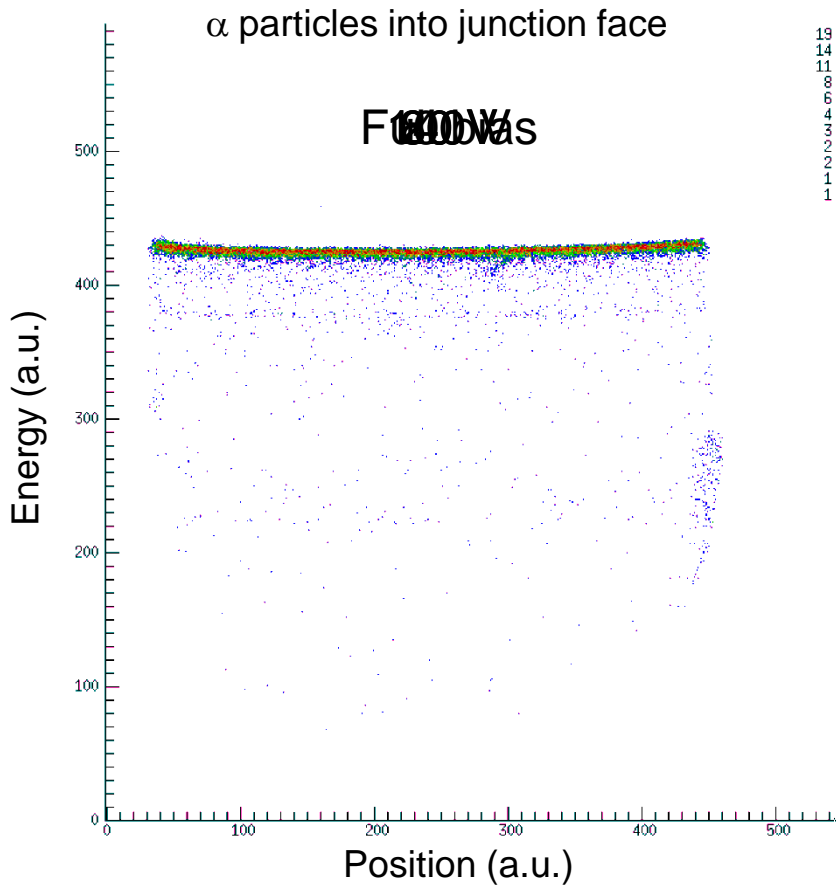
At recombination sites, electrons trapped from the conduction band for a time. A hole may be captured within this time, leading to recombination (loss of charge carriers)

# Charge collection in silicon detectors

5.8 MeV  $\alpha$ -particles only penetrate 30 $\mu\text{m}$  into detector

Non-uniformities in Si (eg leading to trapping)

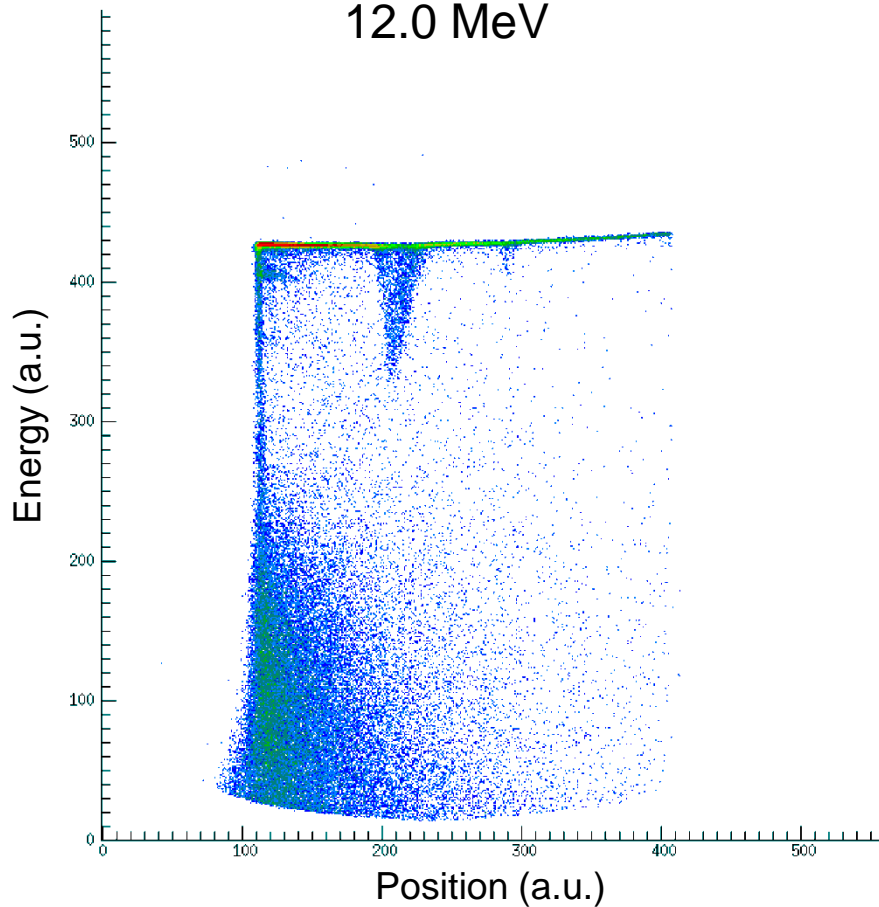
*Ballistic deficit (see later)*



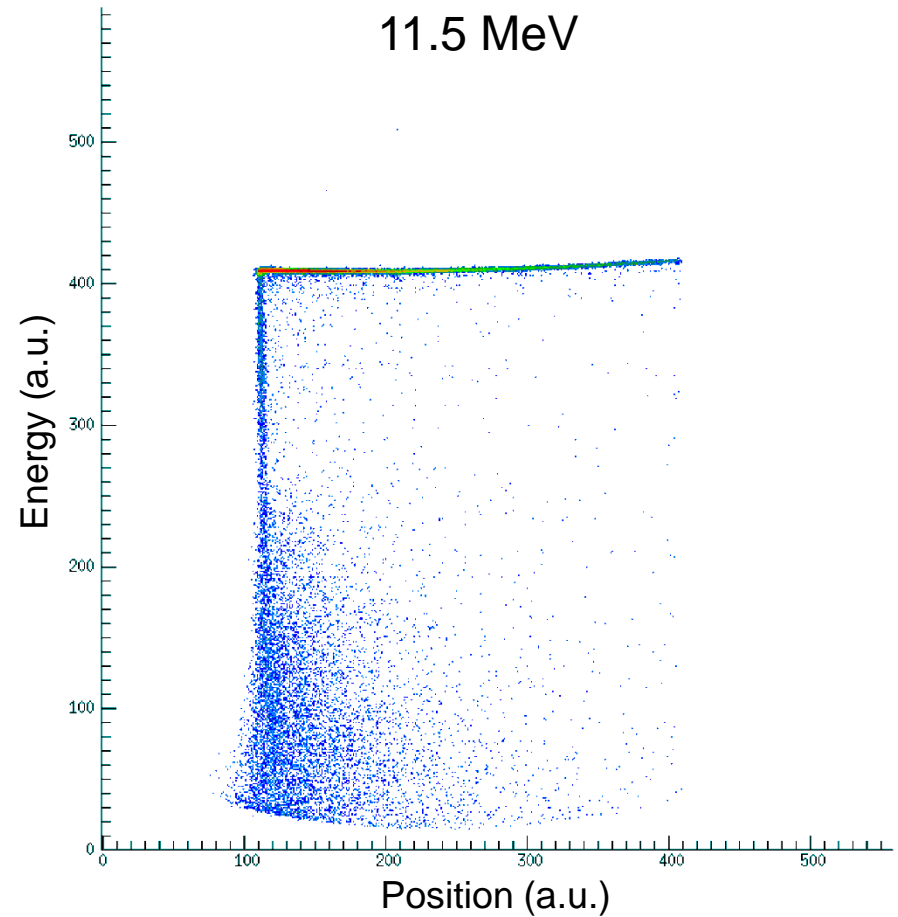
# Charge collection in silicon detectors

5.8 MeV  $\alpha$ -particles only penetrate 30 $\mu\text{m}$  into detector

12.0 MeV



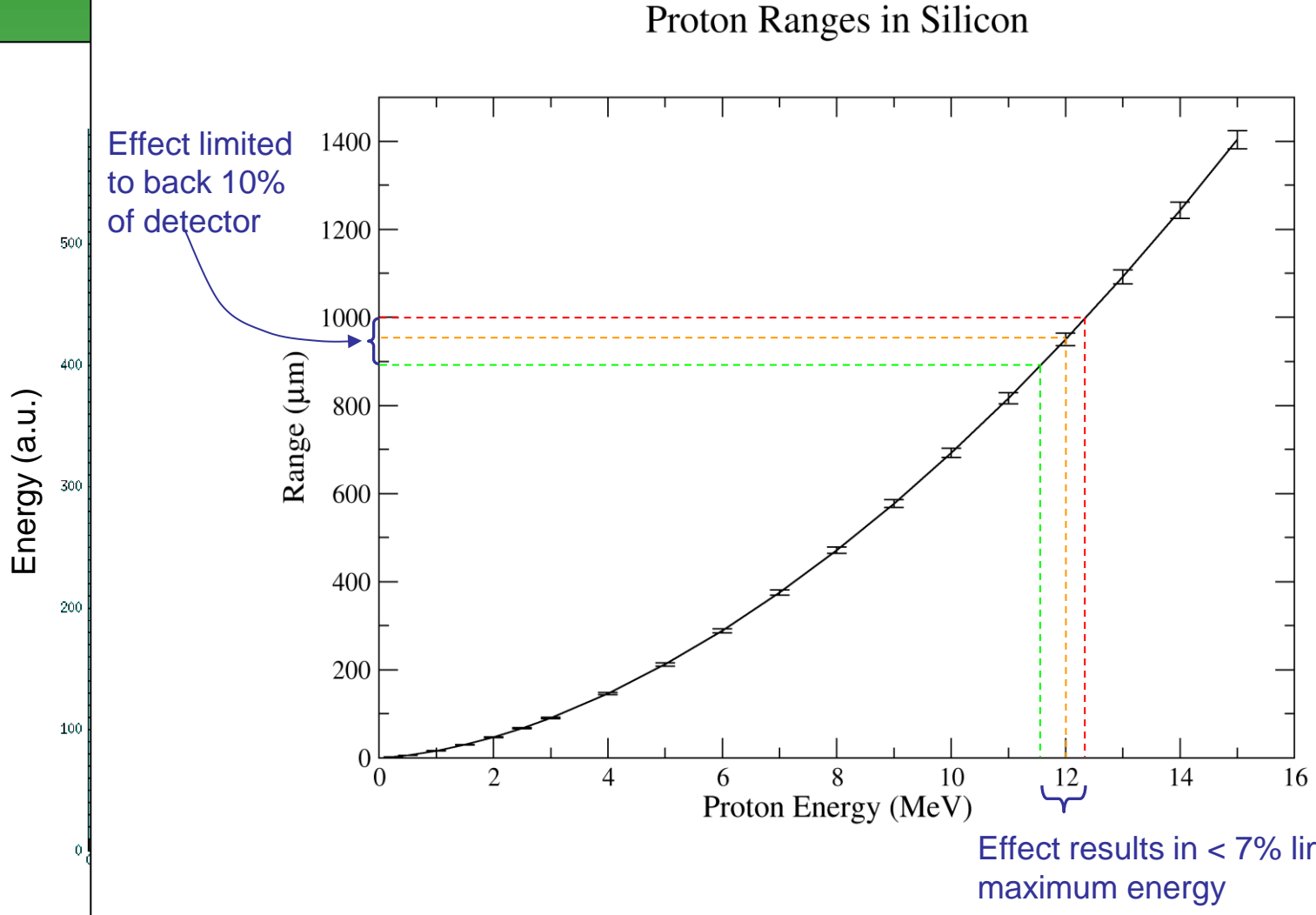
11.5 MeV





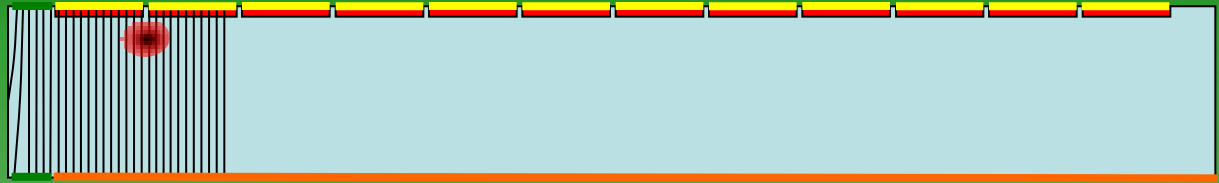
# Charge collection in silicon detectors

5.8 MeV  $\alpha$ -particles only penetrate 30 $\mu\text{m}$  into detector

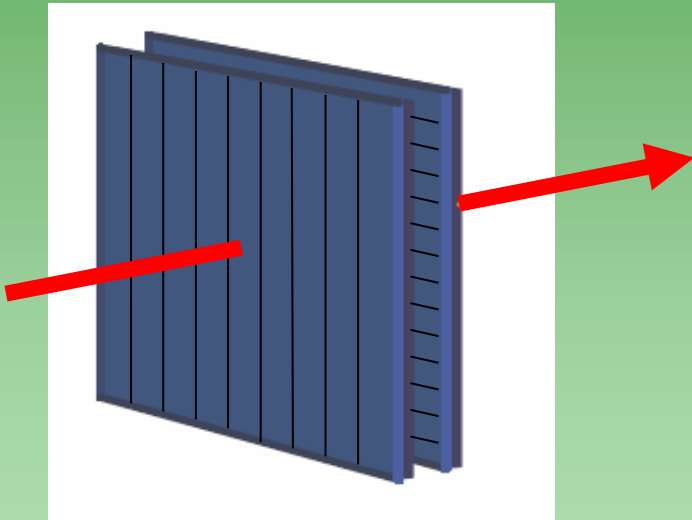


# Charge collection in silicon detectors

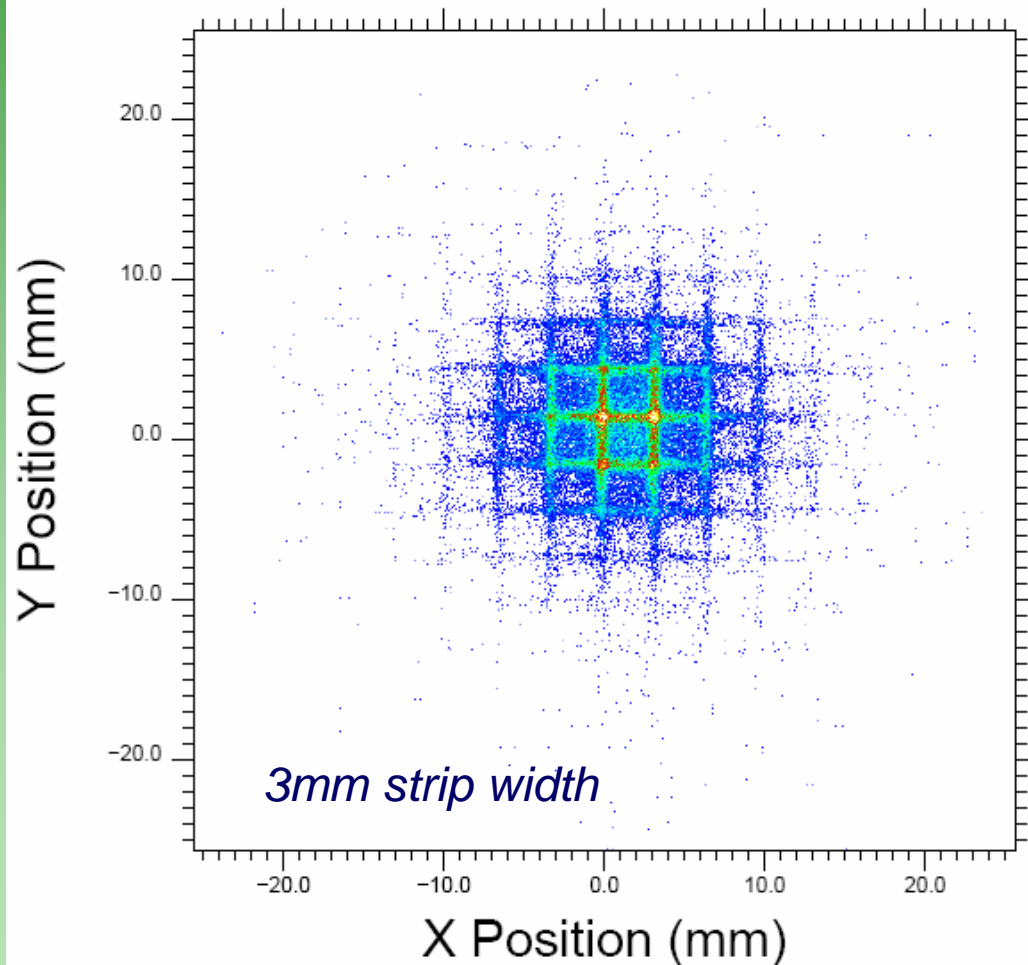
## Charge sharing



Two crossed resistive strip silicon detectors

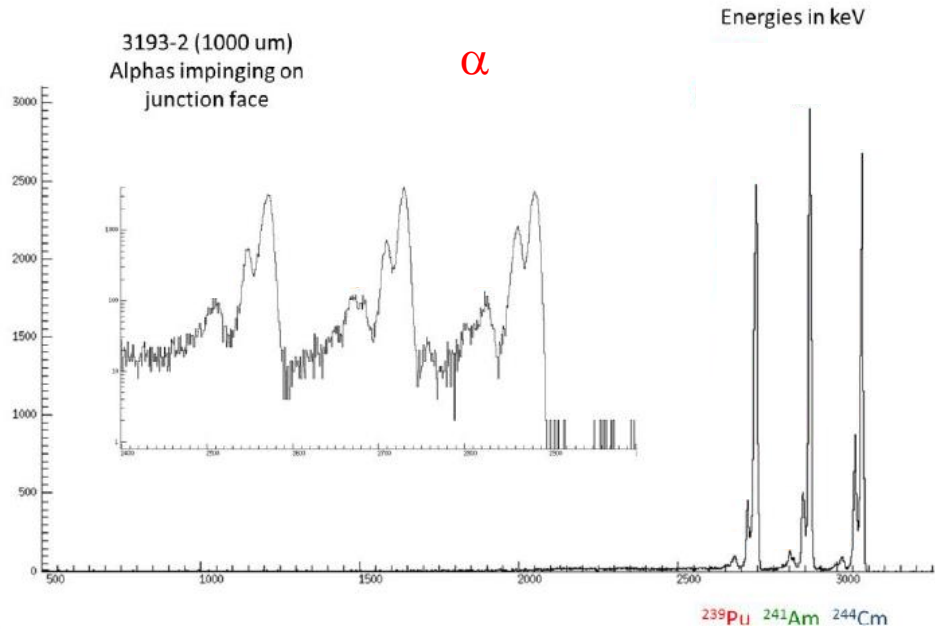
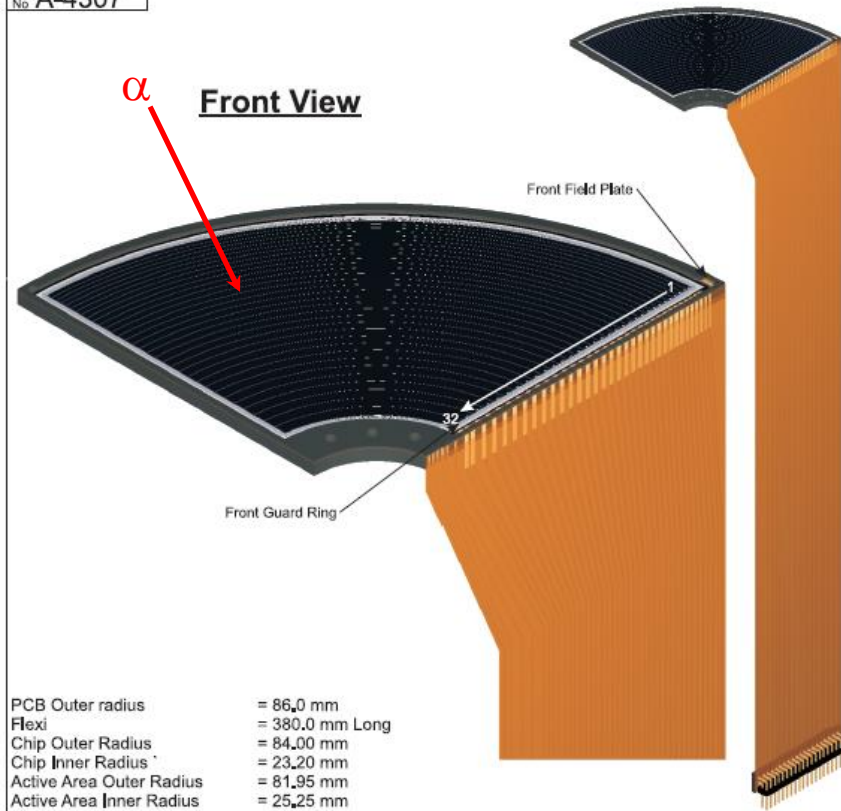


Requiring two hits on one detector, and plotting the position on the other, charge sharing events (along the strip edges) can be highlighted



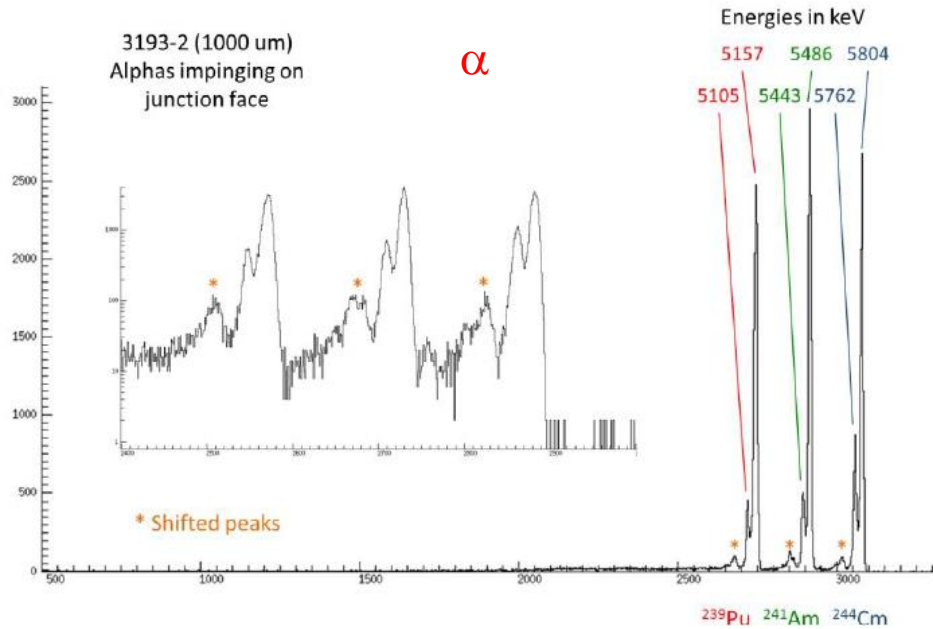
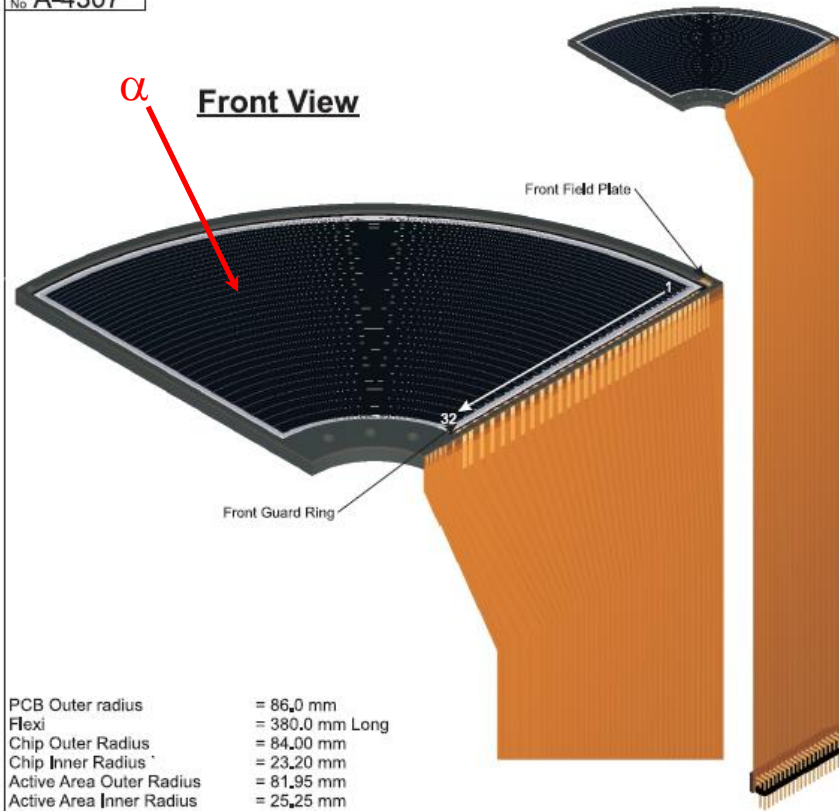
# Example silicon issue

Drp-  
No. A-4307



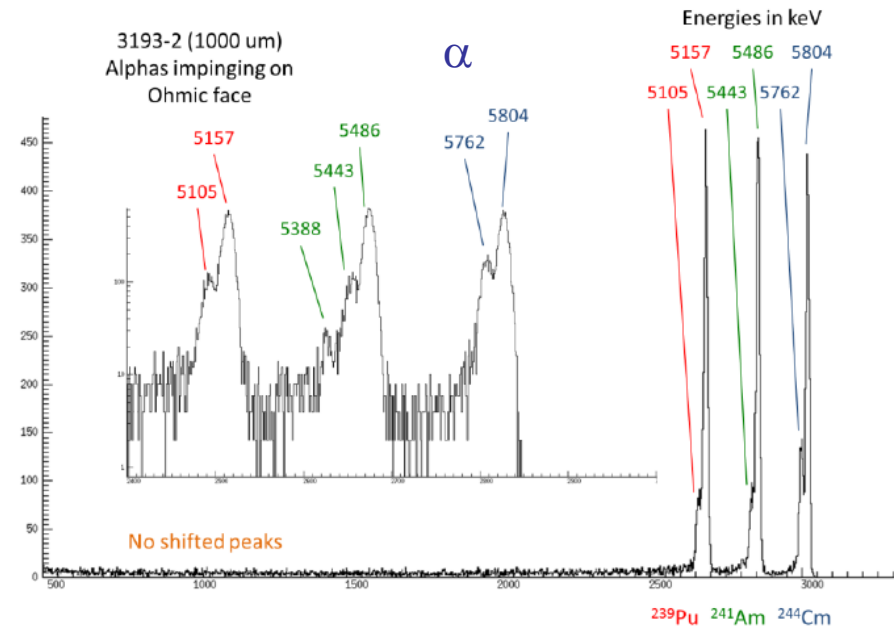
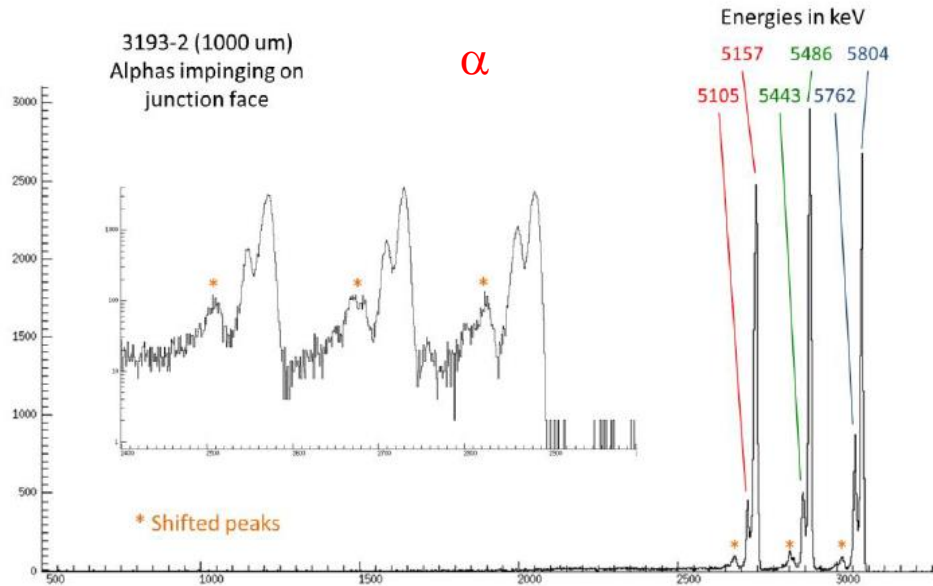
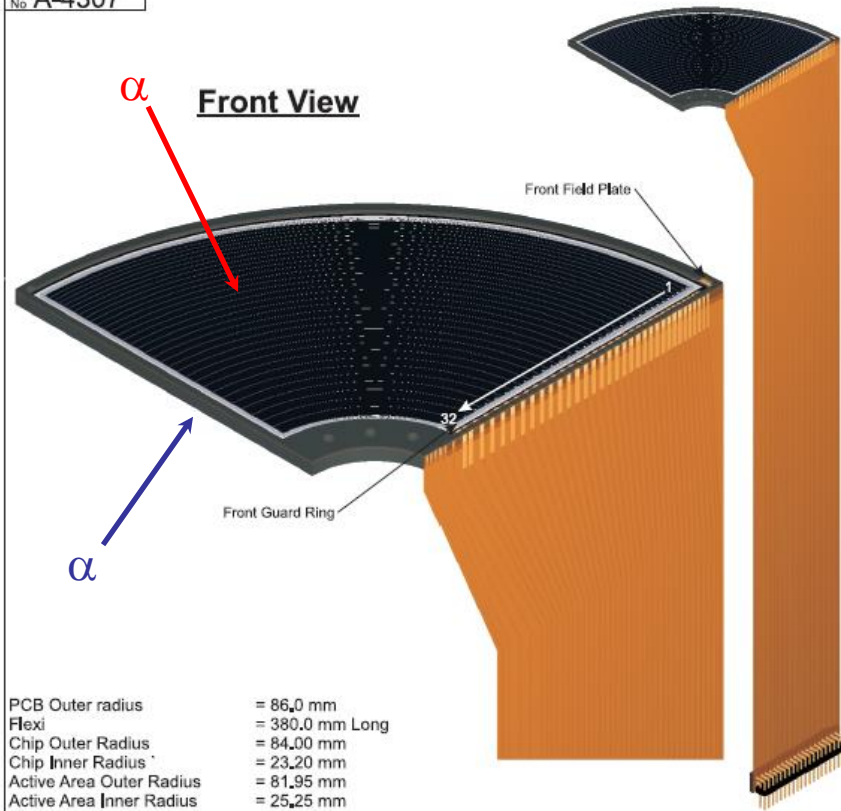
# Example silicon issue

Drp-  
No A-4307

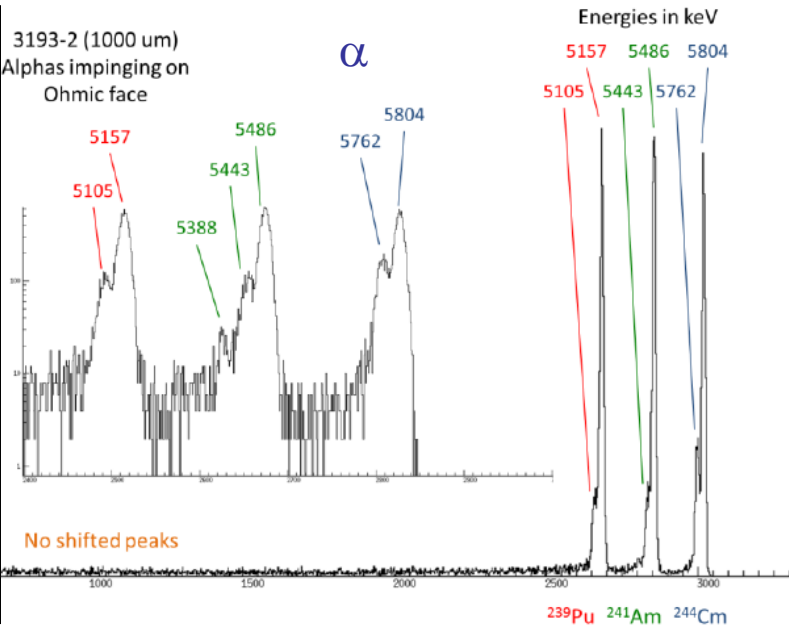
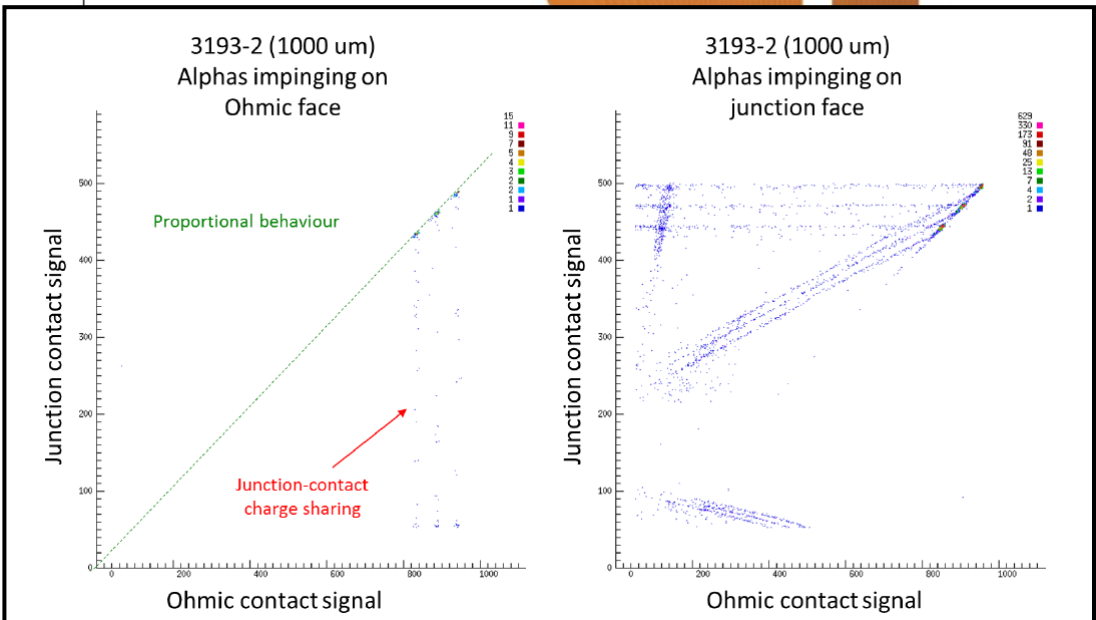
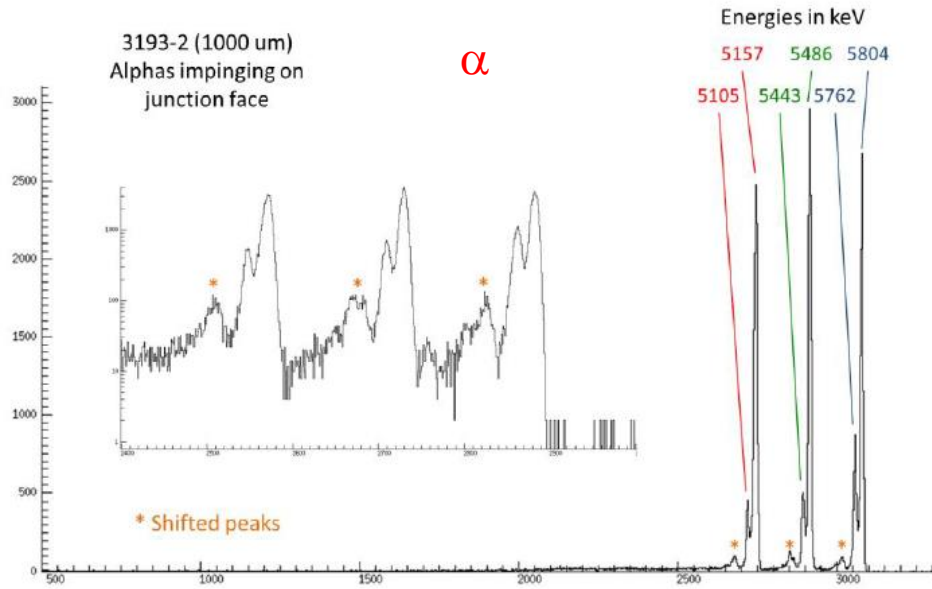
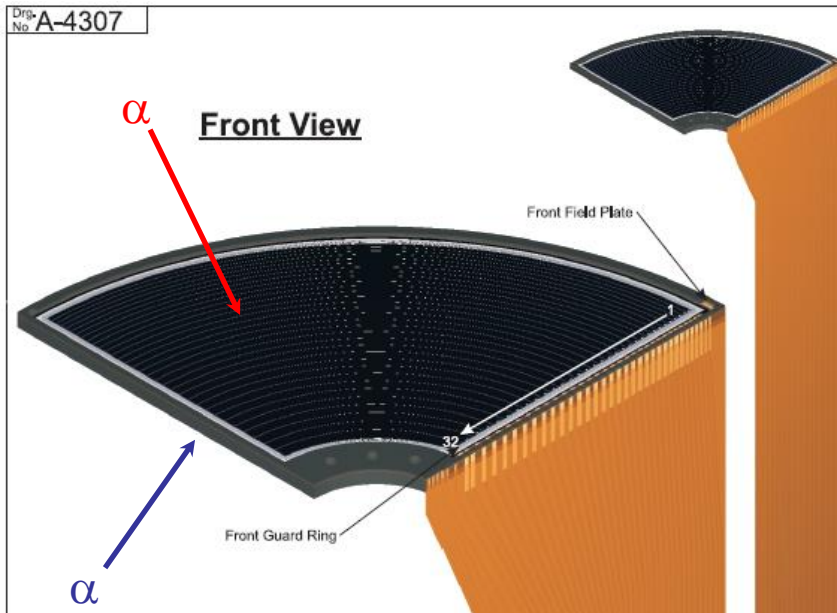


# Example silicon issue

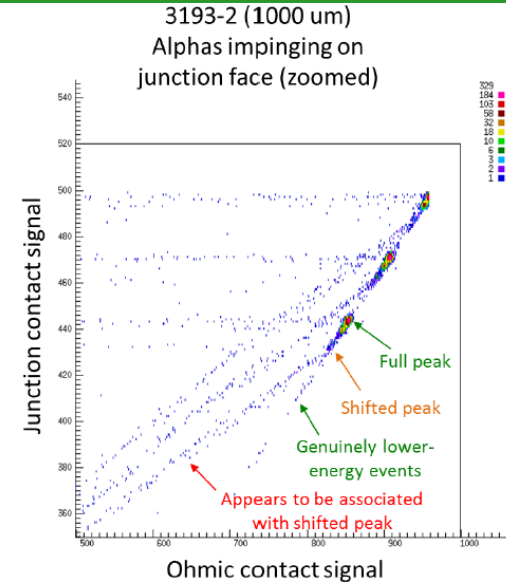
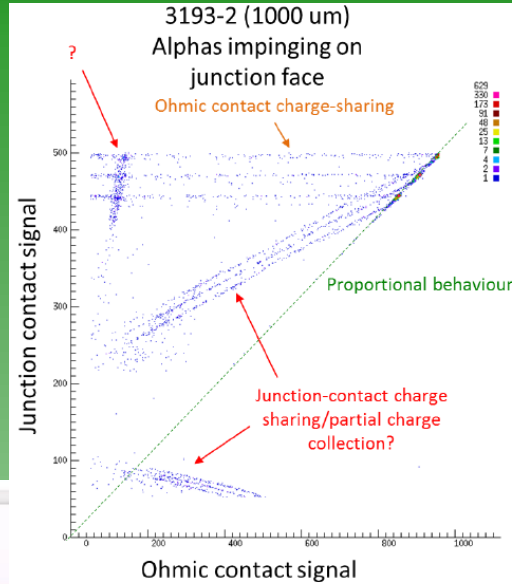
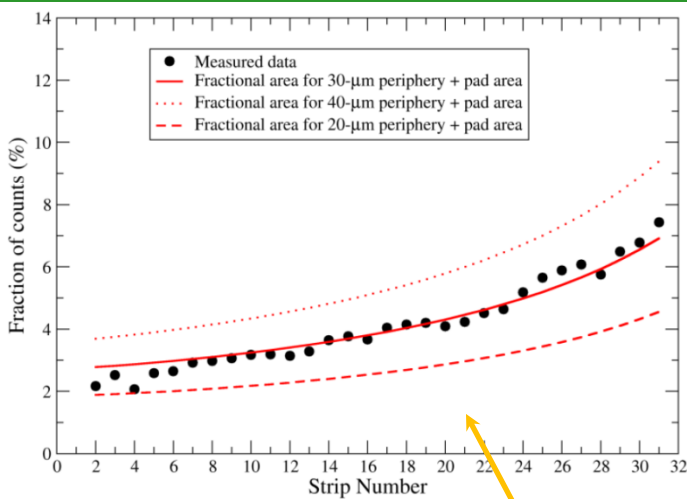
Drp. No. A-4307



# Example silicon issue



# Example silicon issue



JUNCTION  
NUMBER OF RING

CHIP  
OUTER RADIUS = 84 000  $\mu\text{m}$   
INNER 'HOLE' RADIUS = 23 200  $\mu\text{m}$

ACTIVE AREA  
RADIUS OUTER = 81 950  $\mu\text{m}$   
RADIUS INNER = 25 250  $\mu\text{m}$   
**RING SEPARATION = 100  $\mu\text{m}$**

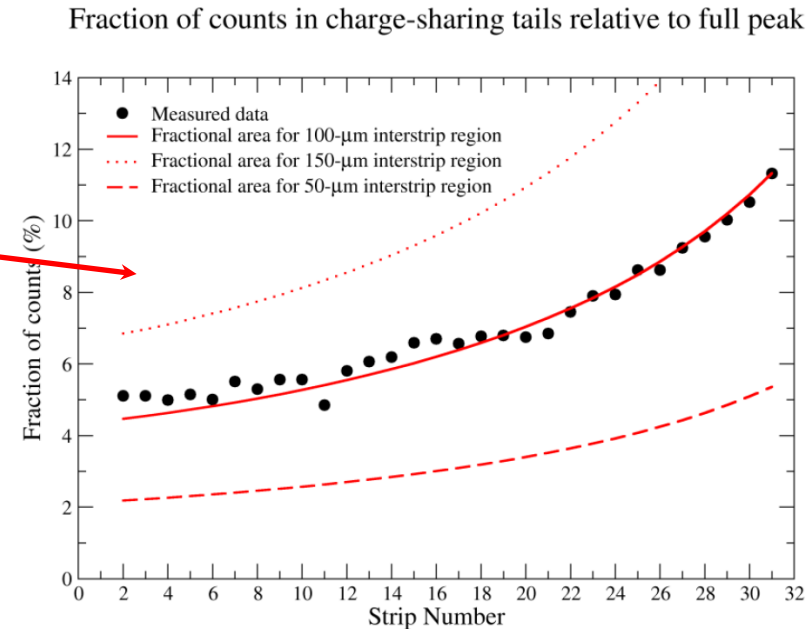
DESIGN TYPE = 9P

PERIPHERY WIDTH  
IMPALIT = 50  $\mu\text{m}$   
**METAL = 30  $\mu\text{m}$**

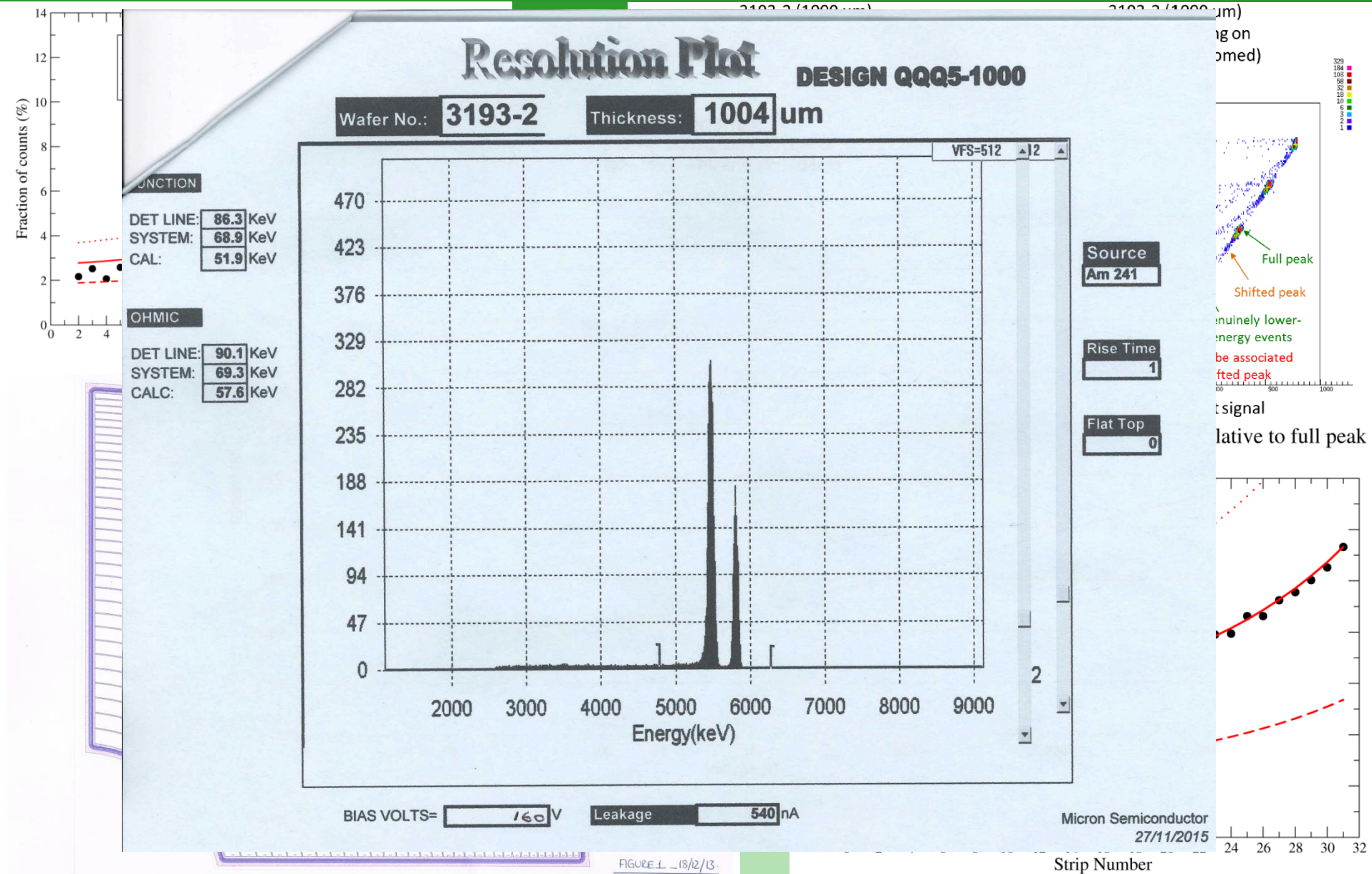
**BOUND PADS ~ 500 x 300  $\mu\text{m}$**

GUARD RINGS MGR  
FIELD PLATE YES

FIGURE 1 - 13/13



# Example silicon issue





# Germanium detectors

## Planar Ge detectors

Thin entrance window

Measuring low energy  $\gamma$  rays and x rays

Beta decay (implant)

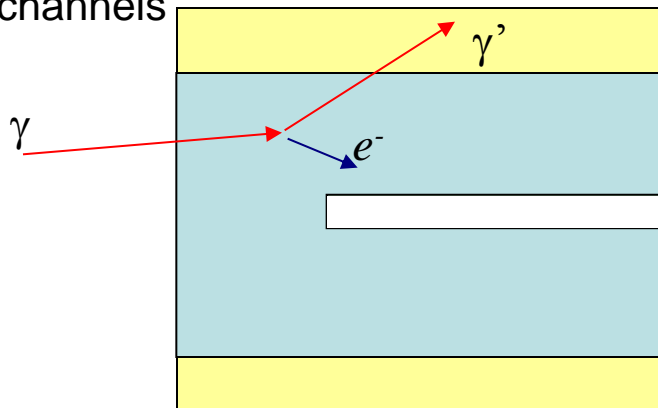
## Coaxial Ge detectors

Large volume for measuring higher energy  $\gamma$

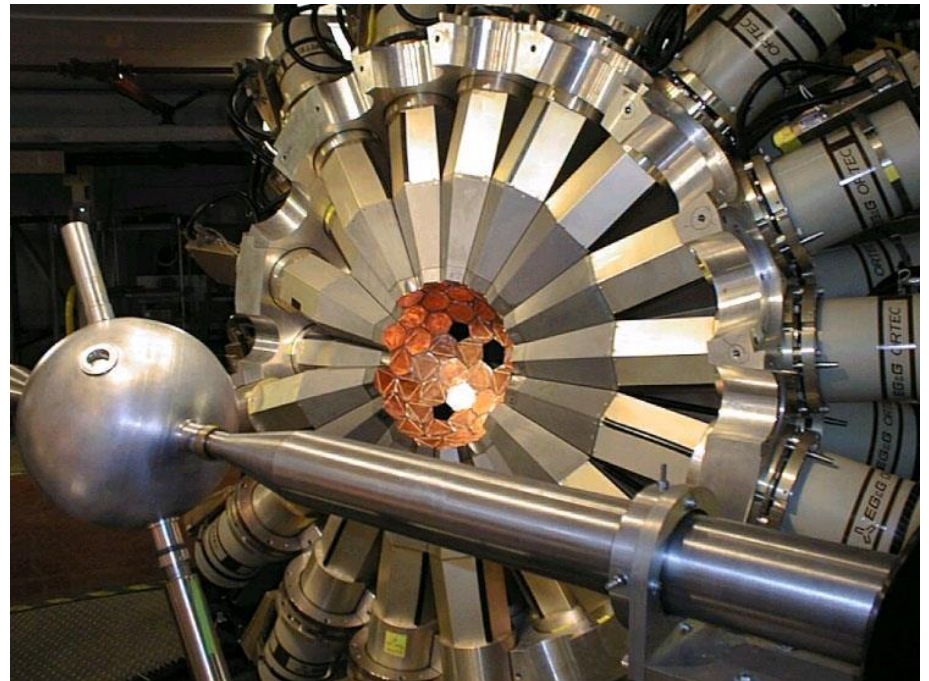
Large arrays (eg Gammasphere)

Often Compton suppressed

Some have coarse position from side-channels



*Gammasphere*



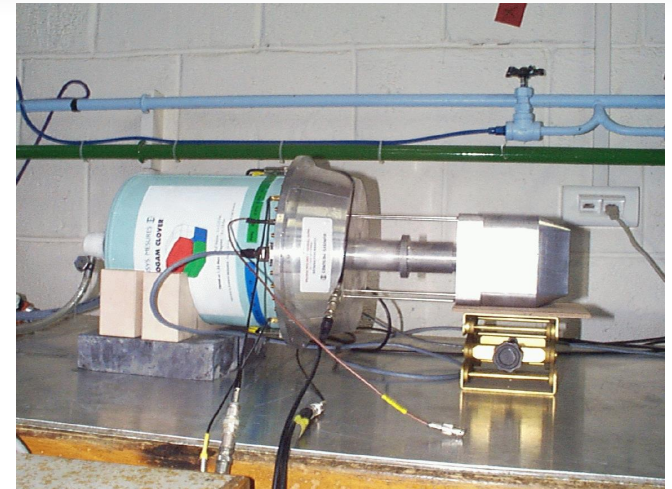
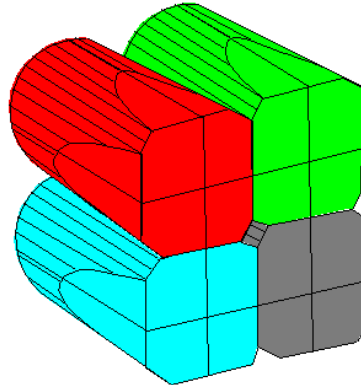
# Germanium detectors

## Clover detectors

Four close-packed crystals in one cryostat

Segmented readout for better position (Doppler) correction

*Exogam, Clarion, Clovershare*



## Highly segmented tracking detectors (digital)

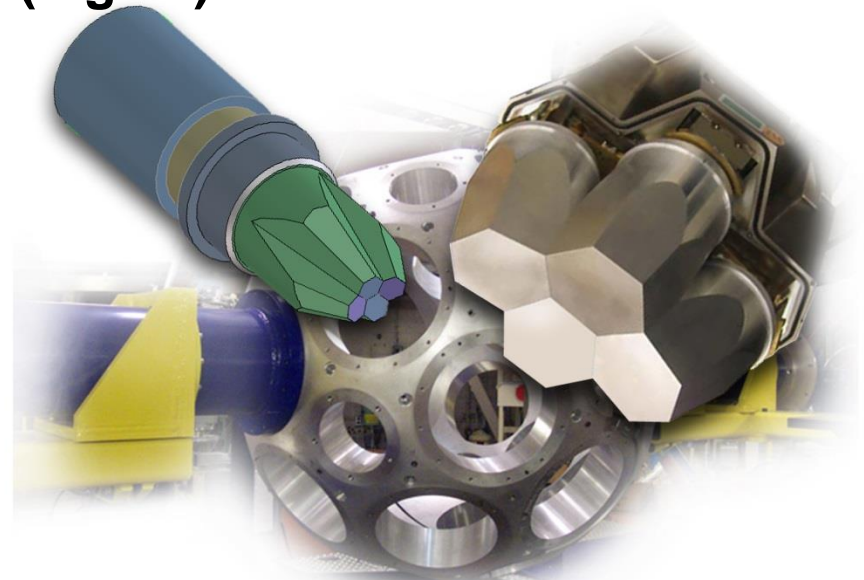
High segmentation

Digital readout allows event reconstruction (tracking) using pulse shapes

First point of interaction (Compton reconstruction) for Doppler correction

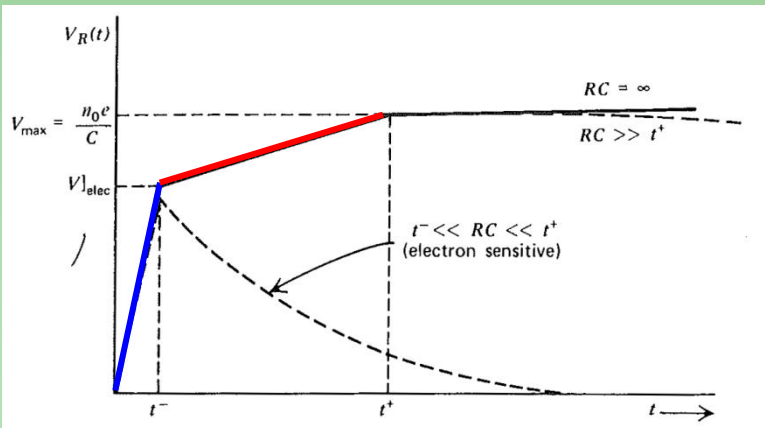
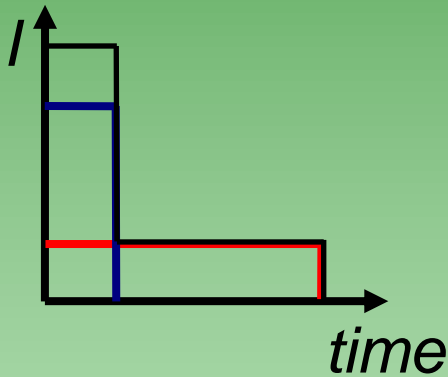
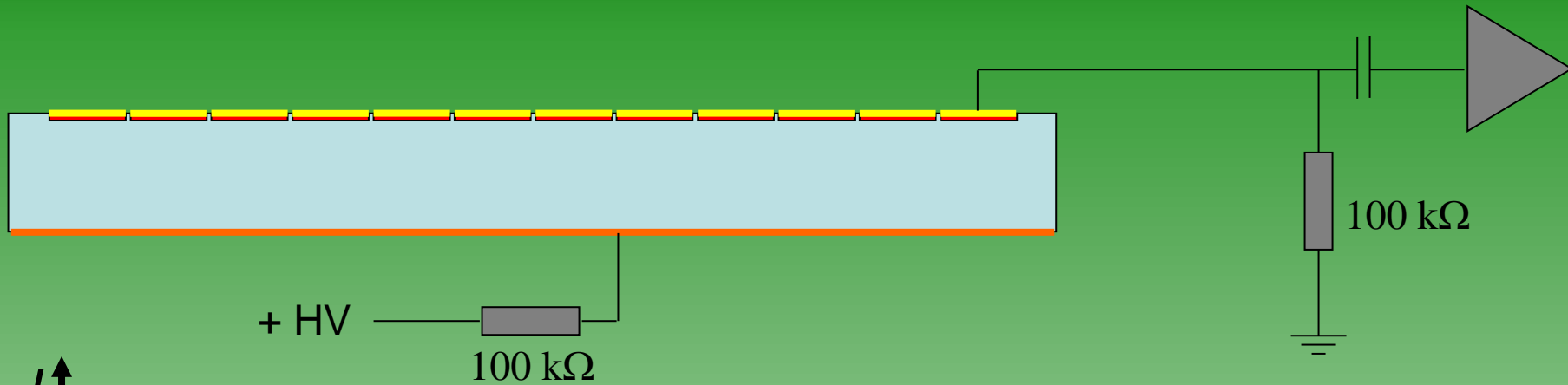
Can dispense with Compton suppression – higher efficiency possible

*GRETINA, AGATA*

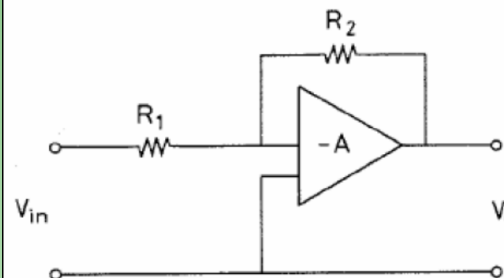


# Signals/DAQ

# Analogue signal processing



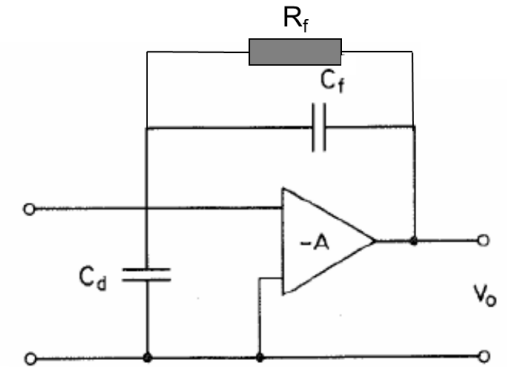
Voltage sensitive preamplifier



$$V_o = \frac{Q}{C_{\text{tot}}}$$

Gain dependent on the detector capacitance (can vary)

Charge sensitive preamplifier

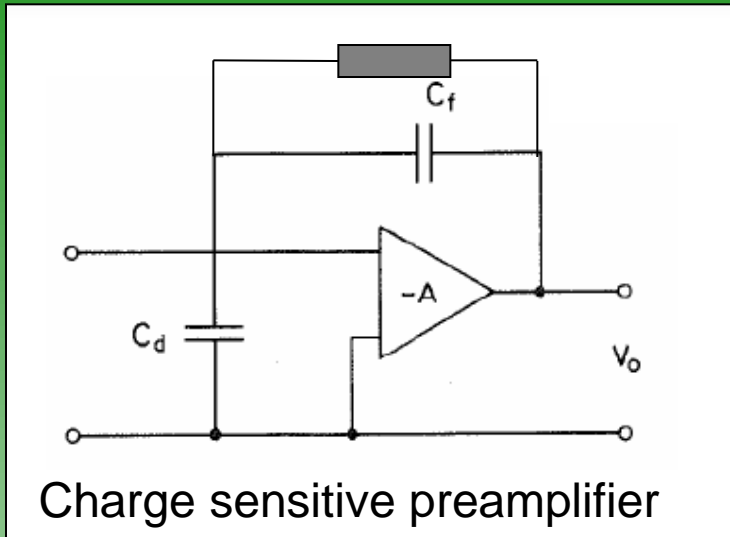


$$V_o = -\frac{Q}{C_f}$$

Output is proportional to charge integrated on  $C_f$ , if signal is fast compared to  $R_f C_f$

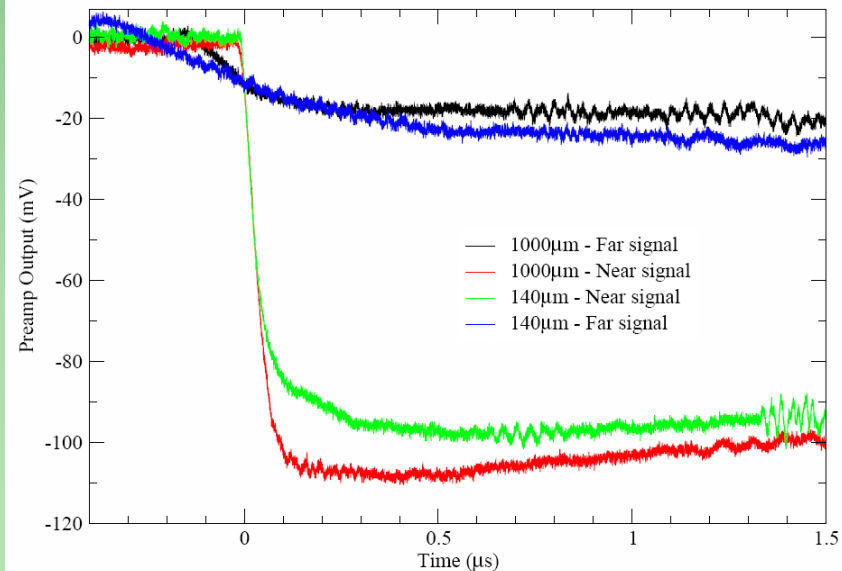
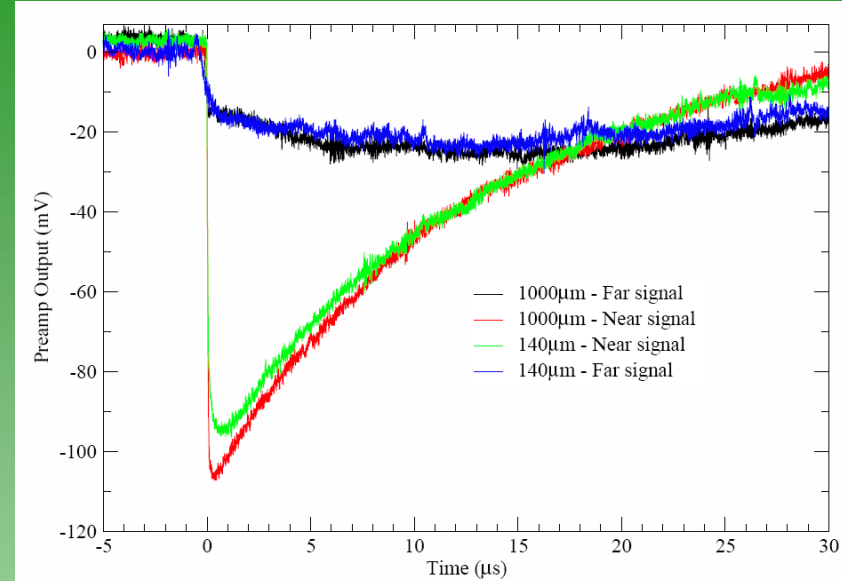
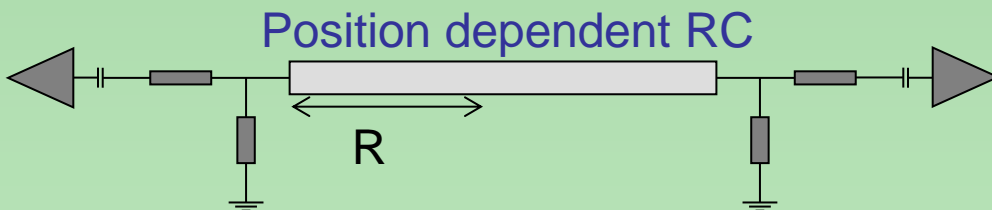
Noise is proportional to  $C_d$

# Analogue signal processing

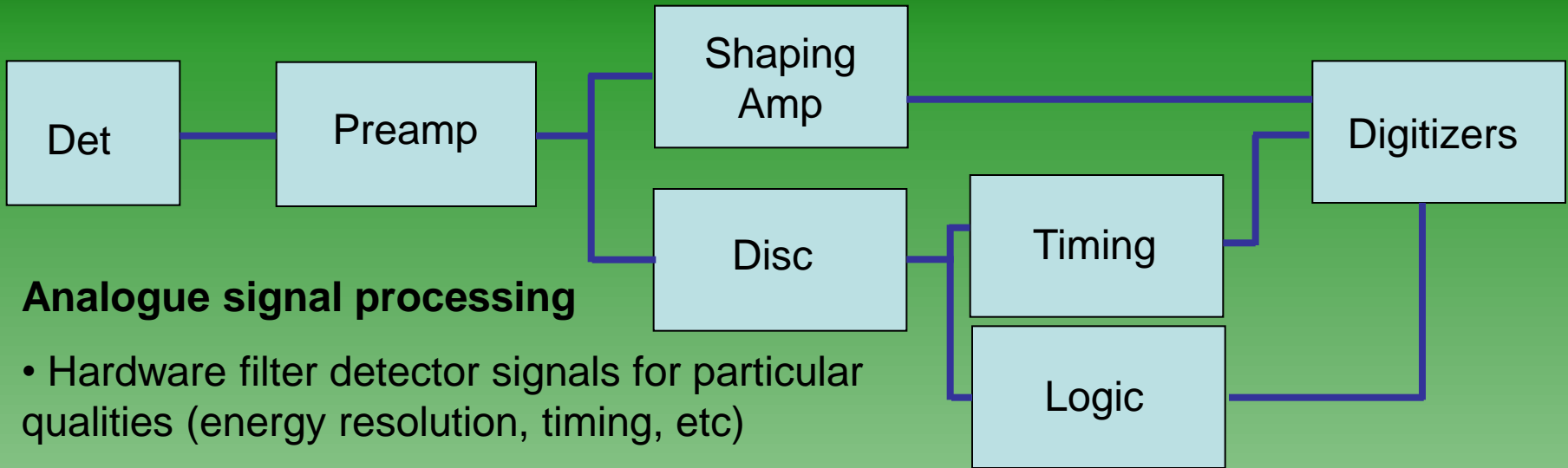


Fast rise-time – pulse height proportional to input signal

Slow rise-time – rise and decay convolved (non-linear signals, worse resolution) – *ballistic deficit*



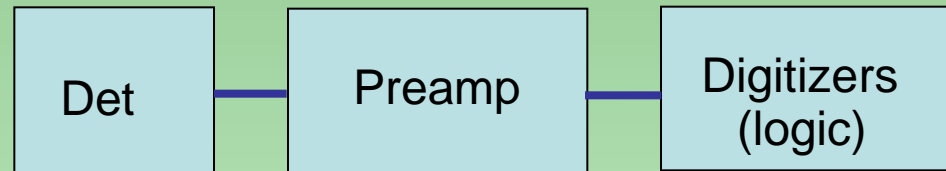
# Signal processing



## Analogue signal processing

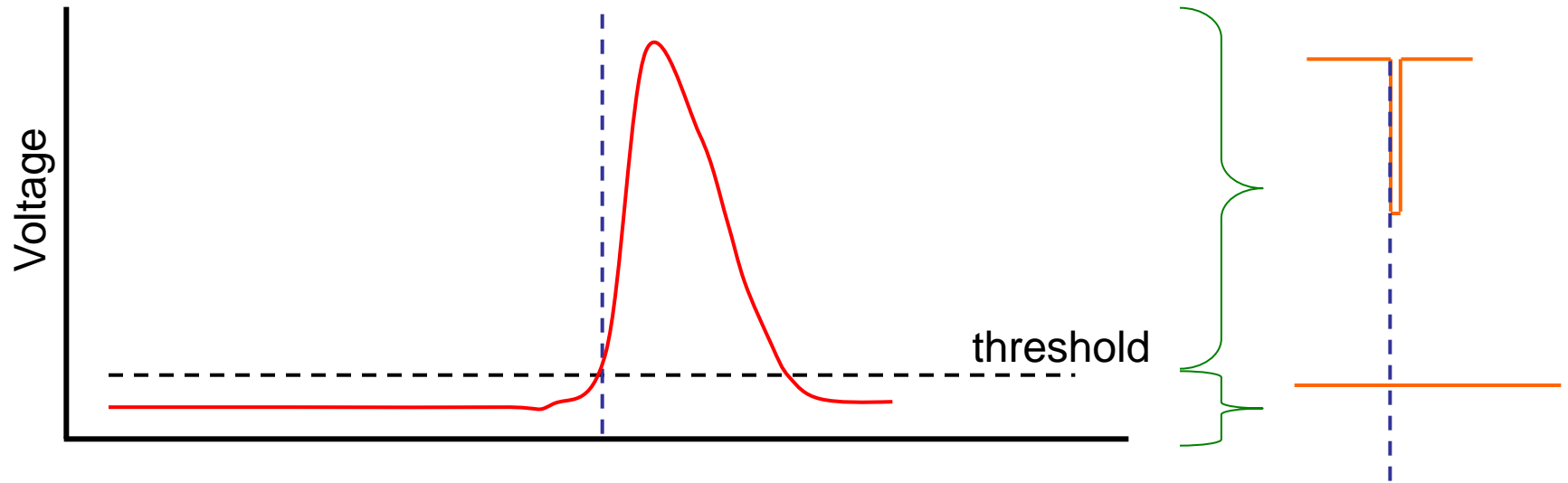
- Hardware filter detector signals for particular qualities (energy resolution, timing, etc)
- Excellent resolution, but some information is discarded
- Separate optimized processing required for different parameters (energy, time, etc)

## Digital signal processing

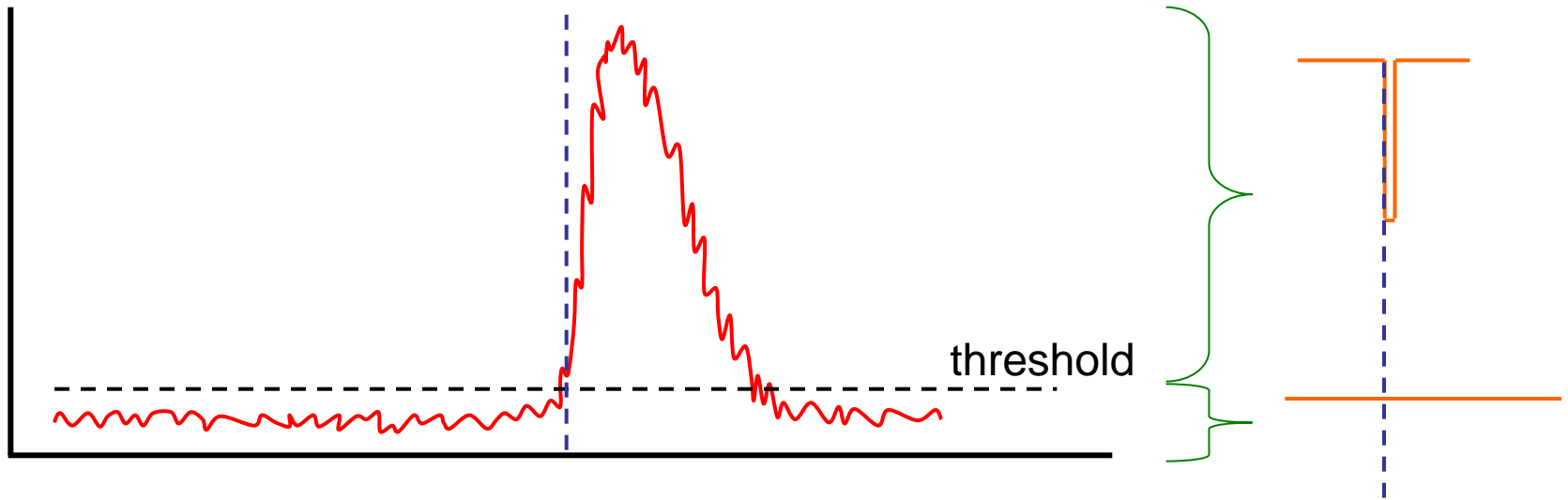


- Process (and sometimes store) a digital approximation of the trace from a detector/preamp
- All information encoded in the preamp trace can be processed (software)
- Single data stream can be multiplied and each stream processed independently

# Leading-edge discriminators

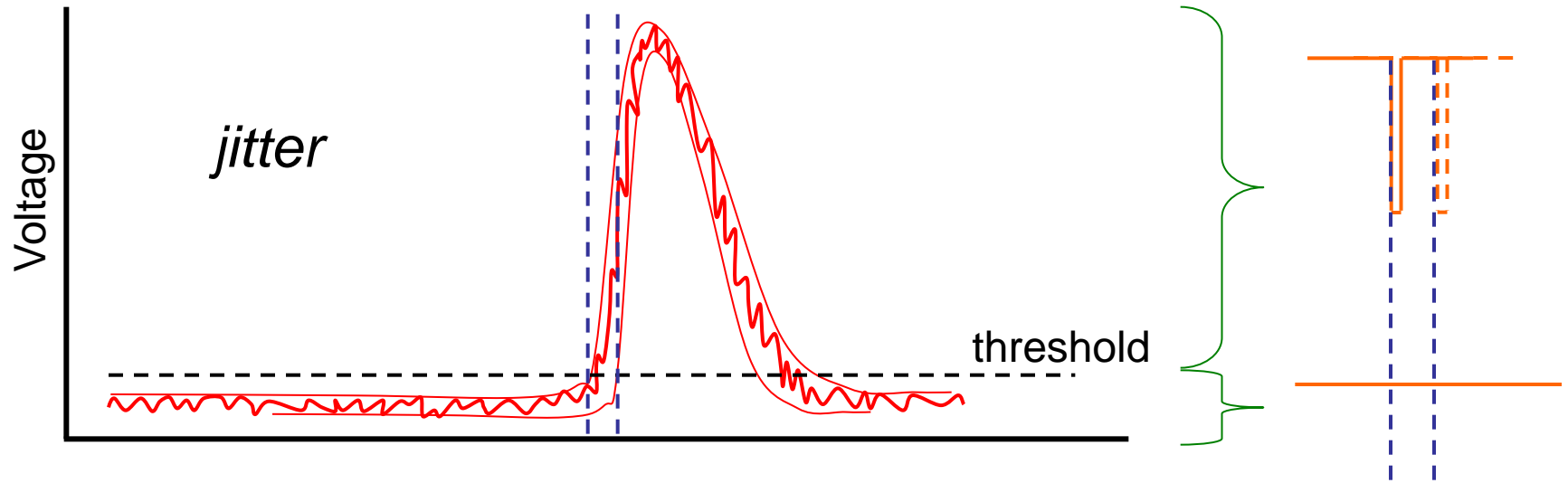


# Leading-edge discriminators

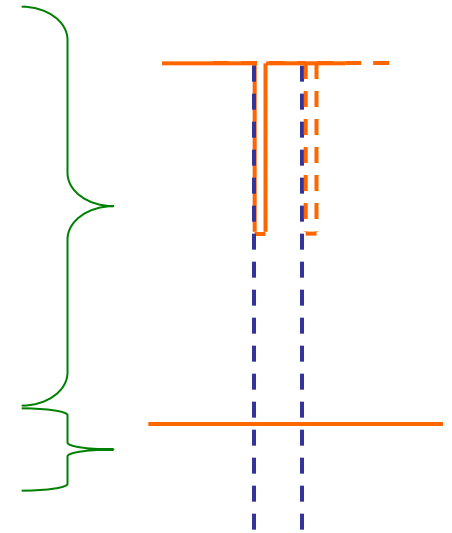
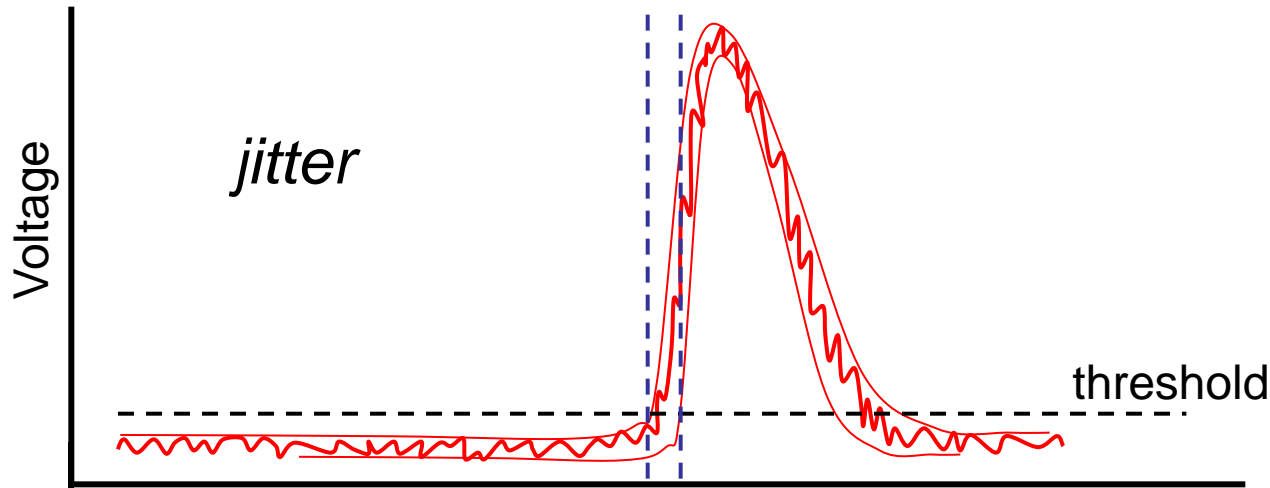




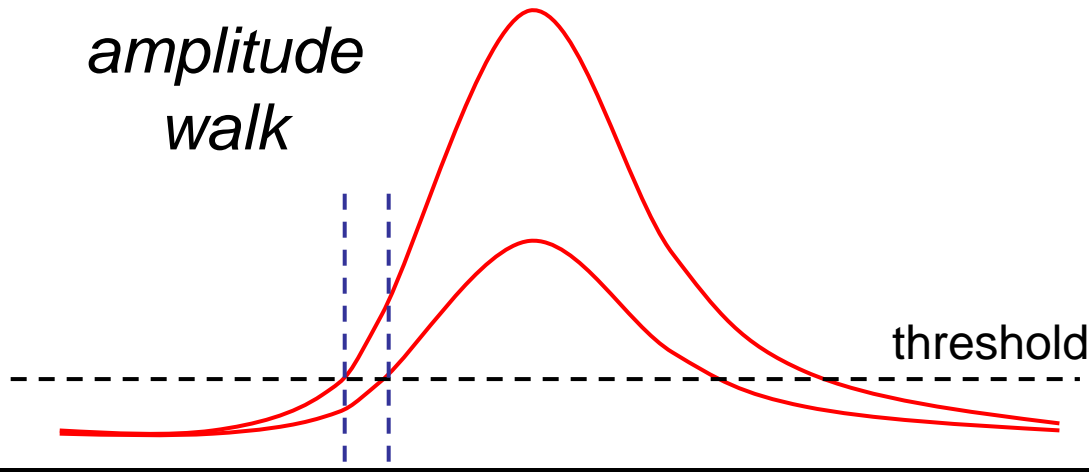
# Leading-edge discriminators



# Leading-edge discriminators



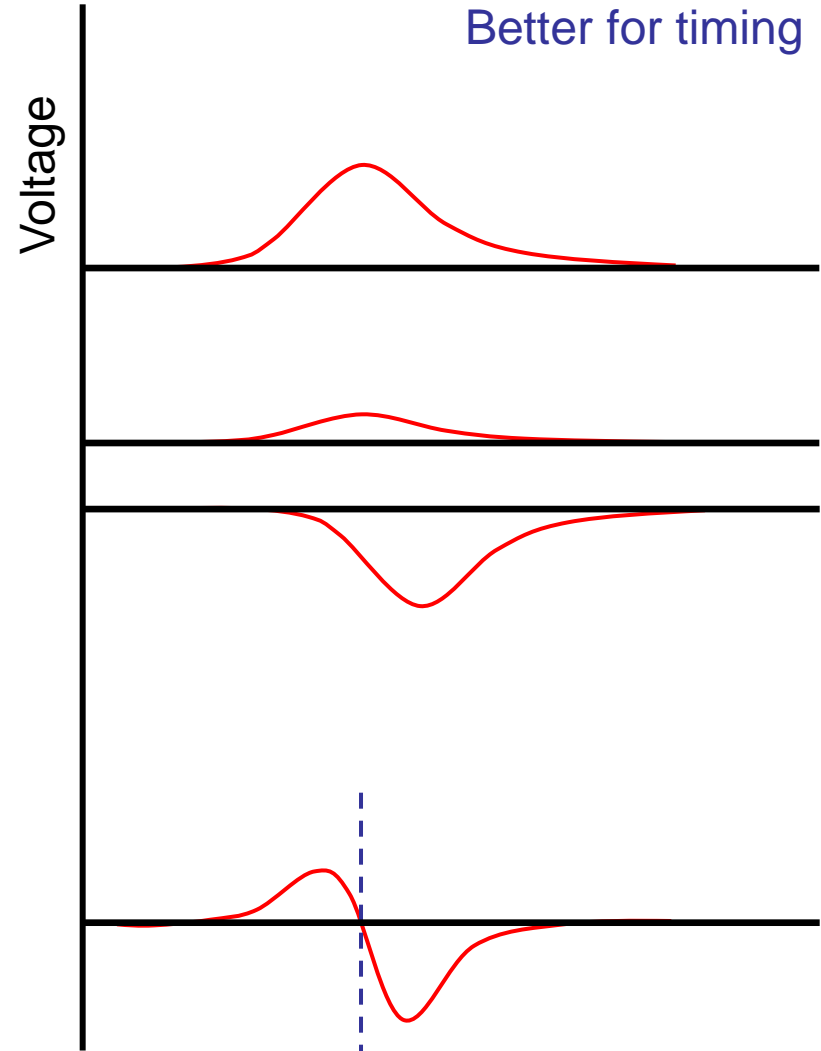
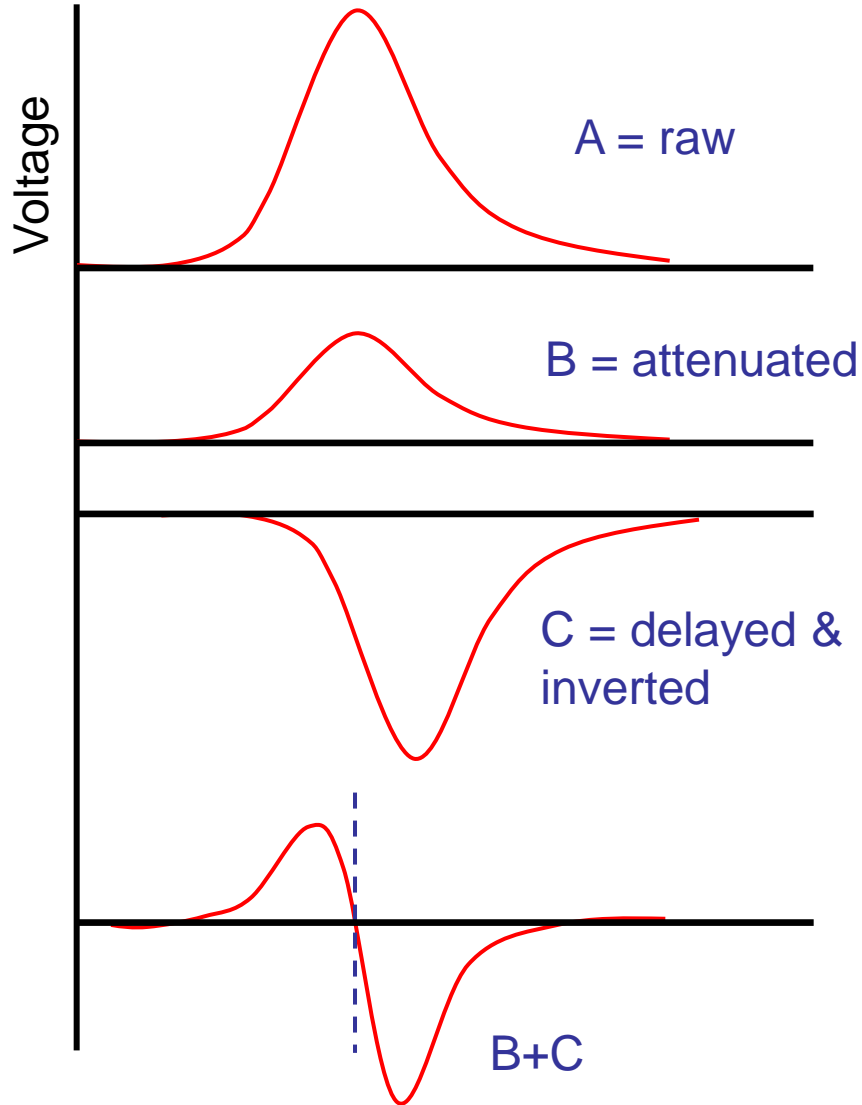
*amplitude walk*



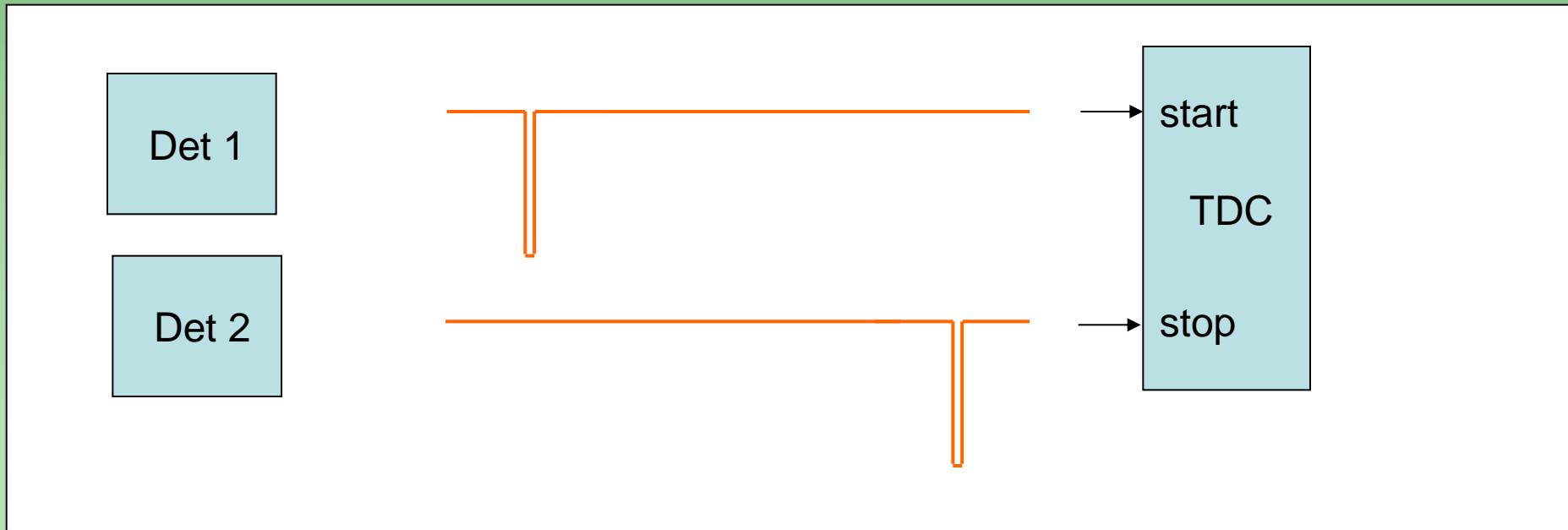
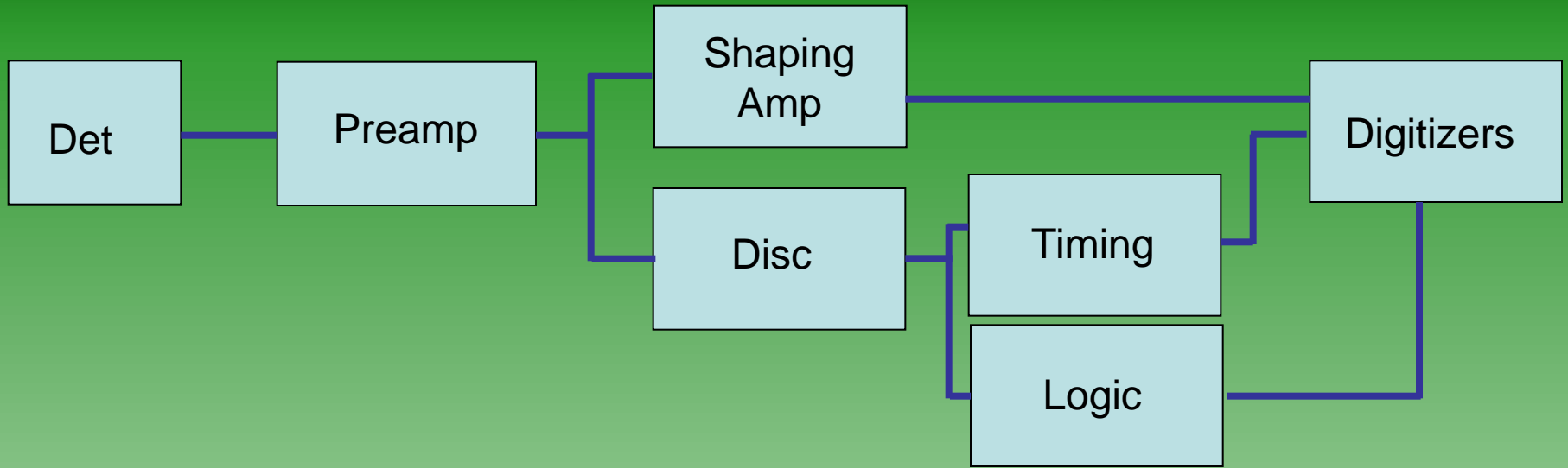
Good for trigger decisions

Bad for timing

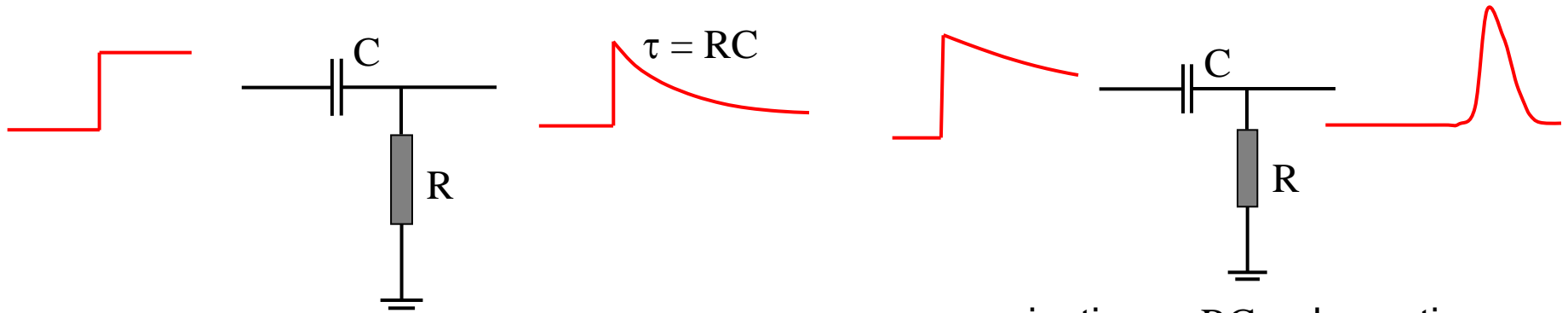
# Constant-fraction discriminators



# Signal processing

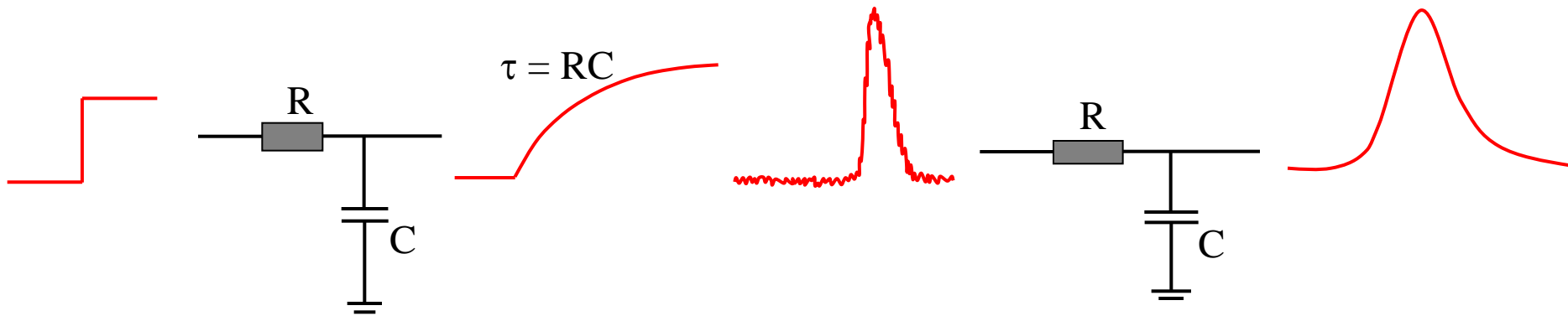


# Analogue signal processing



*High pass filter*

risetime  $< RC <$  decay time



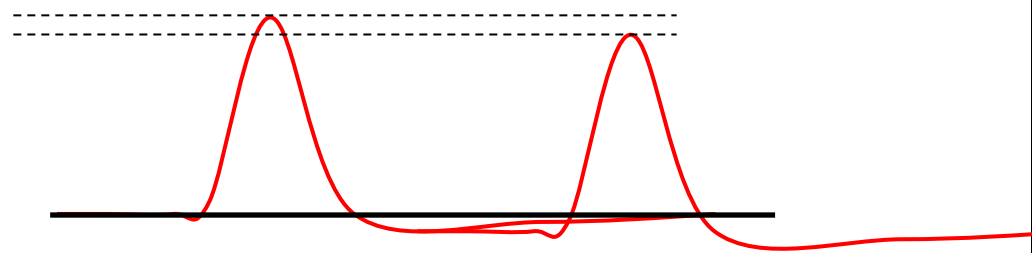
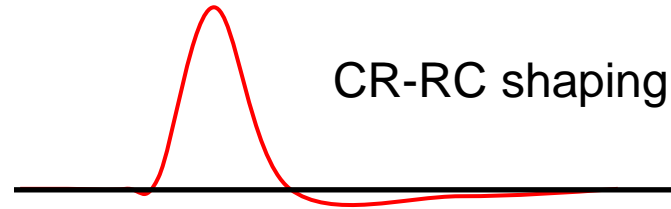
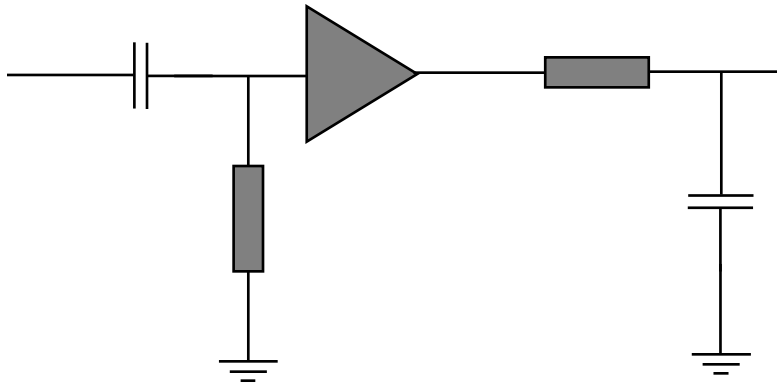
*Low pass filter*

signal length  $< RC$

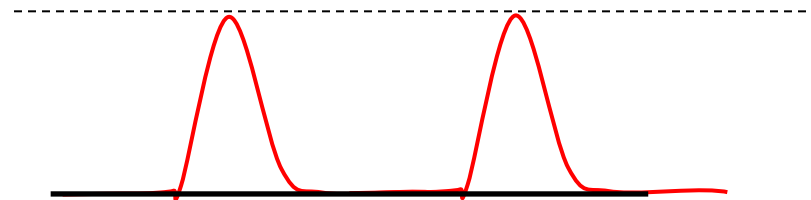
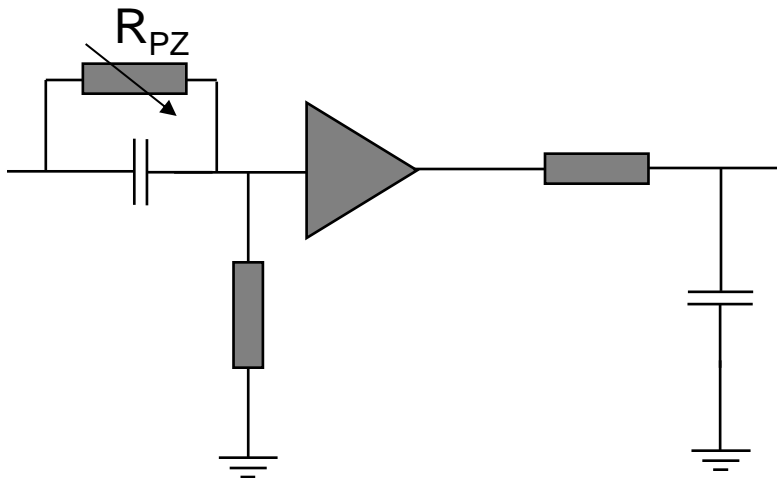
# Shaping amplifiers

Shape pulses to:

- *Improve signal to noise*
- *Reduce pileup effects*



*Undershoot leading to degraded energy resolution*



*Pole zero variable resistor used to tune undershoot*

# Shaping amplifiers

Shape pulses to:

- *Improve signal to noise*
- *Reduce pileup effects*

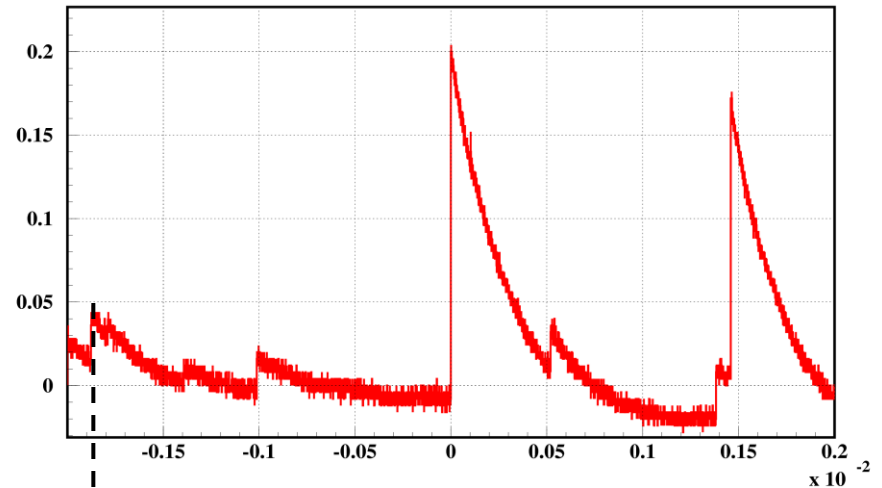
Keep signal height information

Lose shape information

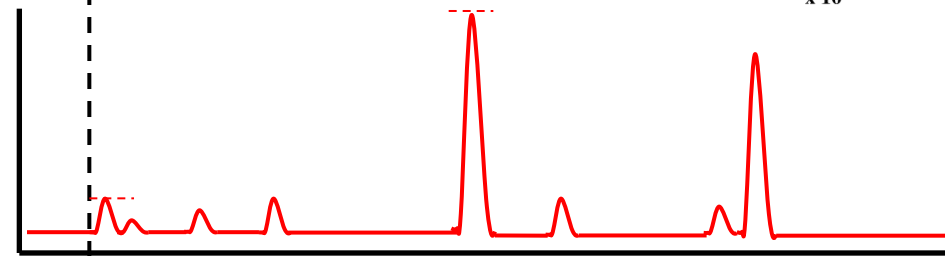
Genuine second pulses missed

→ *Digital!*

*Preamp*



*Shaped signals*



*Trigger*



*ADC gate*



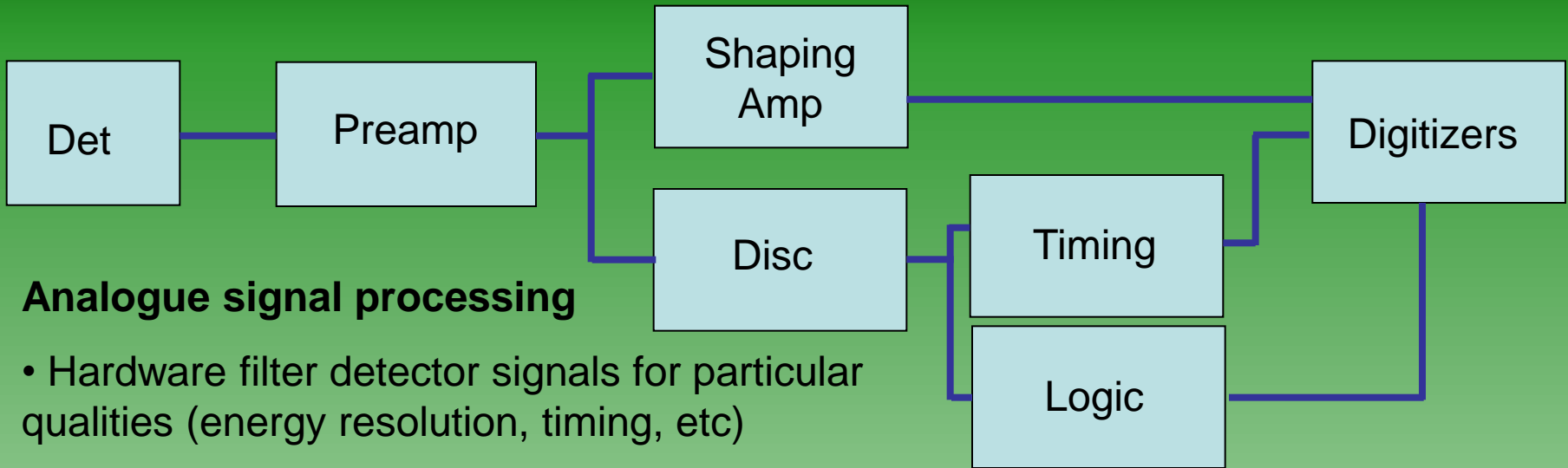
*Conversion/readout*



*Clear*



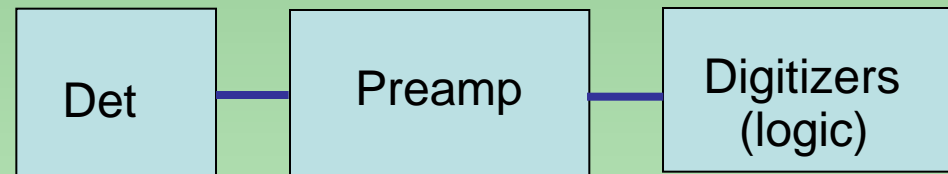
# Signal processing



## Analogue signal processing

- Hardware filter detector signals for particular qualities (energy resolution, timing, etc)
- Excellent resolution, but some information is discarded
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## Digital signal processing



- Process (and sometimes store) a digital approximation of the trace from a detector/preamp
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